RENESAS

RL78/G1C

RENESAS MCU

R01DS0348EJ0110 Rev.1.10 Nov 15, 2013

Datasheet

Integrated USB Controller, True Low Power Platform (as low as 112.5 μ A/MHz, and 0.61 μ A for RTC + LVD), 2.4 V to 5.5 V Operation, 32 Kbyte Flash, 31 DMIPS at 24 MHz, for All USB Based Applications

1. OUTLINE

1.1 Features

Ultra-Low Power Technology

- 2.4 V to 5.5 V operation from a single supply
- Stop (RAM retained): 0.23 μA, (LVD enabled): 0.31 μA
- Halt (RTC + LVD): 0.57 µA
- Supports snooze
- Operating: 71 μA/MHz

16-bit RL78 CPU Core

- Delivers 31 DMIPS at maximum operating frequency of 24 MHz
- Instruction Execution: 86% of instructions can be executed in 1 to 2 clock cycles
- CISC Architecture (Harvard) with 3-stage pipeline
- Multiply Signed & Unsigned: 16 x 16 to 32-bit result in 1 clock cycle
- MAC: 16 x 16 to 32-bit result in 2 clock cycles
- 16-bit barrel shifter for shift & rotate in 1 clock cycle
- 1-wire on-chip debug function

Code Flash Memory

- Density: 32 KB
- Block size: 1 KB
- On-chip single voltage flash memory with protection from block erase/writing
- Self-programming with secure boot swap function and flash shield window function

Data Flash Memory

- Data Flash with background operation
- Data flash size: 2 KB
- Erase Cycles: 1 Million (typ.)
- Erase/programming voltage: 2.4 V to 5.5 V

RAM

- 5.5 KB size options
- Supports operands or instructions
- Back-up retention in all modes

High-speed On-chip Oscillator

- 24 MHz with +/- 1% accuracy over voltage (2.4 V to 5.5 V) and temperature (-20°C to +85°C)
- Pre-configured settings: 48 MHz, 24 MHz (TYP.)

Reset and Supply Management

- Power-on reset (POR) monitor/generator
- Low voltage detection (LVD) with 9 setting options (Interrupt and/or reset function)

USB

- Complying with USB version 2.0, incorporating host/function controller
- Corresponding to full-speed transfer (12 Mbps) and low-speed (1.5 Mbps)
- Complying with Battery Charging Specification Revision 1.2
- Compliant with the 2.1A/1.0A charging mode prescribed in the Apple Inc. MFi specification in the USB power supply component specification ^{Note}

Direct Memory Access (DMA) Controller

- Up to 2 fully programmable channels
- Transfer unit: 8- or 16-bit

Multiple Communication Interfaces

- Up to 2 x I²C master
- Up to 1 x I²C multi-master
- Up to 2 x CSI (7-, 8-bit)
- Up to 1 x UART (7-, 8-, 9-bit)

Extended-Function Timers

- Multi-function 16-bit timer TAU: Up to 4 channels (remote control output available)
- Real-time clock (RTC): 1 channel (full calendar and alarm function with watch correction function)
- 12-bit interval timer: 1 channel
- 15 kHz watchdog timer: 1 channel (window function)

Rich Analog

- ADC: Up to 9 channels, 8/10-bit resolution, 2.1 μs minimum conversion time
- Internal voltage reference (1.45 V)
- On-chip temperature sensor

Safety Features (IEC or UL 60730 compliance)

- Flash memory CRC calculation
- RAM parity error check
- RAM write protection
- SFR write protection
- Illegal memory access detection
- Clock stop/frequency detection
- ADC self-test
- I/O port read back function (echo)

General Purpose I/O

- 5 V tolerant, high-current (up to 20 mA per pin)
- Open-Drain, Internal Pull-up support

Operating Ambient Temperature

- Standard: -40°C to + 85°C
- Extended: -40°C to + 105°C

Package Type and Pin Count

- 32-pin plastic HWQFN (5 x 5)
- 32-pin plastic LQFP (7 x 7)
- 48-pin plastic LFQFP (7 x 7)
- 48-pin plastic HWQFN (7 x 7)
- **Note** To use the Apple Inc. battery charging mode, you must join in Apple's Made for iPod/iPhone/iPad (MFi) licensing program. Before requesting this specification from Renesas Electronics, please join in the Apple's MFi licensing program.



O ROM, RAM capacities

Flash ROM	Data flash	RAM	RL78/G1C		
			32-pin	48-pin	
32 KB	2 KB	5.5 KB ^{Note}	R5F10JBC, R5F10KBC	R5F10JGC, R5F10KGC	

Note This is about 4.5 KB when the self-programming function is used. (For details, see CHAPTER 3 CPU ARCHITECTURE in the RL78/G1C User's Manual: Hardware.)

Remark The functions mounted depend on the product. See **1.6 Outline of Functions**.

1.2 List of Part Numbers

Pin count	Package	USB Function	Fields of Application Note	Part Number
32 pins	32-pin plastic HWQFN	Host/Function controller	А	R5F10JBCANA#U0, R5F10JBCANA#W0
	(5 × 5, 0.5 mm pitch)		G	R5F10JBCGNA#U0, R5F10JBCGNA#W0
		Function controller only	А	R5F10KBCANA#U0, R5F10KBCANA#W0
			G	R5F10KBCGNA#U0, R5F10KBCGNA#W0
	32-pin plastic LQFP	Host/Function controller	А	R5F10JBCAFP#V0, R5F10JBCAFP#X0
	(7 × 7, 0.8 mm pitch)		G	R5F10JBCGFP#V0, R5F10JBCGFP#X0
		Function controller only	А	R5F10KBCAFP#V0, R5F10KBCAFP#X0
			G	R5F10KBCGFP#V0, R5F10KBCGFP#X0
48 pins	48-pin plastic LFQFP	Host/Function controller	А	R5F10JGCAFB#V0, R5F10JGCAFB#X0
	(7 × 7, 0.5 mm pitch)		G	R5F10JGCGFB#V0, R5F10JGCGFB#X0
		Function controller only	А	R5F10KGCAFB#V0, R5F10KGCAFB#X0s
			G	R5F10JGCANA#U0, R5F10JGCANA#W0
	48-pin plastic HWQFN	Host/Function controller	А	R5F10JGCANA#U0, R5F10JGCANA#W0
	(7 × 7, 0.5 mm pitch)		G	R5F10JGCGNA#U0, R5F10JGCGNA#W0
		Function controller only	А	R5F10KGCANA#U0, R5F10KGCANA#W0
			G	R5F10KGCGNA#U0, R5F10KGCGNA#W0

Note For the fields of application, refer to Figure 1-1 Part Number, Memory Size, and Package of RL78/G1C.

Caution The part number above is valid as of when this manual was issued. For the latest part number, see the web page of the target product on the Renesas Electronics website.



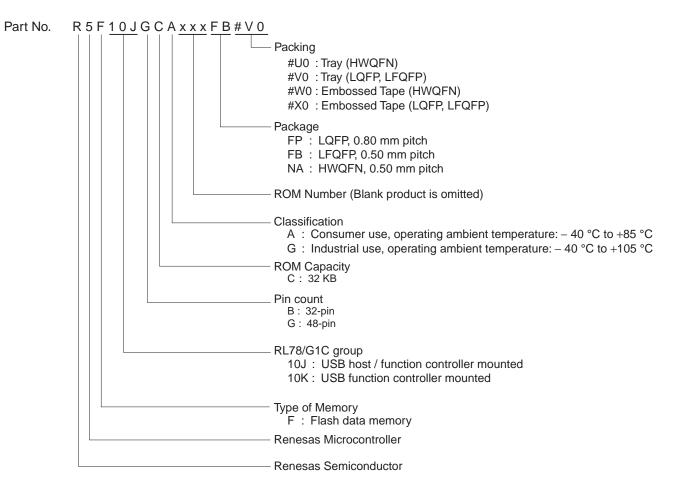


Figure 1-1. Part Number, Memory Size, and Package of RL78/G1C

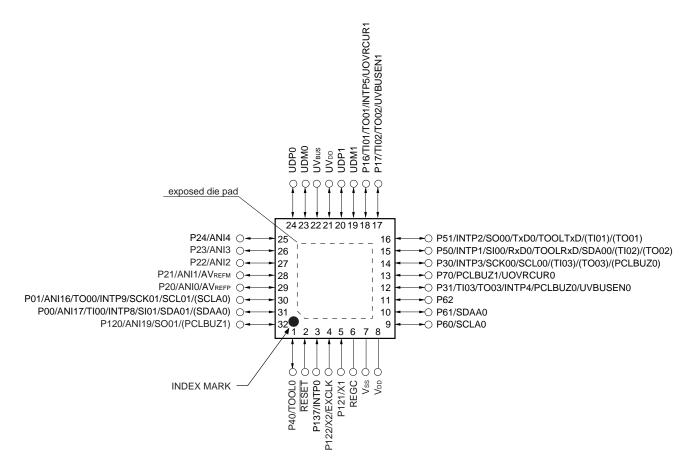


1.3 Pin Configuration (Top View)

1.3.1 32-pin products

• 32-pin plastic HWQFN (5 × 5 mm, 0.5 mm pitch)

(1) USB function: Host/Function controller (R5F10JBC)



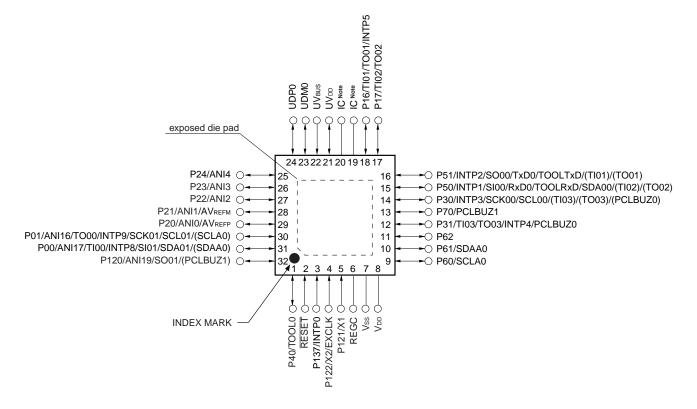
Caution Connect the REGC pin to Vss via a capacitor (0.47 to 1 μ F).

Remarks 1. For pin identification, see 1.4 Pin Identification.

- Functions in parentheses in the above figure can be assigned via settings in the peripheral I/O redirection register (PIOR). Refer to Figure 4-8. Format of Peripheral I/O Redirection Register (PIOR) in the RL78/G1C User's Manual: Hardware.
- 3. It is recommended to connect an exposed die pad to Vss.



(2) USB function: Function controller only (R5F10KBC)



Note IC: Internal Connection Pin. Leave open.

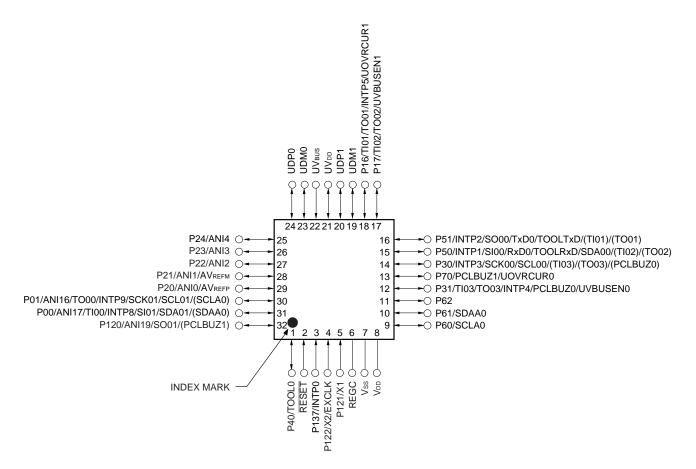
Caution Connect the REGC pin to Vss via a capacitor (0.47 to 1 μ F).

Remarks 1. For pin identification, see 1.4 Pin Identification.

- Functions in parentheses in the above figure can be assigned via settings in the peripheral I/O redirection register (PIOR). Refer to Figure 4-8. Format of Peripheral I/O Redirection Register (PIOR) in the RL78/G1C User's Manual: Hardware.
- 3. It is recommended to connect an exposed die pad to Vss.



- 32-pin plastic LQFP (7 × 7 mm, 0.8 mm pitch)
- (1) USB function: Host/Function controller (R5F10JBC)

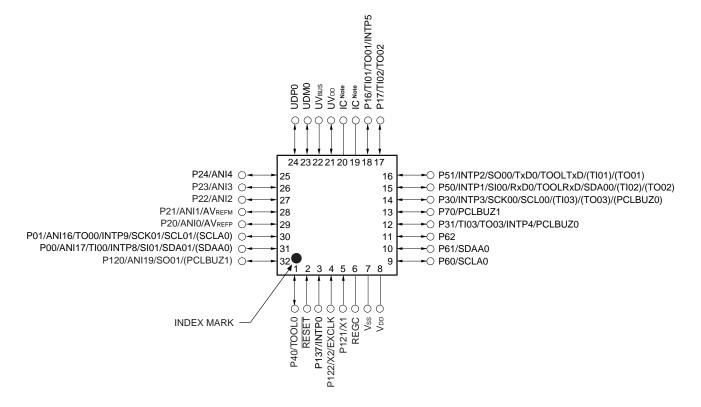


Caution Connect the REGC pin to Vss via a capacitor (0.47 to 1 μ F).

- Remarks 1. For pin identification, see 1.4 Pin Identification.
 - Functions in parentheses in the above figure can be assigned via settings in the peripheral I/O redirection register (PIOR). Refer to Figure 4-8. Format of Peripheral I/O Redirection Register (PIOR) in the RL78/G1C User's Manual: Hardware.



(2) USB function: Function controller only (R5F10KBC)



Note IC: Internal Connection Pin Leave open.

Caution Connect the REGC pin to Vss via a capacitor (0.47 to 1 μ F).

Remarks 1. For pin identification, see 1.4 Pin Identification.

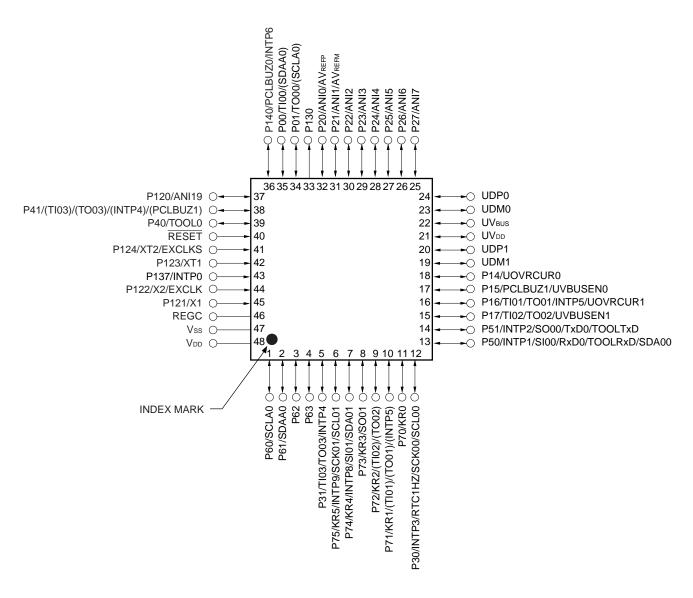
Functions in parentheses in the above figure can be assigned via settings in the peripheral I/O redirection register (PIOR). Refer to Figure 4-8. Format of Peripheral I/O Redirection Register (PIOR) in the RL78/G1C User's Manual: Hardware.



1.3.2 48-pin products

• 48-pin plastic LFQFP (7 × 7, 0.5 mm pitch)

(1) USB function: Host/Function controller (R5F10JGC)

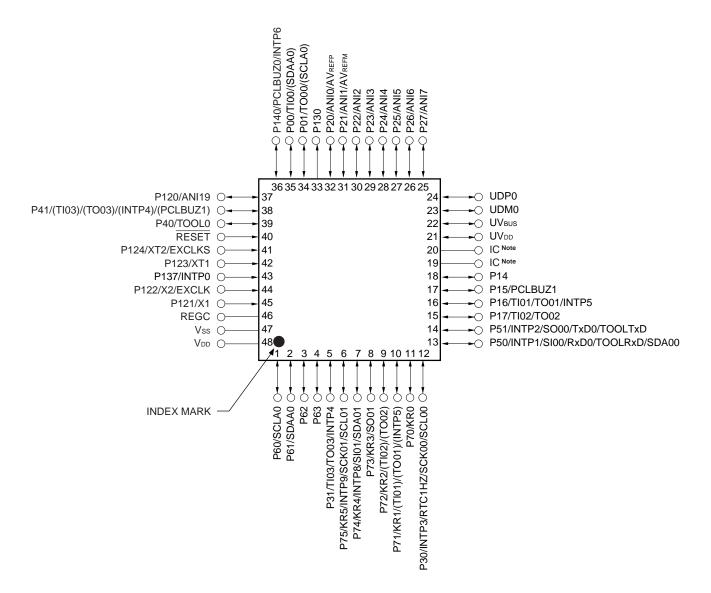


Caution Connect the REGC pin to Vss via a capacitor (0.47 to 1 μ F).

- Remarks 1. For pin identification, see 1.4 Pin Identification.
 - Functions in parentheses in the above figure can be assigned via settings in the peripheral I/O redirection register (PIOR). Refer to Figure 4-8. Format of Peripheral I/O Redirection Register (PIOR) in the RL78/G1C User's Manual: Hardware.



(2) USB function: Function controller only (R5F10KGC)



Note IC: Internal Connection Pin Leave open.

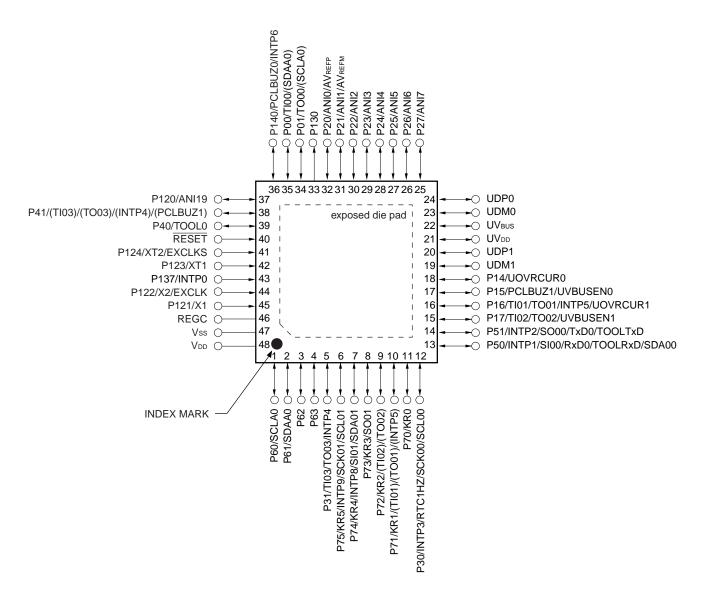
Caution Connect the REGC pin to Vss via a capacitor (0.47 to 1 μ F).

Remarks 1. For pin identification, see 1.4 Pin Identification.

Functions in parentheses in the above figure can be assigned via settings in the peripheral I/O redirection register (PIOR). Refer to Figure 4-8. Format of Peripheral I/O Redirection Register (PIOR) in the RL78/G1C User's Manual: Hardware.



- 48-pin plastic WHQFN (7 × 7, 0.5 mm pitch)
- (1) USB function: Host/Function controller (R5F10JGC)



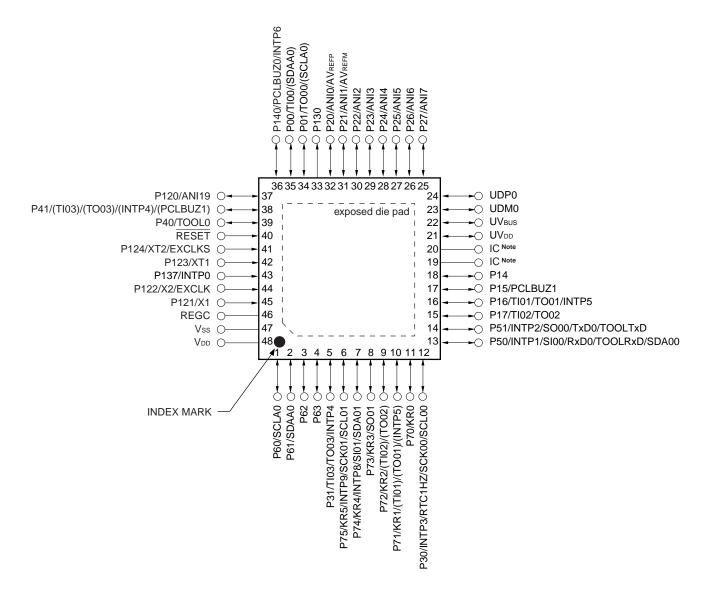
Caution Connect the REGC pin to Vss via a capacitor (0.47 to 1 μ F).

Remarks 1. For pin identification, see 1.4 Pin Identification.

- Functions in parentheses in the above figure can be assigned via settings in the peripheral I/O redirection register (PIOR). Refer to Figure 4-8. Format of Peripheral I/O Redirection Register (PIOR) in the RL78/G1C User's Manual: Hardware.
- 3. It is recommended to connect an exposed die pad to Vss.



(2) USB function: Function controller only (R5F10KGC)



Note IC: Internal Connection Pin Leave open.

Caution Connect the REGC pin to Vss via a capacitor (0.47 to 1 μ F).

Remarks 1. For pin identification, see 1.4 Pin Identification.

- Functions in parentheses in the above figure can be assigned via settings in the peripheral I/O redirection register (PIOR). Refer to Figure 4-8. Format of Peripheral I/O Redirection Register (PIOR) in the RL78/G1C User's Manual: Hardware.
- 3. It is recommended to connect an exposed die pad to Vss.



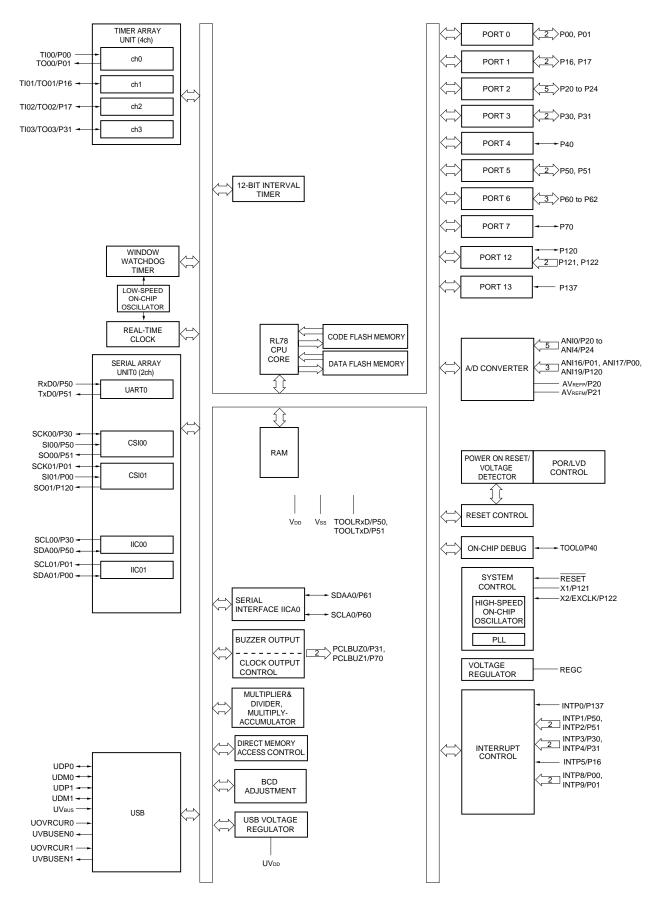
1.4 Pin Identification

ANI0 to ANI7, ANI16, ANI17, ANI19:	Analog Input
AVREFM:	Analog Reference Voltage Minus
AVREFP:	Analog Reference Voltage Plus
EXCLK:	External Clock Input (Main System Clock)
EXCLKS:	External Clock Input (Sub System Clock)
INTP0 to INTP6, INTP8, INTP9:	External Interrupt Input
KR0 to KR5:	Key Return
P00, P01:	Port 0
P14 to P17:	Port 1
P20 to P27:	Port 2
P30, P31:	Port 3
P40, P41:	Port 4
P50, P51:	Port 5
P60 to P63:	Port 6
P70 to P75:	Port 7
P120 to P124:	Port 12
P130, P137:	Port 13
P140:	Port 14
PCLBUZ0, PCLBUZ1:	Programmable Clock Output/Buzzer Output
REGC:	Regulator Capacitance
RESET:	Reset
RTC1HZ:	Real-time Clock Correction Clock (1 Hz) Output
RxD0:	Receive Data
SCK00, SCK01:	Serial Clock Input/Output
SCLA0, SCL00, SCL01:	Serial Clock Input/Output
SDAA0, SDA00, SDA01:	Serial Data Input/Output
SI00, SI01:	Serial Data Input
SO00, SO01:	Serial Data Output
TI00 to TI03:	Timer Input
TO00 to TO03:	Timer Output
TOOL0:	Data Input/Output for Tool
TOOLRxD, TOOLTxD:	Data Input/Output for External Device
TxD0:	Transmit Data
UDM0, UDM1, UDP0, UDP1:	USB Input/Output
UOVRCUR0, UOVRCUR1:	USB Input
UVBUSEN0, UVBUSEN1:	USB Output
UVdd:	USB Power Supply/USB Regulator Capacitance
UVBUS:	USB Input/USB Power Supply (USB Optional BC)
Vdd:	Power Supply
Vss:	Ground
X1, X2:	Crystal Oscillator (Main System Clock)
XT1, XT2:	Crystal Oscillator (Subsystem Clock)



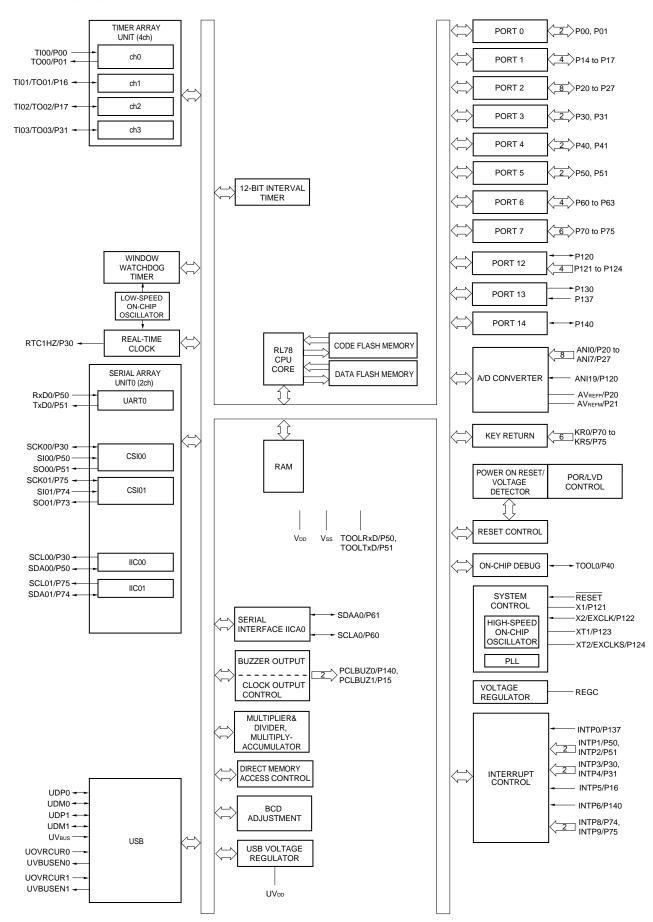
1.5 Block Diagram

1.5.1 32-pin products





1.5.2 48-pin products





1.6 Outline of Functions

[32-pin, 48-pin products]

	Item	32-	-pin	48-	-pin	
		R5F10JBC	R5F10KBC	R5F10JGC	R5F10KGC	
Code fla	sh memory (KB)	32 KB		32 KB		
Data flas	h memory (KB)	2 KB		2 KB		
RAM (KE	3)	5.5 KB Note 1		5.5 KB Note 1		
Memory	space	1 MB		·		
Main system	High-speed system clock	X1 (crystal/ceramic) os 1 to 20 MHz: V _{DD} = 2.7	·	system clock input (EXCL) /DD = 2.4 to 5.5 V	<)	
clock	High-speed on-chip oscillator	1 to 24 MHz (V _{DD} = 2.7		(V _{DD} = 2.4 to 5.5 V)		
	PLL clock	6, 12, 24 MHz Note 2 : V	^v DD = 2.4 to 5.5 V			
Subsyste	em clock	-	-	XT1 (crystal) oscillation 32.768 kHz (TYP.): Vod		
Low-spe	ed on-chip oscillator	On-chip oscillation (Wa	tchdog timer/Real-time	clock/12-bit interval timer	clock)	
		15 kHz (TYP.): VDD = 2.	4 to 5.5 V			
General-	purpose register	8 bits × 32 registers (8	bits $ imes$ 8 registers $ imes$ 4 ba	nks)		
Minimum	instruction execution	0.04167 μ s (High-speed on-chip oscillator: fHOCO = 48 MHz /fH = 24 MHz operation)				
time		0.04167 μs (PLL clock:	fpll = 48 MHz /fiн = 24	MHz ^{Note 2} operation)		
		0.05 μ s (High-speed sy	stem clock: f _{MX} = 20 MH	Iz operation)		
		-	-	30.5 μs (Subsystem clo operation)	лск: fsuв = 32.768 kl	
Instructio	on set	Data transfer (8/16 bit Adder and subtractor/ Multiplication (8 bits × Rotate, barrel shift, ar	logical operation (8/16	bits) , reset, test, and Boolean	operation), etc.	
I/O port	Total	22		38		
	CMOS I/O	16 (N-ch O.D. I/O [VDD	withstand voltage]: 5)	28 (N-ch O.D. I/O [VDD	withstand voltage]:	
	CMOS input	3		5		
	CMOS output	-	_	1		
	N-ch open-drain I/O (6 V tolerance)	3		4		
Timer	16-bit timer	4 channel				
	Watchdog timer	1 channel				
	Real-time clock (RTC)	1 channel Note 3				
	12-bit Interval timer (IT)	1 channel				
	Timer output	4 channels (PWM outpu	t: 3) Note 4			
	RTC output	-	_	1		

Notes 1. In the case of the 5.5 KB, this is about 4.5 KB when the self-programming function is used. (For details, see CHAPTER 3 in the RL78/G1C User's Manual: Hardware)

- 2. In the PLL clock 48 MHz operation, the system clock is 2/4/8 dividing ratio.
- **3.** In 32-pin products, this channel can only be used for the constant-period interrupt function based on the low-speed on-chip oscillator clock (fiL).
- 4. The number of PWM outputs varies depending on the setting of channels in use (the number of masters and slaves). (6.9.3 Operation as multiple PWM output function in the RL78/G1C User's Manual: Hardware)

Caution This outline describes the functions at the time when Peripheral I/O redirection register (PIOR) is set to 00H.



	Item	32-	pin	48	-pin	
		R5F10JBC	R5F10KBC	R5F10JGC	R5F10KGC	
Clock output/buzzer output		2		2		
		 2.93 kHz, 5.86 kHz, 11 (Main system clock: fm 256 Hz, 512 Hz, 1.024 (Subsystem clock: fsue 	an = 24 MHz operation kHz, 2.048 kHz, 4.09	n) 6 kHz, 8.192 kHz, 16.384 k	kHz, 32.768 kHz	
8/10-bit res	solution A/D converter	8 channels		9 channels		
Serial inter		CSI: 2 channels/UART:	1 channel/simplified I ²			
	I ² C bus	1 channel				
USB	Host controller	2 channels	_	2 channels	-	
	Function controller	1 channel			I	
Multiplier and divider/multiply-accumulator		 Multiplier: 16 bits × 16 bits = 32 bits (Unsigned or signed) Divider: 32 bits ÷ 32 bits = 32 bits (Unsigned) Multiply-accumulator:16 bits × 16 bits + 32 bits = 32 bits (Unsigned or signed) 				
DMA contr	oller	2 channels				
Vectored	Internal	20		20		
interrupt sources	External	8		10		
Key interru	pt	-	-	6		
Reset		Reset by RESET pin Internal reset by watch Internal reset by powe Internal reset by voltag Internal reset by illega Internal reset by RAM Internal reset by illega	r-on-reset ge detector I instruction execution parity error	Note		
Power-on-	reset circuit		I.51 V (TYP.) I.50 V (TYP.)			
Voltage de	tector	2.45 V to 4.06 V (9 stag	es)			
On-chip de	bug function	Provided				
Power sup	ply voltage	V _{DD} = 2.4 to 5.5 V				
Operating	ambient temperature	$T_A = -40$ to +85 °C (A: 0	Consumer applications	s), T _A = -40 to +105°C (G:	Industrial application	

Note The illegal instruction is generated when instruction code FFH is executed.

Reset by the illegal instruction execution not issued by emulation with the in-circuit emulator or on-chip debug emulator.



2. ELECTRICAL SPECIFICATIONS (A: T_A = -40 to +85°C)

This chapter describes the electrical specifications for the products "A: Consumer applications (T_A = -40 to +85°C)".

The target products A: Consumer applications ; $T_A = -40$ to $+85^{\circ}C$ R5F10JBCANA, R5F10JBCAFP, R5F10JGCANA, R5F10JGCAFB, R5F10KBCANA, R5F10KBCAFP, R5F10KGCANA, R5F10KGCAFB G: Industrial applications ; when using $T_A = -40$ to $+105^{\circ}C$ specification products at $T_A = -40$ to $+85^{\circ}C$. R5F10JBCGNA, R5F10JBCGFP, R5F10JGCGNA, R5F10JGCGFB, R5F10KBCGNA, R5F10KBCGFP, R5F10KGCGNA, R5F10KGCGFB

- Cautions 1. The RL78 microcontrollers has an on-chip debug function, which is provided for development and evaluation. Do not use the on-chip debug function in products designated for mass production, because the guaranteed number of rewritable times of the flash memory may be exceeded when this function is used, and product reliability therefore cannot be guaranteed. Renesas Electronics is not liable for problems occurring when the on-chip debug function is used.
 - 2. The pins mounted depend on the product. Refer to 2.1 Port Function to 2.2.1 With functions for each product in the RL78/G1C User's Manual: Hardware.



2.1 Absolute Maximum Ratings

Absolute Maximum Ratings (T_A = 25°C) (1/2)

Parameter	Symbols	Conditions	Ratings	Unit
Supply voltage	Vdd		-0.5 to +6.5	V
REGC pin input voltage	Viregc	REGC	-0.3 to +2.8 and -0.3 to V_{DD} +0.3 $^{\text{Note 1}}$	V
UVDD pin input voltage	VIUVDD	UVDD	-0.3 to VDD +0.3	V
Input voltage	Vi1	P00, P01, P14 to P17, P20 to P27, P30, P31, P40, P41, P50, P51, P70 to P75, P120 to P124, P137, P140, EXCLK, EXCLKS, RESET	-0.3 to V _{DD} +0.3 ^{Note 2}	V
	V _{I2}	P60 to P63 (N-ch open-drain)	-0.3 to +6.5	V
	VI3	UDP0, UDM0, UDP1, UDM1	-0.3 to +6.5	V
	VI4	UVBUS	-0.3 to +6.5	V
Output voltage	Vo1	P00, P01, P14 to P17, P20 to P27, P30, P31, P40, P41, P50, P51, P60 to P63, P70 to P75, P120, P130, P140	–0.3 to V _{DD} +0.3 ^{Note 2}	V
	V ₀₂	UDP0, UDM0, UDP1, UDM1	-0.3 to +6.5	V
Analog input voltage	Vaii	ANI16, ANI17, ANI19	-0.3 to V_{DD} +0.3 and -0.3 to AV_{REF} (+) +0.3 Notes 2, 3	V
	Vai2	ANI0 to ANI7	-0.3 to VDD +0.3 and -0.3 to AV_{REF} (+) +0.3 Notes 2, 3	V

Notes 1. Connect the REGC pin to Vss via a capacitor (0.47 to 1 μ F). This value regulates the absolute maximum rating of the REGC pin. Do not use this pin with voltage applied to it.

2. Must be 6.5 V or lower.

- 3. Do not exceed AVREF(+) + 0.3 V in case of A/D conversion target pin
- Caution Product quality may suffer if the absolute maximum rating is exceeded even momentarily for any parameter. That is, the absolute maximum ratings are rated values at which the product is on the verge of suffering physical damage, and therefore the product must be used under conditions that ensure that the absolute maximum ratings are not exceeded.
- **Remarks 1.** Unless specified otherwise, the characteristics of alternate-function pins are the same as those of the port pins.
 - AVREF (+): The + side reference voltage of the A/D converter. This can be selected from AVREFP, the internal reference voltage (1.45 V), and VDD.
 - 3. Vss: Reference voltage



Parameter	Symbols		Conditions	Ratings	Unit	
Output current, high	Іон1	Per pin	P00, P01, P14 to P17, P30, P31,	-40	mA	
			P40, P41, P50, P51, P70 to P75,			
			P120, P130, P140			
		Total of all pins	P00, P01, P40, P41, P120,	-70	mA	
		–170 mA	P130, P140			
			P14 to P17, P30, P31,	-100	mA	
			P50, P51, P70 to P75			
	Іон2	Per pin	P20 to P27	-0.5	mA	
		Total of all pins		-2	mA	
Output current, low	IOL1	Per pin	P00, P01, P14 to P17, P30, P31,	40	mA	
				P40, P41, P50, P51, P60 to P63,		
			P70 to P75, P120, P130, P140			
		Total of all pins	P00, P01, P40, P41, P120,	70	mA	
		170 mA	P130, P140			
			P14 to P17, P30, P31,	100	mA	
			P50, P51, P60 to P63, P70 to P75			
	IOL2	Per pin	P20 to P27	1	mA	
		Total of all pins		5	mA	
Operating ambient	TA	In normal operati	on mode	-40 to +85	°C	
temperature		In flash memory	programming mode			
Storage temperature	Tstg			-65 to +150	°C	

Absolute Maximum Ratings (TA = 25°C) (2/2)

Caution Product quality may suffer if the absolute maximum rating is exceeded even momentarily for any parameter. That is, the absolute maximum ratings are rated values at which the product is on the verge of suffering physical damage, and therefore the product must be used under conditions that ensure that the absolute maximum ratings are not exceeded.



2.2 Oscillator Characteristics

2.2.1 X1, XT1 oscillator characteristics

(TA = -40 to +85°C, 2.4 V \leq VDD \leq 5.5 V, Vss = 0 V)

Parameter	Resonator	Conditions	MIN.	TYP.	MAX.	Unit
X1 clock oscillation frequency (fx) ^{Note}	Ceramic resonator/	$2.7~V \leq V_{\text{DD}} \leq 5.5~V$	1.0		20.0	MHz
	crystal resonator	$2.4~\text{V} \leq \text{V}_{\text{DD}} < 2.7~\text{V}$	1.0		16.0	MHz
XT1 clock oscillation frequency (fxr) ^{Note}	Crystal resonator		32	32.768	35	kHz

Note Indicates only permissible oscillator frequency ranges. Refer to AC Characteristics for instruction execution time. Request evaluation by the manufacturer of the oscillator circuit mounted on a board to check the oscillator characteristics.

- Caution Since the CPU is started by the high-speed on-chip oscillator clock after a reset release, check the X1 clock oscillation stabilization time using the oscillation stabilization time counter status register (OSTC) by the user. Determine the oscillation stabilization time of the OSTC register and the oscillation stabilization time select register (OSTS) after sufficiently evaluating the oscillation stabilization time with the resonator to be used.
- Remark When using the X1 oscillator and XT1 oscillator, refer to 5.4 System Clock Oscillator in the RL78/G1C User's Manual: Hardware.

2.2.2 On-chip oscillator characteristics

$(T_A = -40 \text{ to } +85^{\circ}C, 2.4 \text{ V} \le \text{V}_{DD} \le 5.5 \text{ V}, \text{V}_{SS} = 0 \text{ V})$

Oscillators	Parameters	Conditions	MIN.	TYP.	MAX.	Unit
High-speed on-chip oscillator clock frequency Notes 1, 2	fносо		1		48	MHz
High-speed on-chip oscillator		–20 to +85 °C	-1.0		+1.0	%
clock frequency accuracy		–40 to –20 °C	-1.5		+1.5	%
Low-speed on-chip oscillator clock frequency	fı∟			15		kHz
Low-speed on-chip oscillator clock frequency accuracy			-15		+15	%

Notes 1. High-speed on-chip oscillator frequency is selected by bits 0 to 3 of option byte (000C2H/010C2H) and bits 0 to 2 of HOCODIV register.

2. This indicates the oscillator characteristics only. Refer to AC Characteristics for instruction execution time.



2.2.3 PLL oscillator characteristics

$(T_A = -40 \text{ to } +85^{\circ}\text{C}, 2.4 \text{ V} \le \text{V}_{DD} \le 5.5 \text{ V}, \text{ Vss} = 0 \text{ V})$

		, ,				
Oscillators	Parameters	Conditions	MIN.	TYP.	MAX.	Unit
PLL input frequency Note	fpllin	High-speed system clock	6.00		16.00	MHz
PLL output frequency Note	fpll			48.00		MHz
Lock up time		From PLL output enable to stabilization of the output frequency	40.00			μs
Interval time		From PLL stop to PLL re-operation setteing Wait time	4.00			μs
Setting wait time		From after PLL input clock stabilization and PLL setting is fixed to start setting Wait time required	1.00			μs

Note Indicates only oscillator characteristics. Refer to AC Characteristics for instruction execution time.



2.3 DC Characteristics

2.3.1 Pin characteristics

 $(T_A = -40 \text{ to } +85^{\circ}\text{C}, 2.4 \text{ V} \le \text{V}_{DD} \le 5.5 \text{ V}, \text{V}_{SS} = 0 \text{ V})$

Items	Symbol	Conditions		MIN.	TYP.	MAX.	Unit	
Output current, high ^{Note 1}	Іон1	Per pin for P00, P01, P14 to P17, P30, P31, P40, P41, P50, P51, P70 to P75, P120, P130, P140	$2.4~V \leq V_{DD} \leq 5.5~V$			-10.0 Note 2	mA	
		Total of P00, P01, P40, P41, P120,	$4.0~V \leq V_{DD} \leq 5.5~V$			-55.0	mA	
		P130, P140	$2.7~V \leq V_{DD}~<4.0~V$			-10.0	mA	
		(When duty $\leq 70\%$ ^{Note 3})	$2.4~V \leq V_{DD} < 2.7~V$			-5.0	mA	
			Total of P14 to P17, P30, P31,	$4.0~V \leq V_{DD} \leq 5.5~V$			-80.0	mA
		P50, P51, P70 to P75 (When duty ≤ 70% ^{Note 3})	$2.7~V \leq V_{DD} < 4.0~V$			-19.0	mA	
		(when duty ≤ 70%)	$2.4~V \leq V_{DD}~<2.7~V$			-10.0	mA	
		Total of all pins (When duty ≤ 70% ^{Note 3})	$2.4~V \leq V_{DD} \leq 5.5~V$			-135.0	mA	
	Іон2	Per pin for P20 to P27	$2.4~V \leq V_{\text{DD}} \leq 5.5~V$			-0.1 ^{Note 2}	mA	
		Total of all pins (When duty ≤ 70% ^{Note 3})	$2.4~V \le V_{DD} \le 5.5~V$			-1.5	mA	

Notes 1. Value of current at which the device operation is guaranteed even if the current flows from the V_{DD} pin to an output pin.

- 2. However, do not exceed the total current value.
- Specification under conditions where the duty factor ≤ 70%. The output current value that has changed to the duty factor > 70% the duty ratio can be calculated with the following expression (when changing the duty ratio to n%).
 - Total output current of pins = $(I_{OH} \times 0.7)/(n \times 0.01)$

<Example> Where n = 80% and IoH = -10.0 mA

Total output current of pins = $(-10.0 \times 0.7)/(80 \times 0.01) \approx -8.7$ mA

However, the current that is allowed to flow into one pin does not vary depending on the duty factor.

A current higher than the absolute maximum rating must not flow into one pin.

Caution P00, P01, P30, and P74 do not output high level in N-ch open-drain mode.



Items	Symbol	Conditions		MIN.	TYP.	MAX.	Unit
Output current, Iow ^{Note 1}	Iol1	Per pin for P00, P01, P14 to P17, P30, P31, P40, P41, P50, P51, P70 to P75, P120, P130, P140	$2.4V \leq V_{\text{DD}} \leq 5.5 \text{ V}$			20.0 Note 2	mA
		Per pin for P60 to P63	$2.4V \leq V_{DD} \leq 5.5~V$			20.0 Note 2	mA
		Total of P00, P01, P40, P41, P120,	$4.0~V \leq V_{\text{DD}} \leq 5.5~V$			70.0	mA
		P130, P140	$2.7~\text{V} \leq \text{V}_\text{DD} < 4.0~\text{V}$			15.0	mA
		(When duty ≤ 70% ^{Note 3})	$2.4 \text{ V} \leq \text{V}_{\text{DD}} < 2.7 \text{ V}$			9.0	mA
		Total of P14 to P17, P30, P31, P50,	$4.0~V \leq V_{DD} \leq 5.5~V$			80.0	mA
		P51, P60 to P63, P70 to P75	$2.7~\text{V} \leq \text{V}_\text{DD} < 4.0~\text{V}$			35.0	mA
		(When duty ≤ 70% ^{Note 3})	$2.4 \text{ V} \leq \text{V}_{\text{DD}} < 2.7 \text{ V}$				mA
		Total of all pins (When duty ≤ 70% ^{Note 3})	$2.4V \leq V_{DD} \leq 5.5 \ V$			150.0	mA
	IOL2	Per pin for P20 to P27	$2.4V \leq V_{DD} \leq 5.5~V$			0.4 Note 2	mA
		Total of all pins (When duty ≤ 70% ^{Note 3})	$2.4V \leq V_{DD} \leq 5.5 \ V$			5.0	mA

$(T_A = -40 \text{ to } +85^{\circ}\text{C}, 2.4 \text{ V} \le \text{V}_{DD} \le 5.5 \text{ V}, \text{V}_{SS} = 0 \text{ V})$

Notes 1. Value of current at which the device operation is guaranteed even if the current flows from an output pin to the Vss pin.

2. However, do not exceed the total current value.

3. Specification under conditions where the duty factor ≤ 70%. The output current value that has changed to the duty factor > 70% the duty ratio can be calculated with the following expression (when changing the duty ratio to n%).

- Total output current of pins = $(I_{OL} \times 0.7)/(n \times 0.01)$
- <Example> Where n = 80% and IoL = 10.0 mA

Total output current of pins = $(10.0 \times 0.7)/(80 \times 0.01) \approx 8.7 \text{ mA}$

However, the current that is allowed to flow into one pin does not vary depending on the duty factor. A current higher than the absolute maximum rating must not flow into one pin.



Items	Symbol	Conditions	MIN.	TYP.	MAX.	Unit	
Input voltage, high	Vih1	P00, P01, P14 to P17, P30, P31, P40, P41, P50, P51, P70 to P75, P120, P140	Normal input buffer	0.8Vdd		Vdd	V
	VIH2	P00, P01, P30, P50	TTL input buffer 4.0 V \leq V _{DD} \leq 5.5 V	2.2		Vdd	V
			TTL input buffer $3.3 \text{ V} \leq \text{V}_{\text{DD}} < 4.0 \text{ V}$	2.0		Vdd	V
			TTL input buffer $2.4 \text{ V} \leq \text{V}_{\text{DD}} < 3.3 \text{ V}$	1.5		Vdd	V
	Vінз	P20 to P27	0.7Vdd		Vdd	V	
	VIH4	P60 to P63	0.7Vdd		6.0	V	
	VIH5	P121 to P124, P137, EXCLK, EXCLK	0.8Vdd		Vdd	V	
Input voltage, Iow	VIL1	P00, P01, P14 to P17, P30, P31, P40, P41, P50, P51, P70 to P75, P120, P140	Normal input buffer	0		0.2Vdd	V
	VIL2	P00, P01, P30, P50	TTL input buffer 4.0 V \leq V _{DD} \leq 5.5 V	0		0.8	V
			TTL input buffer $3.3 \text{ V} \leq \text{V}_{\text{DD}} < 4.0 \text{ V}$	0		0.5	V
			TTL input buffer 2.4 V \leq V _{DD} $<$ 3.3 V	0		0.32	V
	VIL3	P20 to P27		0		0.3Vdd	V
	VIL4	P60 to P63		0		0.3Vdd	V
	VIL5	P121 to P124, P137, EXCLK, EXCLK	(S, RESET	0		0.2Vdd	V

$(T_A = -40 \text{ to } +85^{\circ}\text{C}, 2.4 \text{ V} \le \text{V}_{DD} \le 5.5 \text{ V}, \text{ V}_{SS} = 0 \text{ V})$

Caution The maximum value of V_H of pins P00, P01, P30, and P74 is V_{DD}, even in the N-ch open-drain mode.



Items	Symbol	Conditions	MIN.	TYP.	MAX.	Unit	
Output voltage, high	Voh1	P00, P01, P14 to P17, P30, P31, P40, P41, P50, P51, P70 to P75,	$\begin{array}{l} 4.0 \ V \leq V_{\text{DD}} \leq 5.5 \ V, \\ I_{\text{OH1}} = -10.0 \ \text{mA} \end{array}$	Vdd - 1.5			V
		P120, P130, P140	$\begin{array}{l} 4.0 \ V \leq V_{\text{DD}} \leq 5.5 \ V, \\ I_{\text{OH1}} = -3.0 \ \text{mA} \end{array}$	Vdd - 0.7			V
			$\begin{array}{l} 2.7 \ V \leq V_{\text{DD}} \leq 5.5 \ V, \\ I_{\text{OH1}} = -2.0 \ \text{mA} \end{array}$	Vdd - 0.6			V
			$2.4 \text{ V} \le \text{V}_{\text{DD}} \le 5.5 \text{ V},$ Іон1 = -1.5 mA	Vdd - 0.5			V
	Vон2	P20 to P27	2.4 V \leq V _{DD} \leq 5.5 V, Іон2 = -100 μ А	Vdd - 0.5			V
Output voltage, low	Vol1	P00, P01, P14 to P17, P30, P31, P40, P41, P50, P51, P70 to P75,	$\begin{array}{l} 4.0 \ V \leq V_{\text{DD}} \leq 5.5 \ V, \\ I_{\text{OL1}} = 20.0 \ mA \end{array} \end{array} \label{eq:VDD}$			1.3	V
		P120, P130, P140	$\begin{array}{l} 4.0 \ V \leq V_{\text{DD}} \leq 5.5 \ V, \\ I_{\text{OL1}} = 8.5 \ mA \end{array} \end{array} \label{eq:VDD}$			0.7	V
			$\begin{array}{l} 2.7 \ V \leq V_{\text{DD}} \leq 5.5 \ V, \\ I_{\text{OL1}} = 3.0 \ \text{mA} \end{array} \end{array} \label{eq:VDD}$			0.6	V
			$2.7 \text{ V} \leq V_{\text{DD}} \leq 5.5 \text{ V},$ $I_{\text{OL1}} = 1.5 \text{ mA}$			0.4	V
			$2.4 \text{ V} \leq \text{V}_{\text{DD}} \leq 5.5 \text{ V},$ $I_{\text{OL1}} = 0.6 \text{ mA}$			0.4	V
	Vol2	P20 to P27	$2.4 \text{ V} \le \text{V}_{\text{DD}} \le 5.5 \text{ V},$ $\text{Iol2} = 400 \ \mu \text{ A}$			0.4	V
	Vol3	P60 to P63	$4.0 \text{ V} \le \text{V}_{\text{DD}} \le 5.5 \text{ V},$ $I_{\text{OL1}} = 20.0 \text{ mA}$			2.0	V
			$\begin{array}{l} 4.0 \ V \leq V_{\text{DD}} \leq 5.5 \ V, \\ I_{\text{OL1}} = 5.0 \ mA \end{array} \end{array} \label{eq:VDD}$			0.4	V
			$2.7 \text{ V} \leq V_{\text{DD}} \leq 5.5 \text{ V},$ $I_{\text{OL1}} = 3.0 \text{ mA}$			0.4	V
			$\begin{array}{l} 2.4 \ V \leq V_{DD} \leq 5.5 \ V, \\ I_{OL1} = 2.0 \ mA \end{array} \label{eq:VDD}$			0.4	V

$(T_A = -40 \text{ to } +85^{\circ}\text{C}, 2.4 \text{ V} \le \text{V}_{DD} \le 5.5 \text{ V}, \text{ V}_{SS} = 0 \text{ V})$

Caution P00, P01, P30, and P74 do not output high level in N-ch open-drain mode.



Items	Symbol	Conditio	ns		MIN.	TYP.	MAX.	Unit
Input leakage current, high	Iuni	P00, P01, P14 to P17, P20 to P27, P30, P31, P40, P41, P50, P51, P60 to P63, P70 to P75, P120, P137, P140, RESET	Vi = V _{DD}				1	μA
	Ilih2	P121 to P124 (X1, X2, XT1, XT2, EXCLK, EXCLKS)	VI = VDD	In input port or external clock input			1	μA
				In resonator connection			10	μA
Input leakage current, low	Ilil1	P00, P01, P14 to P17, P20 to P27, P30, P31, P40, P41, P50, P51, P60 to P63, P70 to P75, P120, P137, P140, RESET	Vi = Vss				-1	μA
	ILIL2	P121 to P124 (X1, X2, XT1, XT2, EXCLK, EXCLKS)	VI = Vss	In input port or external clock input			-1	μA
				In resonator connection			-10	μA
On-chip pll-up resistance	Ru	P00, P01, P14 to P17, P30, P31, P40, P41, P50, P51, P70 to P75, P120, P140	VI = Vss, In input port		10	20	100	kΩ

(TA = -40 to +85°C, 2.4 V \leq VDD \leq 5.5 V, Vss = 0 V)



2.3.2 Supply current characteristics

(1/2)

Parameter	Symbol	/mbol	Conditions					TYP.	MAX.	Unit	
Supply IDD1	1 0) HS	fносо = 48 MHz	Basic VDD = 5.0 V			1.7		mA		
CUITENT Note 1		mode	(High-speed main) mode	$f_{IH} = 24 \text{ MHz}^{Note 3}$	operation	$V_{DD} = 3.0 V$		1.7		mA	
			Note 6		Normal	$V_{DD} = 5.0 V$		3.7	5.5	mA	
					operation	VDD = 3.0 V		3.7	5.5	mA	
				fносо = 24 MHz ^{Note 5}	Normal	Vdd = 5.0 V		2.3	3.2	mA	
				fін = 12 MHz ^{Note 3}	operation	VDD = 3.0 V		2.3	3.2	mA	
				fносо = 12 MHz ^{Note 5}	Normal	V _{DD} = 5.0 V		1.6	2.0	mA	
				$f_{IH} = 6 \text{ MHz}^{\text{Note 3}}$	operation	VDD = 3.0 V		1.6	2.0	mA	
				fHOCO = 6 MHz ^{Note 5}	Normal	Vdd = 5.0 V		1.2	1.5	mA	
				fiн = 3 MHz Note 3	operation	VDD = 3.0 V		1.2	1.5	mA	
			HS	f _{MX} = 20 MHz ^{Note 2} ,	Normal	Square wave input		3.0	4.6	mA	
		(High-speed	Vdd = 5.0 V	operation	Resonator connection		3.2	4.8	mA		
			main) mode Note 6	$f_{MX} = 20 \text{ MHz}^{Note 2},$	Normal	Square wave input		3.0	4.6	mA	
			Vdd = 3.0 V	operation	Resonator connection		3.2	4.8	mA		
			f _{MX} = 10 MHz ^{Note 2} ,	Normal	Square wave input		1.9	2.7	mA		
	(VDD = 5.0 V	operation	Resonator connection		1.9	2.7	mA		
			f _{MX} = 10 MHz ^{Note 2} ,	Normal operation	Square wave input		1.9	2.7	mA		
			Vdd = 3.0 V		Resonator connection		1.9	2.7	mA		
		HS (High-speed	fpll = 48 MHz,	Normal	V _{DD} = 5.0 V		4.0	5.9	mA		
			fclk = 24 MHz Note 2	operation	V _{DD} = 3.0 V		4.0	5.9	mA		
		(PLL operation) Note 6	operation) Note 6 Subsystem clock	fpll = 48 MHz,	Normal	Vdd = 5.0 V		2.6	3.6	mA	
				operation) fclk = 1	fclk = 12 MHz Note 2	operation	Vdd = 3.0 V		2.6	3.6	mA
				fpll = 48 MHz,	Normal	Vdd = 5.0 V		1.9	2.4	mA	
				fclk = 6 MHz ^{Note 2}	operation	VDD = 3.0 V		1.9	2.4	mA	
				fsuв = 32.768 kHz	Normal	Resonator connection		4.1	4.9	μA	
				Note 4	operation	Square wave input		4.2	5.0	μA	
			operation	$T_{A} = -40^{\circ}C$		2					
				fsuв = 32.768 kHz Note 4	Normal operation	Square wave input		4.1	4.9	μA	
				T _A = +25°C	oportation	Resonator connection		4.2	5.0	μA	
				fsuв = 32.768 kHz	Normal	Square wave input		4.2	5.5	μA	
				Note 4	operation	Resonator connection		4.3	5.6	<i>.</i> μΑ	
				T _A = +50°C							
			fsuв = 32.768 kHz	Normal	Square wave input		4.2	6.3	μA		
			Note 4	operation	Resonator connection		4.3	6.4	μA		
			$T_A = +70^{\circ}C$								
				fsuв = 32.768 kHz	Normal	Square wave input		4.8	7.7	μA	
			Note 4	operation	Resonator connection		4.9	7.8	μA		
				T _A = +85°C							

(Notes and Remarks are listed on the next page.)



- **Notes 1.** Total current flowing into V_{DD}, including the input leakage current flowing when the level of the input pin is fixed to V_{DD}, or V_{SS}. The values below the MAX. column include the peripheral operation current. However, not including the current flowing into the A/D converter, LVD circuit, I/O port, and on-chip pull-up/pull-down resistors and the current flowing during data flash rewrite.
 - 2. When high-speed on-chip oscillator and subsystem clock are stopped.
 - 3. When high-speed system clock and subsystem clock are stopped.
 - **4.** When high-speed on-chip oscillator and high-speed system clock are stopped. When AMPHS1 = 1 (Ultra-low power consumption oscillation). However, not including the current flowing into the RTC, 12-bit interval timer, and watchdog timer.
 - **5.** When Operating frequency setting of option byte = 48 MHz. When fHOCO is divided by HOCODIV. When RDIV[1:0] = 00 (divided by 2: default).
 - **6.** Relationship between operation voltage width, operation frequency of CPU and operation mode is as below.

HS (high-speed main) mode: 2.7 V \leq V_{DD} \leq 5.5 V@1 MHz to 24 MHz 2.4 V \leq V_{DD} \leq 5.5 V@1 MHz to 16 MHz

- Remarks 1. fHOCO: High-speed on-chip oscillator clock frequency (Max. 48 MHz)
 - 2. fill: Main system clock source frequency obtained by dividing the high-speed on-chip oscillator clock by 2, 4, or 8 (Max. 24 MHz)
 - **3.** fmx: High-speed system clock frequency (X1 clock oscillation frequency or external main system clock frequency)
 - 4. fPLL: PLL oscillation frequency
 - 5. fsub: Subsystem clock frequency (XT1 clock oscillation frequency)
 - 6. fclk: CPU/peripheral hardware clock frequency
 - 7. Except subsystem clock operation, temperature condition of the TYP. value is $T_A = 25^{\circ}C$.



		$(0, 2.4 \ V \le VDD \le 0.5 \ V, \ VSS = 0 \ V)$									
Parameter	Symbol			Conditions		MIN.	TYP.	MAX.	Unit		
	IDD2	HALT	HS	fносо = 48 MHz	Vdd = 5.0 V		0.67	1.25	mA		
Current Note 1	Note 2	mode		fiн = 24 MHz ^{Note 4}	VDD = 3.0 V		0.67	1.25	mA		
			main) mode Note 9	fносо = 24 MHz ^{Note 7}	VDD = 5.0 V		0.50	0.86	mA		
				fін = 12 MHz ^{Note 4}	VDD = 3.0 V		0.50	0.86	mA		
				fHOCO = 12 MHz ^{Note 7}	V _{DD} = 5.0 V		0.41	0.67	mA		
				fin = 6 MHz Note 4	V _{DD} = 3.0 V		0.41	0.67	mA		
				$f_{HOCO} = 6 \text{ MHz}^{Note 7}$	V _{DD} = 5.0 V		0.37	0.58	mA		
				fi⊢ = 3 MHz ^{Note 4}	VDD = 3.0 V		0.37	0.58	mA		
			HS	$f_{MX} = 20 \text{ MHz}^{\text{Note 3}},$	Square wave input		0.28	1.00	mA		
			(High-speed	$V_{DD} = 5.0 V$	Resonator connection		0.45	1.17	mA		
			main) mode Note 9	$f_{MX} = 20 \text{ MHz}^{Note 3},$	Square wave input		0.28	1.00	mA		
				$V_{DD} = 3.0 V$	Resonator connection		0.45	1.17	mA		
				$f_{MX} = 10 \text{ MHz}^{Note 3},$	Square wave input		0.19	0.60	mA		
				$V_{DD} = 5.0 V$	Resonator connection		0.26	0.67	mA		
				$f_{MX} = 10 \text{ MHz}^{Note 3},$	Square wave input		0.19	0.60	mA		
				$V_{DD} = 3.0 V$	Resonator connection		0.26	0.67	mA		
			HS (High-speed main) mode (PLL operation) Note 9 Subsystem clock	fpll = 48 MHz,	V _{DD} = 5.0 V		0.91	1.52	mA		
				fclk = 24 MHz ^{Note 3}	V _{DD} = 3.0 V		0.91	1.52	mA		
				fpll = 48 MHz, fclk = 12 MHz ^{Note 3}	VDD = 5.0 V		0.85	1.28	mA		
					VDD = 3.0 V		0.85	1.28	mA		
				$f_{\text{PLL}} = 48 \text{ MHz},$ $f_{\text{CLK}} = 6 \text{ MHz}^{\text{Note 3}}$	V _{DD} = 5.0 V		0.82	1.15	mA		
					V _{DD} = 3.0 V		0.82	1.15	mA		
				fsuв = 32.768 kHz ^{Note 5}	Square wave input		0.25	0.57	μA		
				$T_A = -40^{\circ}C$	Resonator connection		0.44	0.76	μA		
			operation	fsub = 32.768 kHz ^{Note 5}	Square wave input		0.30	0.57	μA		
				T _A = +25°C	Resonator connection		0.49	0.76	μA		
				fsub = 32.768 kHz ^{Note 5}	Square wave input		0.33	1.17	μA		
				$T_A = +50^{\circ}C$	Resonator connection		0.63	1.36	μA		
				fsuв = 32.768 kHz ^{Note 5}	Square wave input		0.46	1.97	μA		
נססן				T _A = +70°C	Resonator connection		0.76	2.16	μA		
				fsuв = 32.768 kHz ^{Note 5}	Square wave input		0.97	3.37	μA		
				$T_A = +85^{\circ}C$	Resonator connection		1.16	3.56	μA		
	IDD3 ^{Note 6}	⁶ STOP mode ^{Note 8}	$T_A = -40^{\circ}C$				0.18	0.50	μA		
			T _A = +25°C				0.23	0.50	μA		
			T _A = +50°C				0.26	1.10	μA		
			T _A = +70°C				0.29	1.90	μA		
			T _A = +85°C				0.90	3.30	μA		

$(T_A = -40 \text{ to } +85^{\circ}C, 2.4 \text{ V} \le \text{V}_{DD} \le 5.5 \text{ V}, \text{V}_{SS} = 0 \text{ V})$

(2/2)

(Notes and Remarks are listed on the next page.)



- **Notes 1.** Total current flowing into VDD, including the input leakage current flowing when the level of the input pin is fixed to VDD or Vss. The values below the MAX. column include the peripheral operation current. However, not including the current flowing into the A/D converter, LVD circuit, USB 2.0 host/function module, I/O port, and on-chip pull-up/pull-down resistors and the current flowing during data flash rewrite.
 - 2. During HALT instruction execution by flash memory.
 - 3. When high-speed on-chip oscillator and subsystem clock are stopped.
 - 4. When high-speed system clock and subsystem clock are stopped.
 - When high-speed on-chip oscillator and high-speed system clock are stopped. When RTCLPC = 1 and setting ultra-low current consumption (AMPHS1 = 1). The current flowing into the RTC is included. However, not including the current flowing into the 12-bit interval timer and watchdog timer.
 - 6. Not including the current flowing into the RTC, 12-bit interval timer, and watchdog timer.
 - **7.** When Operating frequency setting of option byte = 48 MHz. When fHOCO is divided by HOCODIV. When RDIV[1:0] = 00 (divided by 2: default).
 - 8. Regarding the value for current to operate the subsystem clock in STOP mode, refer to that in HALT mode.
 - **9.** Relationship between operation voltage width, operation frequency of CPU and operation mode is as below.

HS (high-speed main) mode: 2.7 V \leq V_{DD} \leq 5.5 V@1 MHz to 24 MHz 2.4 V \leq V_{DD} \leq 5.5 V@1 MHz to 16 MHz

- Remarks 1. fHOCO: High-speed on-chip oscillator clock frequency (Max. 48 MHz)
 - 2. fill: Main system clock source frequency obtained by dividing the high-speed on-chip oscillator clock by 2, 4, or 8 (Max. 24 MHz)
 - **3.** fmx: High-speed system clock frequency (X1 clock oscillation frequency or external main system clock frequency)
 - 4. fPLL: PLL oscillation frequency
 - 5. fsub: Subsystem clock frequency (XT1 clock oscillation frequency)
 - 6. fcLK: CPU/peripheral hardware clock frequency
 - 7. Except subsystem clock operation, temperature condition of the TYP. value is $T_A = 25^{\circ}C$.



Parameter	Symbol		MIN.	TYP.	MAX.	Unit	
Low-speed on-chip oscillator operating current	IFIL ^{Note 1}				0.20		μA
RTC operating current	IRTC Notes 1, 2, 3				0.02		μA
12-bit interval timer operating current	IT Notes 1, 2, 4			0.02		μA	
Watchdog timer operating current	WDT Notes 1, 2, 5	fı∟ = 15 kHz		0.22		μA	
A/D converter	ADC Notes 1, 6	When conversion	Normal mode, AV _{REFP} = V _{DD} = 5.0 V		1.3	1.7	mA
operating current		at maximum speed	Low voltage mode, $AV_{REFP} = V_{DD} = 3.0 V$		0.5	0.7	mA
A/D converter reference voltage current	ADREF Note 1				75.0		μA
Temperature sensor operating current	ITMPS Note 1				75.0		μA
LVD operating current	LVD Notes 1, 7				0.08		μA
Self-programming operating current	IFSP Notes 1, 9				2.00	12.20	mA
BGO operating current	IBGO Notes 1, 8				2.00	12.20	mA
SNOOZE operating	Isnoz Note 1	ADC operation	The mode is performed Note 10		0.50	1.06	mA
current			The A/D conversion operations are performed, Low voltage mode, $AV_{REFP} = V_{DD} = 3.0 V$		1.20	1.62	mA
		CSI operation	·		0.70	0.84	mA

(TA = -40 to +85°C, 2.4 V \leq VDD \leq 5.5 V, Vss = 0 V) (1/2)

(Notes and Remarks are listed on the next page.)



$(T_A = -40 \text{ to } +85^{\circ}\text{C}, 2.4 \text{ V} \le \text{V}_{DD} \le 5.5 \text{ V}, \text{ V}_{SS} = 0 \text{ V})$ (2/2)

Parameter	Symbol	Conditions	MIN.	TYP.	MAX.	Unit
USB operating current	IUSBH Note 11	 During USB communication operation under the following settings and conditions (V_{DD} = 5.0 V, T_A = +25°C): The internal power supply for the USB is used. X1 oscillation frequency (fx) = 12 MHz, PLL oscillation frequency (f_{PLL}) = 48 MHz The host controller (via two ports) is set to operate in full-speed mode with four pipes (end points) used simultaneously. (PIPE4: Bulk OUT transfer (64 bytes), PIPE5: Bulk IN transfer (64 bytes), PIPE6: Interrupt OUT transfer, PIPE7: Interrupt IN transfer). The USB ports (two ports) are individually connected to a peripheral function via a 0.5 m USB cable. 		9.0		mA
	IUSBF Note 11	 During USB communication operation under the following settings and conditions (V_{DD} = 5.0 V, T_A = +25°C): The internal power supply for the USB is used. X1 oscillation frequency (f_X) = 12 MHz, PLL oscillation frequency (f_{PLL}) = 48 MHz The function controller is set to operate in full-speed mode with four pipes (end points) used simultaneously. (PIPE4: Bulk OUT transfer (64 bytes), PIPE5: Bulk IN transfer (64 bytes), PIPE6: Interrupt OUT transfer, PIPE7: Interrupt IN transfer). The USB port (one port) is connected to the host device via a 0.5 m USB cable. 		2.5		mA
	ISUSP Note 12	 During suspended state under the following settings and conditions (V_{DD} = 5.0 V, T_A = +25°C): The function controller is set to full-speed mode (the UDP0 pin is pulled up). The internal power supply for the USB is used. The system is set to STOP mode (When the high-speed on-chip oscillator, high-speed system clock, and subsystem clock are stopped. When the watchdog timer is stopped.). The USB port (one port) is connected to the host device via a 0.5 m USB cable. 		240		μA

(Notes and Remarks are listed on the next page.)



Notes 1. Current flowing to VDD.

- 2. When high speed on-chip oscillator and high-speed system clock are stopped.
- 3. Current flowing only to the real-time clock (RTC) (excluding the operating current of the low-speed on-chip ocsillator and the XT1 oscillator). The supply current of the RL78 microcontrollers is the sum of the values of either IDD1 or IDD2, and IRTC, when the real-time clock operates in operation mode or HALT mode. When the low-speed on-chip oscillator is selected, IFIL should be added. IDD2 subsystem clock operation includes the operational current of the real-time clock.
- 4. Current flowing only to the 12-bit interval timer (excluding the operating current of the low-speed on-chip ocsillator and the XT1 oscillator). The supply current of the RL78 microcontrollers is the sum of the values of either IDD1 or IDD2, and IIT, when the 12-bit interval timer operates in operation mode or HALT mode. When the low-speed on-chip oscillator is selected, IFIL should be added.
- 5. Current flowing only to the watchdog timer (including the operating current of the low-speed on-chip oscillator). The supply current of the RL78 microcontrollers is the sum of IDD1, IDD2 or IDD3 and IWDT when the watchdog timer is in operation.
- 6. Current flowing only to the A/D converter. The supply current of the RL78 microcontrollers is the sum of IDD1 or IDD2 and IADC when the A/D converter operates in an operation mode or the HALT mode.
- **7.** Current flowing only to the LVD circuit. The current value of the RL78/G1C is the sum of IDD1, IDD2 or IDD3 and ILV1 when the LVD circuit operates in the Operating, HALT or STOP mode.
- 8. Current flowing only during data flash rewrite.
- 9. Current flowing only during self programming.
- 10. For shift time to the SNOOZE mode, see 19.3.3 SNOOZE mode in the RL78/G1C User's Manual: Hardware.
- **11.** Current consumed only by the USB module and the internal power supply for the USB.
- **12.** Includes the current supplied from the pull-up resistor of the UDP0 pin to the pull-down resistor of the host device, in addition to the current consumed by this MCU during the suspended state.

Remarks 1. fil: Low-speed on-chip oscillator clock frequency

- 2. fsub: Subsystem clock frequency (XT1 clock oscillation frequency)
- 3. fcLK: CPU/peripheral hardware clock frequency
- 4. Temperature condition of the TYP. value is $T_A = 25^{\circ}C$



2.4 AC Characteristics

2.4.1 Basic operation

(TA = -40 to +85°C, 2.4 V \leq VDD \leq 5.5 V, Vss = 0 V)

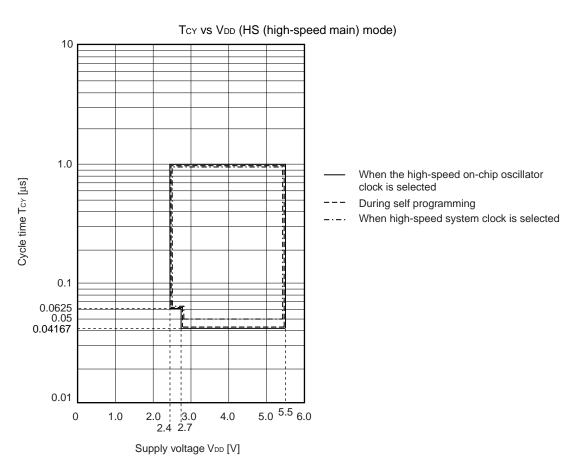
Items	Symbol		Condition	6	MIN.	TYP.	MAX.	Unit
Instruction cycle (minimum	Тсч	Main	HS	$2.7V\!\leq\!V_{DD}\!\leq\!5.5V$	0.04167		1	μs
instruction execution time)		system clock (f _{MAIN}) operation	(High-speed main) mode	2.4 V≤V _{DD} < 2.7 V	0.0625		1	μs
		Subsystem c	lock (fsua)	$2.4 \text{V} \le \text{V}_{\text{DD}} \le 5.5 \text{V}$	28.5	30.5	31.3	μs
		operation						
		In the self	HS	$2.7V\!\leq\!V_{DD}\!\leq\!5.5V$			1	μs
		programming mode	(High-speed main) mode	$2.4 V \le V_{DD} < 2.7 V$	0.0625		1	μs
External system clock frequency	fex	$2.7 \text{ V} \leq \text{V}_{\text{DD}} \leq$	≦ 5.5 V		1.0		20.0	MHz
		$2.4 \text{ V} \leq \text{V}_{\text{DD}}$ <	< 2.7 V		1.0		16.0	MHz
	fexs				32		35	kHz
External system clock input	texh, texl	$2.7 \text{ V} \leq V_{\text{DD}} \leq 5.5 \text{ V}$			24			ns
high-level width, low-level width		$2.4 \text{ V} \leq \text{V}_{\text{DD}} < 2.7 \text{ V}$			30			ns
	texhs, texls				13.7			μs
TI00 to TI03 input high-level width, low-level width	tтıн, tтı∟				1/fмск+10			ns
TO00 to TO03 output frequency	fтo	High-speed r	main 4.0 V	\leq Vdd \leq 5.5 V			12	MHz
		mode	2.7 V	\leq Vdd < 4.0 V			8	MHz
			2.4 V	$2.4 \text{ V} \leq \text{V}_{\text{DD}} < 2.7 \text{ V}$			4	MHz
PCLBUZ0, PCLBUZ1 output	f PCL	High-speed r	main 4.0 V	\leq Vdd \leq 5.5 V			16	MHz
frequency		mode	2.7 V	\leq Vdd < 4.0 V			8	MHz
			2.4 V	≤ Vdd < 2.7 V			4	MHz
Interrupt input high-level width, low-level width	tinth, tintl	INTP0 to INT INTP8, INTP		$2.4~\text{V} \leq \text{V}_{\text{DD}} \leq 5.5~\text{V}$				μs
Key interrupt input low-level width	t kr	KR0 to KR5	2.4 V	$2.4~V \leq V_{DD} \leq 5.5~V$				ns
RESET low-level width	trsl				10			μs

Remark fmck: Timer array unit operation clock frequency

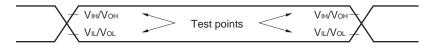
(Operation clock to be set by the CKS0n bit of timer mode register 0n (TMR0n). n: Channel number (n = 0 to 3))



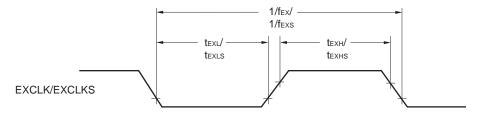
Minimum Instruction Execution Time during Main System Clock Operation



AC Timing Test Points

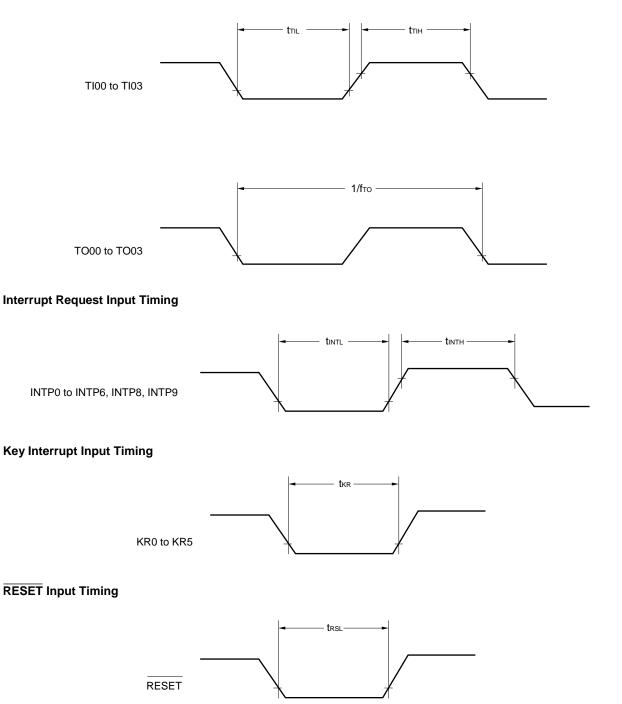


External System Clock Timing





TI/TO Timing





2.5 Peripheral Functions Characteristics

2.5.1 Serial array unit

(1) During communication at same potential (UART mode) (dedicated baud rate generator output) ($T_A = -40$ to +85°C, 2.4 V \leq V_{DD} \leq 5.5 V, V_{SS} = 0 V)

Parameter	Symbol	Conditions	MIN.	TYP.	MAX.	Unit
Transfer rate					fмск/6	bps
		Theoretical value of the maximum transfer rate $f_{MCK} = f_{CLK}$ ^{Note}			4.0	Mbps

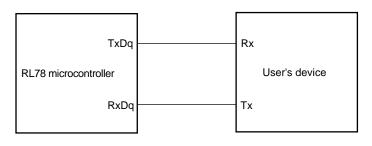
Note The maximum operating frequencies of the CPU/peripheral hardware clock (fcLK) are:

HS (high-speed main) mode: 24 MHz (2.7 V \leq VDD \leq 5.5 V)

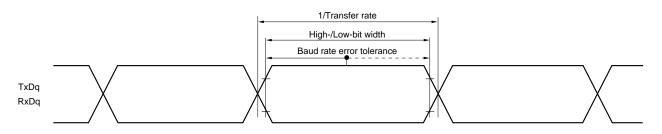
16 MHz (2.4 V \leq VDD \leq 5.5 V)

Caution Select the normal input buffer for the RxDq pin and the normal output mode for the TxDq pin by using port input mode register g (PIMg) and port output mode register g (POMg).

UART mode connection diagram (during communication at same potential)



UART mode bit width (during communication at same potential) (reference)



- **Remarks 1.** q: UART number (q = 0), g: PIM and POM number (g = 5)
 - 2. fmck: Serial array unit operation clock frequency

(Operation clock to be set by the CKSmn bit of serial mode register mn (SMRmn). m: Unit number,

n: Channel number (mn = 00))



(2) During communication at same potential (CSI mode) (master mode, SCKp... internal clock output, corresponding CSI00 only)

Parameter	Symbol	Conditions		MIN.	TYP.	MAX.	Unit
SCKp cycle time	tkCY1	tксү1 ≥ 2/fclк	$2.7~V \leq V_{\text{DD}} \leq 5.5~V$	83.3			ns
SCKp high-/low-level width	t кн1,	$4.0 \text{ V} \leq \text{V}_{\text{DD}} \leq$	5.5 V	tkcy1/2 - 7			ns
	t KL1	$2.7~V \leq V_{\text{DD}} \leq 5.5~V$		tксү1/2 – 10			ns
SIp setup time (to SCKp↑) Note 1	tsik1	$4.0 \text{ V} \leq \text{V}_{\text{DD}} \leq 5.5 \text{ V}$		23			ns
		$2.7 \text{ V} \leq \text{V}_{\text{DD}} \leq$	5.5 V	33			ns
SIp hold time (from SCKp↑) Note 2	tksi1	$2.7 \text{ V} \leq \text{V}_{\text{DD}} \leq$	5.5 V	10			ns
Delay time from SCKp↓ to SOp output ^{Note 3}	tkso1	C = 20 pF ^{Note}	3			10	ns

 $(T_A = -40 \text{ to } +85^{\circ}\text{C}, 2.7 \text{ V} \le \text{V}_{DD} \le 5.5 \text{ V}, \text{ V}_{SS} = 0 \text{ V})$

Notes 1. When DAPmn = 0 and CKPmn = 0, or DAPmn = 1 and CKPmn = 1. The SIp setup time becomes "to SCKp↓" when DAPmn = 0 and CKPmn = 1, or DAPmn = 1 and CKPmn = 0.

- 2. When DAPmn = 0 and CKPmn = 0, or DAPmn = 1 and CKPmn = 1. The SIp hold time becomes "from SCKp↓" when DAPmn = 0 and CKPmn = 1, or DAPmn = 1 and CKPmn = 0.
- 3. When DAPmn = 0 and CKPmn = 0, or DAPmn = 1 and CKPmn = 1. The delay time to SOp output becomes "from SCKp[↑]" when DAPmn = 0 and CKPmn = 1, or DAPmn = 1 and CKPmn = 0.
- **4.** C is the load capacitance of the SCKp and SOp output lines.
- Caution Select the normal input buffer for the SIp pin and the normal output mode for the SOp pin and SCKp pin by using port input mode register g (PIMg) and port output mode register g (POMg).
- **Remarks 1.** This specification is valid only when CSI00's peripheral I/O redirect function is not used.
 - p: CSI number (p = 00), m: Unit number (m = 0), n: Channel number (n = 0),
 g: PIM and POM numbers (g = 3, 5)
 - 3. fMCK: Serial array unit operation clock frequency

(Operation clock to be set by the CKSmn bit of serial mode register mn (SMRmn). m: Unit number,

n: Channel number (mn = 00))



Parameter	Symbol	C	conditions	MIN.	TYP.	MAX.	Unit
SCKp cycle time	tkcy1	tксү1 ≥ 4/fclк	$2.7~V \leq V_{\text{DD}} \leq 5.5~V$	167			ns
			$2.4~V \leq V_{\text{DD}} \leq 5.5~V$	250			ns
SCKp high-/low-level width	t кн1,	$4.0~V \leq V_{\text{DD}} \leq$	$4.0 \text{ V} \le \text{V}_{\text{DD}} \le 5.5 \text{ V}$ t				ns
	tĸ∟1	$2.7 \text{ V} \leq \text{V}_{\text{DD}} \leq 5.5 \text{ V}$		tkcy1/2 - 18			ns
		$2.4~V \leq V_{DD} \leq$	$2.4 \text{ V} \leq \text{V}_{\text{DD}} \leq 5.5 \text{ V}$				ns
SIp setup time (to SCKp↑) ^{Note 1}	tsik1	$4.0~\text{V} \leq \text{V}_{\text{DD}} \leq 5.5~\text{V}$		44			ns
		$2.7~V \leq V_{\text{DD}} \leq$	5.5 V	44			ns
		$2.4~V \leq V_{\text{DD}} \leq 5.5~V$		75			ns
SIp hold time (from SCKp \uparrow) ^{Note 2}	tksi1			19			ns
Delay time from SCKp↓ to SOp output ^{Note 3}	tkso1	C = 30 pF ^{Note 4}				25	ns

(3) During communication at same potential (CSI mode) (master mode, SCKp... internal clock output) ($T_A = -40$ to +85°C, 2.4 V < Vpp < 5.5 V, Vss = 0 V)

Notes 1. When DAPmn = 0 and CKPmn = 0, or DAPmn = 1 and CKPmn = 1. The SIp setup time becomes "to SCKp↓" when DAPmn = 0 and CKPmn = 1, or DAPmn = 1 and CKPmn = 0.

2. When DAPmn = 0 and CKPmn = 0, or DAPmn = 1 and CKPmn = 1. The SIp hold time becomes "from SCKp↓" when DAPmn = 0 and CKPmn = 1, or DAPmn = 1 and CKPmn = 0.

3. When DAPmn = 0 and CKPmn = 0, or DAPmn = 1 and CKPmn = 1. The delay time to SOp output becomes "from SCKp[↑]" when DAPmn = 0 and CKPmn = 1, or DAPmn = 1 and CKPmn = 0.

4. C is the load capacitance of the SCKp and SOp output lines.

Caution Select the normal input buffer for the SIp pin and the normal output mode for the SOp pin and SCKp pin by using port input mode register g (PIMg) and port output mode register g (POMg).

Remarks 1. p: CSI number (p = 00, 01), m: Unit number (m = 0), n: Channel number (n = 0, 1),

g: PIM and POM numbers (g = 0, 3, 5, 7)

2. fmck: Serial array unit operation clock frequency

(Operation clock to be set by the CKSmn bit of serial mode register mn (SMRmn). m: Unit number,

n: Channel number (mn = 00, 01))



Parameter	Symbol	Conc	litions	MIN.	TYP.	MAX.	Unit	
SCKp cycle time Note 5	t ксү2	$4.0~V \leq V_{\text{DD}} \leq 5.5~V$	20 MHz < fмск	8/fмск			ns	
			fмск ≤ 20 MHz	6/fмск			ns	
		$2.7~V \leq V_{\text{DD}} \leq 5.5~V$	16 MHz < fмск	8/fмск			ns	
			fмск ≤ 16 MHz	6/fмск			ns	
		$2.4~V \leq V_{DD} \leq 5.5~V$		6/fмск and 500			ns	
SCKp high-/low-level width	tкн2,	$4.0~V \leq V_{\text{DD}} \leq 5.5~V$		tксү2/2-7			ns	
	tĸl2	$2.7~V \leq V_{\text{DD}} \leq 5.5~V$		tксү2/2-8			ns	
		$2.4~V \leq V_{DD} \leq 5.5~V$		tксү2/2 – 18			ns	
SIp setup time	tsik2	$2.7~V \leq V_{\text{DD}} \leq 5.5~V$	$2.7~V \leq V_{\text{DD}} \leq 5.5~V$				ns	
(to SCKp↑) Note 1		$2.4~V \leq V_{\text{DD}} \leq 5.5~V$		1/fмск+30			ns	
SIp hold time	tKSI2	$2.7~V \leq V_{\text{DD}} \leq 5.5~V$		1/fмск+31			ns	
(from SCKp↑) Note 2		$2.4 \text{ V} \leq V_{\text{DD}} \leq 5.5 \text{ V}$		1/fмск+31			ns	
Delay time from SCKp↓ to	tkso2	C = 30 pF ^{Note 4}	$2.7~V \leq V_{\text{DD}} \leq 5.5~V$			2/fмск+44	ns	
SOp output Note 3				$2.4~V \leq V_{\text{DD}} \leq 5.5~V$			2/fмск+75	ns

(4) During communication at same potential (CSI mode) (slave mode, SCKp... external clock input) ($T_A = -40$ to +85°C, 2.4 V $\leq V_{DD} \leq 5.5$ V. Vss = 0 V)

Notes 1. When DAPmn = 0 and CKPmn = 0, or DAPmn = 1 and CKPmn = 1. The SIp setup time becomes "to SCKp↓" when DAPmn = 0 and CKPmn = 1, or DAPmn = 1 and CKPmn = 0.

2. When DAPmn = 0 and CKPmn = 0, or DAPmn = 1 and CKPmn = 1. The SIp hold time becomes "from SCKp↓" when DAPmn = 0 and CKPmn = 1, or DAPmn = 1 and CKPmn = 0.

- **3.** When DAPmn = 0 and CKPmn = 0, or DAPmn = 1 and CKPmn = 1. The delay time to SOp output becomes "from SCKp[↑]" when DAPmn = 0 and CKPmn = 1, or DAPmn = 1 and CKPmn = 0.
- 4. C is the load capacitance of the SOp output lines.
- 5. Transfer rate in the SNOOZE mode: MAX. 1 Mbps

Caution Select the normal input buffer for the SIp pin and SCKp pin and the normal output mode for the SOp pin by using port input mode register g (PIMg) and port output mode register g (POMg).

Remarks 1. p: CSI number (p = 00, 01), m: Unit number (m = 0),

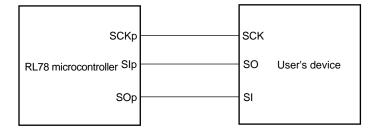
n: Channel number (n = 0, 1), g: PIM number (g = 0, 3, 5, 7)

2. fmck: Serial array unit operation clock frequency

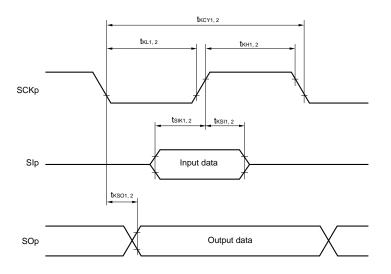
(Operation clock to be set by the CKSmn bit of serial mode register mn (SMRmn). m: Unit number, n: Channel number (mn = 00, 01))

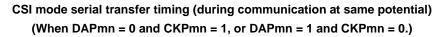


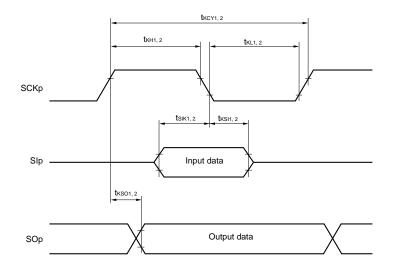
CSI mode connection diagram (during communication at same potential)



CSI mode serial transfer timing (during communication at same potential) (When DAPmn = 0 and CKPmn = 0, or DAPmn = 1 and CKPmn = 1.)







Remarks 1. p: CSI number (p = 00, 01)

2. m: Unit number, n: Channel number (mn = 00, 01)



$(T_A = -40 \text{ to } +85^{\circ}\text{C}, 2.4 \text{ V} \le \text{V}_{\text{DD}} \le 5.5 \text{ V}, \text{V}_{\text{S}})$	s = 0 V	•	1	T	
Parameter	Symbol	Conditions	MIN.	MAX.	Unit
SCLr clock frequency	fscL	$2.7 \text{ V} \leq \text{V}_{\text{DD}} \leq 5.5 \text{ V},$		1000 ^{Note 1}	kHz
		C_b = 50 pF, R_b = 2.7 k Ω			
		$2.4~V \leq V_{\text{DD}} \leq 5.5~V,$		400 Note 1	kHz
		$C_b = 100 \text{ pF}, R_b = 3 \text{ k}\Omega$			
		$2.4 \text{ V} \leq \text{V}_{\text{DD}} < 2.7 \text{ V},$		300 Note 1	kHz
		C_b = 100 pF, R_b = 5 k Ω			
Hold time when SCLr = "L"	tLOW	$2.7 \text{ V} \leq \text{V}_{\text{DD}} \leq 5.5 \text{ V},$	475		ns
		C_b = 50 pF, R_b = 2.7 k Ω			
		$2.4 \text{ V} \leq \text{V}_{\text{DD}} \leq 5.5 \text{ V},$	1150		ns
		$C_b = 100 \text{ pF}, R_b = 3 \text{ k}\Omega$			
		$2.4 \text{ V} \leq \text{V}_{\text{DD}} < 2.7 \text{ V},$	1550		ns
		C_b = 100 pF, R_b = 5 k Ω			
Hold time when SCLr = "H"	tнigн	$2.7 \text{ V} \leq \text{V}_{\text{DD}} \leq 5.5 \text{ V},$	475		ns
		$C_b = 50 \text{ pF}, R_b = 2.7 \text{ k}\Omega$			
		$2.4 \text{ V} \leq \text{V}_{\text{DD}} \leq 5.5 \text{ V},$	1150		ns
		C_b = 100 pF, R_b = 3 k Ω			
		$2.4 \text{ V} \leq \text{V}_{\text{DD}} < 2.7 \text{ V},$	1550		ns
		C_b = 100 pF, R_b = 5 k Ω			
Data setup time (reception)	tsu:dat	$2.7 \text{ V} \leq \text{V}_{\text{DD}} \leq 5.5 \text{ V},$	1/fмск + 85		ns
		$C_b = 50 \text{ pF}, R_b = 2.7 \text{ k}\Omega$	Note 2		
		$2.4 \text{ V} \leq \text{V}_{\text{DD}} \leq 5.5 \text{ V},$	1/fмск + 145		ns
		$C_b = 100 \text{ pF}, R_b = 3 \text{ k}\Omega$	Note 2		
		$2.4 \text{ V} \leq \text{V}_{\text{DD}} < 2.7 \text{ V},$	1/fмск + 230 Note 2		ns
		C_b = 100 pF, R_b = 5 k Ω	Note 2		
Data hold time (transmission)	thd:dat	$2.7 \text{ V} \leq \text{V}_{\text{DD}} \leq 5.5 \text{ V},$	0	305	ns
		C_b = 50 pF, R_b = 2.7 k Ω			
		$2.4~V \leq V_{\text{DD}} \leq 5.5~V,$	0	355	ns
		$C_b = 100 \text{ pF}, R_b = 3 \text{ k}\Omega$			
		$2.4 \text{ V} \leq \text{V}_{\text{DD}} < 2.7 \text{ V},$	0	405	ns
		C_b = 100 pF, R_b = 5 k Ω			

(5) During communication at same potential (simplified l^2C mode) (T₄ = -40 to +85°C 2.4 V \leq Vpp \leq 5.5 V. Vss = 0.V)

Notes 1. The value must also be equal to or less than $f_{MCK}/4$.

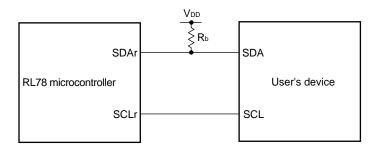
2. Set the fMCK value to keep the hold time of SCLr = "L" and SCLr = "H".

(Caution and Remarks are listed on the next page.)

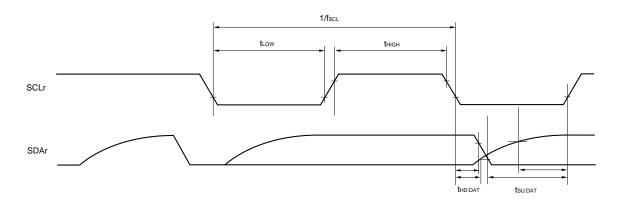


Caution Select the normal input buffer and the N-ch open drain output (VDD tolerance) mode for the SDAr pin and the normal output mode for the SCLr pin by using port input mode register g (PIMg) and port output mode register h (POMh).

Simplified I²C mode mode connection diagram (during communication at same potential)



Simplified I²C mode serial transfer timing (during communication at same potential)



Remarks 1. R_b[Ω]:Communication line (SDAr) pull-up resistance, C_b[F]: Communication line (SDAr, SCLr) load capacitance

2. r: IIC number (r = 00, 01), g: PIM number (g = 5), h: POM number (h = 3, 5)

3. fMCK: Serial array unit operation clock frequency

(Operation clock to be set by the CKSmn bit of serial mode register mn (SMRmn). m: Unit number (m

= 0), n: Channel number (n = 0, 1), mn = 00, 01)



(6) Communication at different potential (2.5 V, 3 V) (UART mode) (1/2)

(T _A = -40 to +85°C,	$2.4 V < V_{DD}$	< 5.5 V. Vss = 0 V	
(1	Z.T V D V D U .	<u> </u>	

Parameter	Symbol		Conditior	IS	MIN.	TYP.	MAX.	Unit
Transfer rate		reception	$4.0~V \leq V_{\text{DD}} \leq 5.5~V,$				fмск/6 ^{Note 1}	bps
			$2.7~V \leq V_b \leq 4.0~V$	Theoretical value of the maximum transfer rate $f_{MCK} = f_{CLK} N^{ote 2}$			4.0	Mbps
			$2.7 \text{ V} \leq \text{V}_{\text{DD}} < 4.0 \text{ V},$				fмск/6 ^{Note 1}	bps
			$2.3~V \leq V_b \leq 2.7~V$	Theoretical value of the maximum transfer rate $f_{MCK} = f_{CLK}^{Note 2}$			4.0	Mbps
			$2.4 \text{ V} \leq \text{V}_{\text{DD}} < 3.3 \text{ V},$				fмск/6 ^{Note 1}	bps
			$1.6~V \leq V_b \leq 2.0~V$	Theoretical value of the maximum transfer rate $f_{MCK} = f_{CLK} N^{\text{Note 2}}$			4.0	Mbps

Notes 1. Use it with $V_{DD} \ge V_b$.

2. The maximum operating frequencies of the CPU/peripheral hardware clock (fclk) are:

HS (high-speed main) mode: 24 MHz (2.7 V \leq V_{DD} \leq 5.5 V) 16 MHz (2.4 V \leq V_{DD} \leq 5.5 V)

Caution Select the TTL input buffer for the RxDq pin and the N-ch open drain output (VDD tolerance) mode for the TxDq pin by using port input mode register g (PIMg) and port output mode register g (POMg). For VIH and VIL, see the DC characteristics with TTL input buffer selected.

Remarks 1. Vb[V]: Communication line voltage

- **2.** q: UART number (q = 0), g: PIM and POM number (g = 5)
- 3. fmck: Serial array unit operation clock frequency

(Operation clock to be set by the CKSmn bit of serial mode register mn (SMRmn). m: Unit number,

n: Channel number (mn = 00)



(6) Communication at different potential (2.5 V, 3 V) (UART mode) (2/2) (T_A = -40 to $+85^{\circ}$ C. 2.4 V \leq Vpp \leq 5.5 V. Vss = 0 V)

Parameter	Symbol		Condi	tions	MIN.	TYP.	MAX.	Unit
Transfer rate		transmission	$4.0~V \leq V_{DD} \leq 5.5~V,$				Note 1	bps
			$2.7~V \leq V_b \leq 4.0~V$	Theoretical value of the maximum transfer rate $C_b = 50 \text{ pF}, R_b = 1.4 \text{ k}\Omega, V_b = 2.7 \text{ V}$			2.8 ^{Note 2}	Mbps
			$2.7~\text{V} \leq \text{V}_{\text{DD}} < 4.0~\text{V}$				Note 3	bps
			$2.3 \text{ V} \leq \text{V}_b \leq 2.7 \text{ V}$	Theoretical value of the maximum transfer rate $C_b = 50 \text{ pF}, R_b = 2.7 \text{ k}\Omega, V_b = 2.3 \text{ V}$			1.2 ^{Note 4}	Mbps
			$2.4 \text{ V} \le \text{V}_{\text{DD}} < 3.3 \text{ V}$				Notes 5, 6	bps
			$1.6~V \leq V_b \leq 2.0~V$	Theoretical value of the maximum transfer rate			0.43 Note 7	Mbps
				$C_b = 50 \text{ pF}, R_b = 5.5 \text{ k}\Omega, V_b = 1.6 \text{ V}$				

Notes 1. The smaller maximum transfer rate derived by using fMCK/6 or the following expression is the valid maximum transfer rate.

Expression for calculating the transfer rate when 4.0 V \leq V_{DD} \leq 5.5 V and 2.7 V \leq V_b \leq 4.0 V

Maximum transfer rate =

$$\frac{1}{\{-Cb \times Rb \times ln (1 - \frac{2.2}{Vb})\} \times 3}$$
 [bps]

Baud rate error (theoretical value) =

 $\frac{1}{\text{Transfer rate} \times 2} - \{-\text{Cb} \times \text{Rb} \times \ln(1 - \frac{2.2}{\text{Vb}})\}$ $\frac{1}{(\frac{1}{\text{Transfer rate}}) \times \text{Number of transferred bits}}$

- × 100 [%]

* This value is the theoretical value of the relative difference between the transmission and reception sides.

- 2. This value as an example is calculated when the conditions described in the "Conditions" column are met. Refer to Note 1 above to calculate the maximum transfer rate under conditions of the customer.
- **3.** The smaller maximum transfer rate derived by using fMCK/6 or the following expression is the valid maximum transfer rate.

Expression for calculating the transfer rate when 2.7 V \leq VDD < 4.0 V and 2.3 V \leq Vb \leq 2.7 V

Maximum transfer rate =
$$\frac{1}{\{-Cb \times Rb \times \ln (1 - \frac{2.0}{Vb})\} \times 3}$$
 [bps]

Baud rate error (theoretical value) =
$$\frac{\frac{1}{\text{Transfer rate} \times 2} - \{-\text{Cb} \times \text{Rb} \times \ln(1 - \frac{2.0}{\text{Vb}})\}}{(\frac{1}{\text{Transfer rate}}) \times \text{Number of transferred bits}} \times 100 \,[\%]$$

* This value is the theoretical value of the relative difference between the transmission and reception sides.

- **4.** This value as an example is calculated when the conditions described in the "Conditions" column are met. Refer to Note 3 above to calculate the maximum transfer rate under conditions of the customer.
- **5.** Use it with $V_{DD} \ge V_b$.



Notes 6. The smaller maximum transfer rate derived by using fMCK/6 or the following expression is the valid maximum transfer rate.

Expression for calculating the transfer rate when 2.4 V \leq VDD < 3.3 V and 1.6 V \leq Vb \leq 2.0 V

Maximum transfer rate =
$$\frac{1}{\{-Cb \times Rb \times ln (1 - \frac{1.5}{Vb})\} \times 3}$$
 [bps]

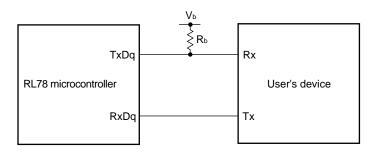
Baud rate error (theoretical value) =

$$\frac{\frac{1}{\text{Transfer rate} \times 2} - \{-\text{Cb} \times \text{Rb} \times \ln(1 - \frac{1.5}{\text{Vb}})\}}{(\frac{1}{\text{Transfer rate}}) \times \text{Number of transferred bits}} \times 100 [\%]$$

* This value is the theoretical value of the relative difference between the transmission and reception sides.7. This value as an example is calculated when the conditions described in the "Conditions" column are

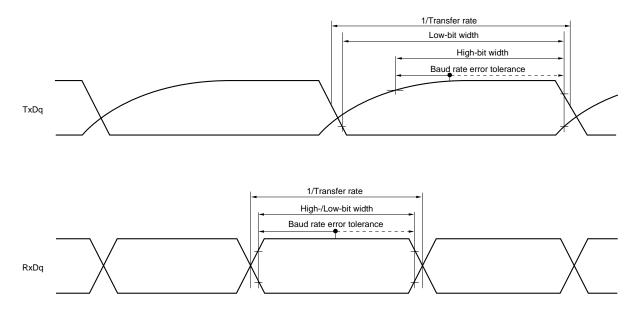
- met. Refer to Note 6 above to calculate the maximum transfer rate under conditions of the customer.
- Caution Select the TTL input buffer for the RxDq pin and the N-ch open drain output (V_{DD} tolerance) mode for the TxDq pin by using port input mode register g (PIMg) and port output mode register g (POMg). For V_H and V_L, see the DC characteristics with TTL input buffer selected.

UART mode connection diagram (during communication at different potential)





UART mode bit width (during communication at different potential) (reference)



- **Remarks 1.** R_b[Ω]:Communication line (TxDq) pull-up resistance, C_b[F]: Communication line (TxDq) load capacitance, V_b[V]: Communication line voltage
 - **2.** q: UART number (q = 0), g: PIM and POM number (g = 5)
 - 3. fmck: Serial array unit operation clock frequency

(Operation clock to be set by the CKSmn bit of serial mode register mn (SMRmn).

m: Unit number, n: Channel number (mn = 00))



(7) Communication at different potential (2.5 V, 3 V) (CSI mode) (master mode, SCKp... internal clock output, corresponding CSI00 only)

Parameter	Symbol		Conditions	MIN.	TYP.	MAX.	Unit
SCKp cycle time	tkcy1	tксү1 ≥ 2/fclк		200			ns
			$\label{eq:VD} \begin{split} & 2.7 \; V \leq V_{DD} < 4.0 \; V, \\ & 2.3 \; V \leq V_b \leq 2.7 \; V, \\ & C_b = 20 \; pF, \; R_b = 2.7 \; k\Omega \end{split}$	300			ns
SCKp high-level width	t кн1	$4.0~V \leq V_{DD} \leq$	5.5 V, 2.7 V \leq V _b \leq 4.0 V,	tксү1/2 – 50			ns
		C_b = 20 pF, R_b = 1.4 k Ω					
		$2.7 \text{ V} \leq \text{V}_{\text{DD}}$ <	4.0 V, 2.3 V \leq V _b \leq 2.7 V,	t ксү1/2 –			ns
		$C_b = 20 \text{ pF}, \text{ R}$	b = 2.7 kΩ	120			
SCKp low-level width	tĸ∟1	$4.0~V \leq V_{DD} \leq$	5.5 V, 2.7 V \leq V _b \leq 4.0 V,	tксү1/2 – 7			ns
		$C_b = 20 \text{ pF}, \text{ R}$	b = 1.4 kΩ				
		$2.7 \text{ V} \leq \text{V}_{\text{DD}}$ <	4.0 V, 2.3 V \leq V _b \leq 2.7 V,	tксү1/2 – 10			ns
		$C_{b} = 20 \text{ pF}, \text{ R}$	b = 2.7 kΩ				
SIp setup time	tsik1	$4.0~V \leq V_{DD} \leq$	5.5 V, 2.7 V \leq V _b \leq 4.0 V,	58			ns
(to SCKp↑) ^{Note 1}		$C_{b} = 20 \text{ pF}, \text{ R}$	_b = 1.4 kΩ				
		$2.7 \text{ V} \leq \text{V}_{\text{DD}}$ <	4.0 V, 2.3 V \leq V _b \leq 2.7 V,	121			ns
		$C_{b} = 20 \text{ pF}, \text{ R}$	b = 2.7 kΩ				
SIp hold time (from SCKp↑) ^{Note 1}	tksi1	$4.0~V \leq V_{DD} \leq$	5.5 V, 2.7 V \leq V _b \leq 4.0 V,	10			ns
		C _b = 20 pF, R	_b = 1.4 kΩ				
		$2.7 \text{ V} \leq \text{V}_{\text{DD}}$ <	4.0 V, 2.3 V \leq V _b \leq 2.7 V,	10			ns
		$C_{b} = 20 \text{ pF}, \text{ R}$	_b = 2.7 kΩ				
Delay time from SCKp \downarrow to	tĸso1	$4.0~V \leq V_{DD} \leq$	5.5 V, 2.7 V \leq V _b \leq 4.0 V,			60	ns
SOp output Note 1		$C_{b} = 20 \text{ pF}, \text{ R}$	_b = 1.4 kΩ				
		$2.7 \text{ V} \leq \text{V}_{\text{DD}}$ <	4.0 V, 2.3 V \leq V _b \leq 2.7 V,			130	ns
		$C_{b} = 20 \text{ pF}, \text{ R}$	_b = 2.7 kΩ				
SIp setup time	tsik1	$4.0~V \leq V_{DD} \leq$	5.5 V, 2.7 V \leq V _b \leq 4.0 V,	23			ns
(to SCKp↓) ^{Note 2}		$C_{b} = 20 \text{ pF}, \text{ R}$	_b = 1.4 kΩ				
		$2.7 \text{ V} \leq \text{V}_{\text{DD}}$ <	4.0 V, 2.3 V \leq V _b \leq 2.7 V,	33			ns
		$C_{b} = 20 \text{ pF}, \text{ R}$	b = 2.7 kΩ				
SIp hold time	tksi1	$4.0~V \leq V_{DD} \leq$	5.5 V, 2.7 V \leq V _b \leq 4.0 V,	10			ns
(from SCKp↓) ^{Note 2}		C _b = 20 pF, R	_b = 1.4 kΩ				
		$2.7 \text{ V} \leq \text{V}_{\text{DD}}$ <	4.0 V, 2.3 V \leq V _b \leq 2.7 V,	10			ns
		C _b = 20 pF, R	b = 2.7 kΩ				
Delay time from SCKp↑ to	tkso1	$4.0~V \leq V_{DD} \leq$	5.5 V, 2.7 V \leq V _b \leq 4.0 V,			10	ns
SOp output Note 2		C _b = 20 pF, R	_b = 1.4 kΩ				
		$2.7 \text{ V} \leq \text{V}_{\text{DD}}$ <	4.0 V, 2.3 V \leq V _b \leq 2.7 V,			10	ns
		C₀ = 20 pF, R	_b = 2.7 kΩ				

Notes 1. When DAPmn = 0 and CKPmn = 0, or DAPmn = 1 and CKPmn = 1.

2. When DAPmn = 0 and CKPmn = 1, or DAPmn = 1 and CKPmn = 0.

(Caution and Remark are listed on the next page.)



- Caution Select the TTL input buffer for the SIp pin and the N-ch open drain output (V_{DD} tolerance) mode for the SOp pin and SCKp pin by using port input mode register g (PIMg) and port output mode register g (POMg). For V_H and V_L, see the DC characteristics with TTL input buffer selected.
- **Remarks 1.** R_b[Ω]:Communication line (SCKp, SOp) pull-up resistance, C_b[F]: Communication line (SCKp, SOp) load capacitance, V_b[V]: Communication line voltage
 - p: CSI number (p = 00), m: Unit number (m = 0), n: Channel number (n = 0),
 g: PIM and POM number (g = 3, 5)
 - fmcκ: Serial array unit operation clock frequency
 (Operation clock to be set by the CKSmn bit of serial mode register mn (SMRmn).
 m: Unit number, n: Channel number (mn = 00)
 - 4. This value is valid only when CSI00's peripheral I/O redirect function is not used.



(8) Communication at different potential (1.8 V, 2.5 V, 3 V) (CSI mode) (master mode, SCKp... internal clock output) (1/2)

Parameter	Symbol		Conditions	MIN.	TYP.	MAX.	Unit
SCKp cycle time	tkcy1	tkcy1 ≥ 4/fclk	$\begin{array}{l} 4.0 \ V \leq V_{DD} \leq 5.5 \ V, \\ 2.7 \ V \leq V_b \leq 4.0 \ V, \\ C_b = 30 \ pF, \ R_b = 1.4 \ k\Omega \end{array}$	300			ns
			$\begin{array}{l} 2.7 \ V \leq V_{DD} < 4.0 \ V, \\ 2.3 \ V \leq V_b \leq 2.7 \ V, \\ C_b = 30 \ pF, \ R_b = 2.7 \ k\Omega \end{array}$	500			ns
			$\begin{array}{l} 2.4 \ V \leq V_{DD} < 3.3 \ V, \\ 2.4 \ V \leq V_b \leq 2.0 \ V, \\ C_b = 30 \ pF, \ R_b = 5.5 \ k\Omega \end{array}$	1150			ns
SCKp high-level width	tкнı	$\begin{array}{l} 4.0 \; V \leq V_{DD} \leq 5.5 \; V, \; 2.7 \; V \leq V_{b} \leq 4.0 \; V, \\ \\ \mathbf{C}_{b} = 30 \; pF, \; R_{b} = 1.4 \; k\Omega \end{array}$		tkcy1/2 - 75			ns
		$2.7 \text{ V} \le \text{V}_{\text{DD}} <$ $C_{\text{b}} = 30 \text{ pF}, \text{ H}$	 < 4.0 V, 2.3 V ≤ V_b ≤ 2.7 V, R_b = 2.7 kΩ 	tксү1/2 – 170			ns
		$\begin{array}{l} 2.4 \ V \leq V_{DD} < 3.3 \ V, \ 1.6 \ V \leq V_b \leq 2.0 \ V, \\ C_b = 30 \ pF, \ R_b = 5.5 \ k\Omega \end{array}$		tксү1/2 – 458			ns
SCKp low-level width	tĸ∟1	$4.0 \text{ V} \leq \text{V}_{\text{DD}} \leq C_{\text{b}} = 30 \text{ pF}, \text{ H}$	≤ 5.5 V, 2.7 V \leq Vb ≤ 4.0 V, Rb = 1.4 k\Omega	tксү1/2 – 12			ns
		$2.7 \text{ V} \leq \text{V}_{\text{DD}} <$ $C_{\text{b}} = 30 \text{ pF}, \text{ H}$	 < 4.0 V, 2.3 V ≤ V_b ≤ 2.7 V, R_b = 2.7 kΩ 	tксү1/2 – 18			ns
		$2.4 \text{ V} \leq \text{V}_{\text{DD}} <$ $C_{\text{b}} = 30 \text{ pF, H}$	< 3.3 V, 1.6 V ≤ V _b ≤ 2.0 V, R _b = 5.5 kΩ	tксү1/2 – 50			ns

 $(T_A = -40 \text{ to } +85^{\circ}\text{C}, 2.4 \text{ V} \le \text{V}_{DD} \le 5.5 \text{ V}, \text{ V}_{SS} = 0 \text{ V})$

Cautions 1. Select the TTL input buffer for the SIp pin and the N-ch open drain output (V_{DD} tolerance) mode for the SOp pin and SCKp pin by using port input mode register g (PIMg) and port output mode register g (POMg). For V_{IH} and V_{IL}, see the DC characteristics with TTL input buffer selected.

2. Use it with $V_{DD} \ge V_b$.

(Remarks are listed two pages after the next page.)



(8) Communication at different potential (1.8 V, 2.5 V, 3 V) (CSI mode) (master mode, SCKp... internal clock output) (2/2)

Parameter	Symbol	Conditions	MIN.	TYP.	MAX.	Unit
SIp setup time	tsik1	$4.0 \ \text{V} \leq \text{V}_{\text{DD}} \leq 5.5 \ \text{V}, \ 2.7 \ \text{V} \leq \text{V}_{\text{b}} \leq 4.0 \ \text{V}, \label{eq:VDD}$	81			ns
(to SCKp↑) ^{Note 1}		$C_{b}=30 \text{ pF}, \text{R}_{b}=1.4 \text{k}\Omega$				
		$2.7 \ V \leq V_{DD} < 4.0 \ V, \ 2.3 \ V \leq V_b \leq 2.7 \ V,$	177			ns
		$C_{b}=30 \text{ pF}, \text{R}_{b}=2.7 \text{k}\Omega$				
		$2.4 \ V \leq V_{\text{DD}} < 3.3 \ V, \ 1.6 \ V \leq V_{b} \leq 2.0 \ V^{\text{Note 3}},$	479			ns
		$C_{\rm b}=30~pF,~R_{\rm b}=5.5~k\Omega$				
SIp hold time	tksi1	$4.0 \ V \leq V_{DD} \leq 5.5 \ V, \ 2.7 \ V \leq V_b \leq 4.0 \ V,$	19			ns
(from SCKp↑) Note 1		C_b = 30 pF, R_b = 1.4 k Ω				
		$2.7 \ V \leq V_{DD} < 4.0 \ V, \ 2.3 \ V \leq V_b \leq 2.7 \ V,$	19			ns
		C_b = 30 pF, R_b = 2.7 k Ω				
		$2.4 \ V \leq V_{\text{DD}} < 3.3 \ V, \ 1.6 \ V \leq V_{b} \leq 2.0 \ V^{\text{Note 3}},$	19			ns
		C_b = 30 pF, R_b = 5.5 k Ω				
Delay time from SCKp↓ to	tkso1	$4.0 \ V \leq V_{\text{DD}} \leq 5.5 \ V, \ 2.7 \ V \leq V_{\text{b}} \leq 4.0 \ V,$			100	ns
SOp output Note 1		$C_{b}=30 \text{ pF}, \text{R}_{b}=1.4 \text{k}\Omega$				
		$2.7 \ V \leq V_{DD} < 4.0 \ V, \ 2.3 \ V \leq V_b \leq 2.7 \ V,$			195	ns
		C_b = 30 pF, R_b = 2.7 k Ω				
		$2.4 \ V \leq V_{\text{DD}} < 3.3 \ V, \ 1.6 \ V \leq V_{\text{b}} \leq 2.0 \ V^{\text{Note 3}},$			483	ns
		C_b = 30 pF, R_b = 5.5 k Ω				
SIp setup time	tsik1	$4.0 \ V \leq V_{\text{DD}} \leq 5.5 \ V, \ 2.7 \ V \leq V_{\text{b}} \leq 4.0 \ V,$	44			ns
(to SCKp↓) ^{Note 2}		C_b = 30 pF, R_b = 1.4 k Ω				
		$2.7 \ V \leq V_{DD} < 4.0 \ V, \ 2.3 \ V \leq V_b \leq 2.7 \ V,$	44			ns
		$C_{\rm b}=30~pF,~R_{\rm b}=2.7~k\Omega$				
		$2.4 \ V \leq V_{\text{DD}} < 3.3 \ V, \ 1.6 \ V \leq V_{b} \leq 2.0 \ V^{\text{Note 3}},$	110			ns
		C_b = 30 pF, R_b = 5.5 k Ω				
SIp hold time	tksi1	$4.0~V \leq V_{\text{DD}} \leq 5.5~V,~2.7~V \leq V_{\text{b}} \leq 4.0~V,$	19			ns
(from SCKp↓) Note 2		C_b = 30 pF, R_b = 1.4 k Ω				
		$2.7 \ V \leq V_{DD} < 4.0 \ V, \ 2.3 \ V \leq V_b \leq 2.7 \ V,$	19			ns
		$C_b=30 \text{ pF}, \text{R}_b=2.7 \text{k}\Omega$				
		$2.4 \ V \leq V_{\text{DD}} < 3.3 \ V, \ 1.6 \ V \leq V_{\text{b}} \leq 2.0 \ V^{\text{Note 3}},$	19			ns
		$C_b = 30 \text{ pF}, R_b = 5.5 \text{ k}\Omega$				
Delay time from SCKp↑ to	tkso1	$4.0 \ V \leq V_{DD} \leq 5.5 \ V, \ 2.7 \ V \leq V_b \leq 4.0 \ V,$			25	ns
SOp output Note 2		C_b = 30 pF, R_b = 1.4 k Ω				
		$2.7 \ V \leq V_{\text{DD}} < 4.0 \ V, \ 2.3 \ V \leq V_{\text{b}} \leq 2.7 \ V,$			25	ns
		C_b = 30 pF, R_b = 2.7 k Ω				
		$2.4 \ \text{V} \leq \text{V}_{\text{DD}} < 3.3 \ \text{V}, \ 1.6 \ \text{V} \leq \text{V}_{\text{b}} \leq 2.0 \ \text{V}^{\text{Note 3}},$			25	ns
		$C_b = 30 \text{ pF}, R_b = 5.5 \text{ k}\Omega$				

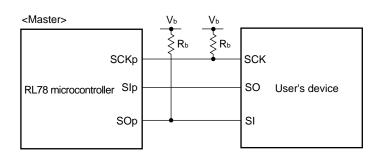
$(T_{A} = -40 +$	o ±820C	2 A V	< 5 5 V	Vss = 0 V)	
1 A = -40 t	0 +03°C.	Z.4 V	≤ э. э v.	. vss = u v)	

(Notes, Cautions and Remarks are listed on the next page.)



- **Notes 1.** When DAPmn = 0 and CKPmn = 0, or DAPmn = 1 and CKPmn = 1.
 - 2. When DAPmn = 0 and CKPmn = 1, or DAPmn = 1 and CKPmn = 0.
 - **3.** Use it with $V_{DD} \ge V_b$.
- Caution Select the TTL input buffer for the SIp pin and the N-ch open drain output (V_{DD} tolerance) mode for the SOp pin and SCKp pin by using port input mode register g (PIMg) and port output mode register g (POMg). For V_{IH} and V_{IL}, see the DC characteristics with TTL input buffer selected.

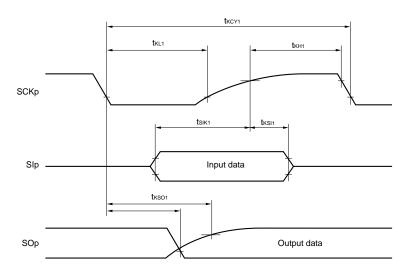
CSI mode connection diagram (during communication at different potential)



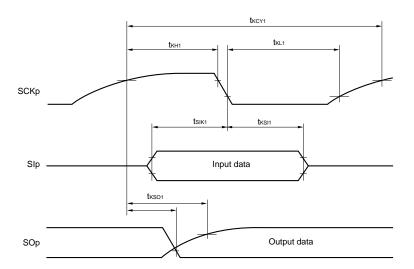
- **Remarks 1.** R_b[Ω]: Communication line (SCKp, SOp) pull-up resistance, C_b[F]: Communication line (SCKp, SOp) load capacitance, V_b[V]: Communication line voltage
 - p: CSI number (p = 00), m: Unit number , n: Channel number (mn = 00), g: PIM and POM number (g = 0, 3, 5, 7)
 - **3.** fMCK: Serial array unit operation clock frequency (Operation clock to be set by the CKSmn bit of serial mode register mn (SMRmn). m: Unit number, n: Channel number (mn = 00))
 - **4.** CSI01 cannot communicate at different potential. Use other CSI for communication at different potential.



CSI mode serial transfer timing (master mode) (during communication at different potential) (When DAPmn = 0 and CKPmn = 0, or DAPmn = 1 and CKPmn = 1.)



CSI mode serial transfer timing (master mode) (during communication at different potential) (When DAPmn = 0 and CKPmn = 1, or DAPmn = 1 and CKPmn = 0.)



- **Remarks 1.** p: CSI number (p = 00), m: Unit number, n: Channel number (mn = 00), g: PIM and POM number (g = 0, 3, 5, 7)
 - 2. CSI01 cannot communicate at different potential. Use other CSI for communication at different potential.



(9) Communication at different potential (1.8 V, 2.5 V, 3 V) (CSI mode) (slave mode, SCKp... external clock input)

Parameter	Symbol	С	onditions	MIN.	TYP.	MAX.	Unit
SCKp cycle time Note 1	t ксү2	$4.0 V \le V_{DD} \le 5.5 V$,	20 MHz < fмск ≤24 MHz	12/fмск			ns
		$2.7 V \le V_b \le 4.0 V$	8 MHz < fмск ≤20 MHz	10/fмск			ns
			4 MHz < fмск ≤ 8 MHz	8/f мск			ns
			fмск ≤4 MHz	6/fмск			ns
		$2.7 \text{ V} \le \text{V}_{\text{DD}} < 4.0 \text{ V},$	20 MHz < fмск ≤24 MHz	16/fмск			ns
		$2.3 V \le V_b \le 2.7 V$	16 MHz < fмск ≤20 MHz	14/fмск			ns
			8 MHz < fмск ≤ 16 MHz	12/fмск			ns
			4 MHz < fмск ≤ 8 MHz	8/fмск			ns
			fмск ≤4 MHz	6/fмск			ns
		$2.4 \text{ V} \leq \text{V}_{\text{DD}} < 3.3 \text{ V},$	20 MHz < fмск ≤24 MHz	36/f мск			ns
		$1.6~V\!\le\!V_b\!\le\!2.0~V^{\text{Note 2}}$	16 MHz < fмск ≤20 MHz	32/fмск			ns
			8 MHz < fмск ≤ 16 MHz	26/f мск			ns
			4 MHz < fмск ≤ 8 MHz	16/f мск			ns
			fмск ≤4 MHz	10/fмск			ns
SCKp high-/low-level width	tкн2, tкL2	$4.0 \text{ V} \leq \text{V}_{\text{DD}} \leq 5.5 \text{ V},$	$2.7~V \leq V_b \leq 4.0~V$	tксү2/2 – 12			ns
		$2.7 \text{ V} \le \text{V}_{\text{DD}} < 4.0 \text{ V},$	$2.3~V \leq V_b \leq 2.7~V$	tксү2/2 – 18			ns
		$2.4 \text{ V} \le \text{V}_{\text{DD}} < 3.3 \text{ V},$	$1.6~V \leq V_b \leq 2.0~V^{\text{Note 2}}$	tксү2/2 – 50			ns
SIp setup time (to SCKp↑) ^{Note 3}	tsik2	$4.0 \text{ V} \leq \text{V}_{\text{DD}} \leq 5.5 \text{ V},$	$2.7~V \leq V_b \leq 4.0~V$	1/fмск + 20			ns
		$2.7 \text{ V} \le \text{V}_{\text{DD}} < 4.0 \text{ V},$	$2.3~V \leq V_b \leq 2.7~V$	1/fмск + 20			ns
		$2.4 \text{ V} \le \text{V}_{\text{DD}} < 3.3 \text{ V},$	$1.6~V \leq V_b \leq 2.0~V^{\text{Note 2}}$	1/fмск + 30			ns
SIp hold time (from SCKp↑) ^{Note 4}	tksi2			1/fмск + 31			ns
Delay time from SCKp↓ to	tĸso2	$4.0 \text{ V} \leq \text{V}_{\text{DD}} \leq 5.5 \text{ V},$	$2.7~V \leq V_b \leq 4.0~V,$			2/fмск +	ns
SOp output Note 5		$C_b = 30 \text{ pF}, R_b = 1.4$	kΩ			120	
		$2.7 \text{ V} \le \text{V}_{\text{DD}} < 4.0 \text{ V},$	$2.3~V \leq V_b \leq 2.7~V,$			2/fмск +	ns
		$C_b = 30 \text{ pF}, R_b = 2.7$	'kΩ			214	
		$2.4 \text{ V} \le \text{V}_{\text{DD}} < 3.3 \text{ V},$	$1.6~V \leq V_{b} \leq 2.0~V^{\text{Note 2}},$			2/fмск +	ns
		$C_b = 30 \text{ pF}, R_b = 5.5$	δkΩ			573	

 $(T_A = -40 \text{ to } +85^{\circ}\text{C}, 2.4 \text{ V} \le \text{V}_{DD} \le 5.5 \text{ V}, \text{ V}_{SS} = 0 \text{ V})$

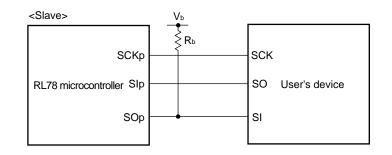
Notes 1. Transfer rate in the SNOOZE mode: MAX. 1 Mbps

- **2.** Use it with $V_{DD} \ge V_b$.
- 3. When DAPmn = 0 and CKPmn = 0, or DAPmn = 1 and CKPmn = 1. The SIp setup time becomes "to SCKp↓" when DAPmn = 0 and CKPmn = 1, or DAPmn = 1 and CKPmn = 0.
- 4. When DAPmn = 0 and CKPmn = 0, or DAPmn = 1 and CKPmn = 1. The SIp hold time becomes "from SCKp↓" when DAPmn = 0 and CKPmn = 1, or DAPmn = 1 and CKPmn = 0.
- **5.** When DAPmn = 0 and CKPmn = 0, or DAPmn = 1 and CKPmn = 1. The delay time to SOp output becomes "from SCKp[↑]" when DAPmn = 0 and CKPmn = 1, or DAPmn = 1 and CKPmn = 0.

(Caution and Remarks are listed on the next page.)

Caution Select the TTL input buffer for the SIp pin and the N-ch open drain output (V_{DD} tolerance) mode for the SOp pin and SCKp pin by using port input mode register g (PIMg) and port output mode register g (POMg). For V_H and V_L, see the DC characteristics with TTL input buffer selected.

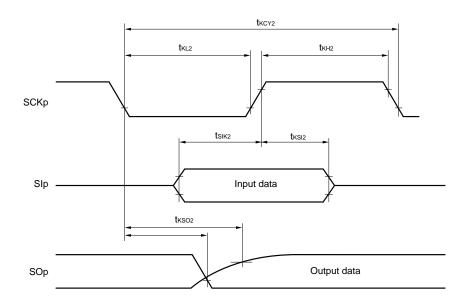
CSI mode connection diagram (during communication at different potential)

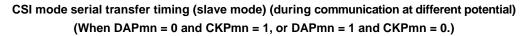


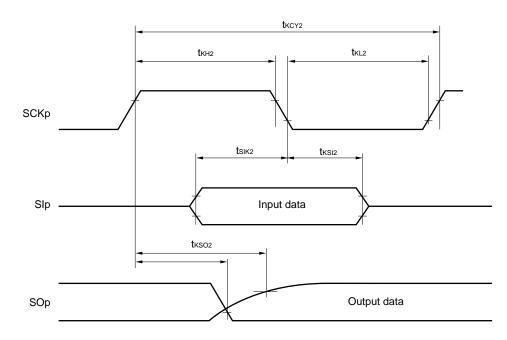
- **Remarks 1.** R_b[Ω]:Communication line (SOp) pull-up resistance, C_b[F]: Communication line (SOp) load capacitance, V_b[V]: Communication line voltage
 - 2. p: CSI number (p = 00), m: Unit number, n: Channel number (mn = 00), g: PIM and POM number (g = 0, 3, 5, 7)
 - fMCK: Serial array unit operation clock frequency
 (Operation clock to be set by the CKSmn bit of serial mode register mn (SMRmn).
 m: Unit number, n: Channel number (mn = 00))
 - **4.** CSI01 cannot communicate at different potential. Use other CSI for communication at different potential.



CSI mode serial transfer timing (slave mode) (during communication at different potential) (When DAPmn = 0 and CKPmn = 0, or DAPmn = 1 and CKPmn = 1.)







- **Remarks 1.** p: CSI number (p = 00), m: Unit number, n: Channel number (mn = 00), g: PIM and POM number (g = 0, 3, 5, 7)
 - **2.** CSI01 cannot communicate at different potential. Use other CSI for communication at different potential.



(10) Communication at different potential (1.8 V, 2.5 V, 3 V) (simplified I^2C mode) (1/2)

Parameter	Symbol	Conditions	MIN.	MAX.	Unit
SCLr clock frequency	fscL	$\begin{array}{l} 4.0 \; V \leq V_{DD} \leq 5.5 \; V, \\ 2.7 \; V \leq V_b \leq 4.0 \; V, \\ \mathbf{C}_b = 50 \; pF, \; R_b = 2.7 \; k\Omega \end{array}$		1000 ^{Note 1}	kHz
		$\begin{array}{l} 2.7 \ V \leq V_{DD} < 4.0 \ V, \\ 2.3 \ V \leq V_b < 2.7 \ V, \\ C_b = 50 \ pF, \ R_b = 2.7 \ k\Omega \end{array}$		1000 ^{Note 1}	kHz
				400 ^{Note 1}	kHz
		$\label{eq:VDD} \begin{array}{l} 2.7 \ V \leq V_{DD} < 4.0 \ V, \\ 2.3 \ V \leq V_{b} < 2.7 \ V, \\ \mathbf{C}_{b} = 100 \ pF, \ R_{b} = 2.7 \ k\Omega \end{array}$		400 ^{Note 1}	kHz
		$ \begin{array}{l} 2.4 \; V \leq V_{DD} < 3.3 \; V, \\ 1.6 \; V \leq V_b \leq 2.0 \; V^{\mbox{Note 2}}, \\ C_b = 100 \; pF, \; R_b = 5.5 \; k\Omega \end{array} $		300 ^{Note 1}	kHz
Hold time when SCLr = "L"	tLow		475		ns
		$\label{eq:VDD} \begin{array}{l} 2.7 \ V \leq V_{DD} < 4.0 \ V, \\ 2.3 \ V \leq V_b < 2.7 \ V, \\ C_b = 50 \ pF, \ R_b = 2.7 \ k\Omega \end{array}$	475		ns
			1150		ns
		$\label{eq:VDD} \begin{array}{l} 2.7 \ V \leq V_{DD} < 4.0 \ V, \\ 2.3 \ V \leq V_b < 2.7 \ V, \\ C_b = 100 \ p\text{F}, \ R_b = 2.7 \ k\Omega \end{array}$	1150		ns
		$ \begin{split} & 2.4 \; V \leq V_{DD} < 3.3 \; V, \\ & 1.6 \; V \leq V_{b} \leq 2.0 \; V^{\; \text{Note 2}}, \\ & C_{b} = 100 \; pF, \; R_{b} = 5.5 \; k\Omega \end{split} $	1550		ns
Hold time when SCLr = "H"	tніgн		245		ns
		$\label{eq:VDD} \begin{array}{l} 2.7 \; V \leq V_{DD} < 4.0 \; V, \\ 2.3 \; V \leq V_b < 2.7 \; V, \\ C_b = 50 \; pF, \; R_b = 2.7 \; k\Omega \end{array}$	200		ns
			675		ns
		$\begin{array}{l} 2.7 \ V \leq V_{DD} < 4.0 \ V, \\ 2.3 \ V \leq V_{b} < 2.7 \ V, \\ C_{b} = 100 \ pF, \ R_{b} = 2.7 \ k\Omega \end{array}$	600		ns
		$\begin{array}{l} 2.4 \; V \leq V_{DD} < 3.3 \; V, \\ 1.6 \; V \leq V_{b} \leq 2.0 \; V^{\text{Note 2}}, \\ C_{b} = 100 \; pF, \; R_{b} = 5.5 \; k\Omega \end{array}$	610		ns

(Notes, Caution and Remarks are listed on the next page.)



Parameter	Symbol	Conditions	MIN.	MAX.	Unit
Data setup time (reception)	tsu:dat		1/fмск + 135 Note 3		ns
			1/fмск + 135 Note 3		ns
			1/fмск + 190 Note 3		ns
		$\label{eq:VDD} \begin{array}{l} 2.7 \; V \leq V_{DD} < 4.0 \; V, \\ 2.3 \; V \leq V_b < 2.7 \; V, \\ C_b = 100 \; pF, \; R_b = 2.7 \; k\Omega \end{array}$	1/f _{MCK} + 190 Note 3		ns
			1/fмск + 190 Note 3		ns
Data hold time (transmission)	thd:dat		0	305	ns
			0	305	ns
			0	355	ns
		$\label{eq:VDD} \begin{array}{l} 2.7 \; V \leq V_{DD} < 4.0 \; V, \\ 2.3 \; V \leq V_b < 2.7 \; V, \\ C_b = 100 \; pF, \; R_b = 2.7 \; k\Omega \end{array}$	0	355	ns
		$\label{eq:VDD} \begin{split} & 2.4 \; V \leq V_{\text{DD}} < 3.3 \; V, \\ & 1.6 \; V \leq V_{b} \leq 2.0 \; V^{\text{Note 2}}, \\ & C_{b} = 100 \; \text{pF}, \; R_{b} = 5.5 \; \text{k}\Omega \end{split}$	0	405	ns

(10) Communication at different potential (1.8 V, 2.5 V, 3 V) (simplified I^2C mode) (2/2) (T₄ = -40 to +85°C 2.4 V < V_{DD} < 5.5 V, V_{SS} = 0.V)

Notes 1. The value must also be equal to or less than $f_{MCK}/4$.

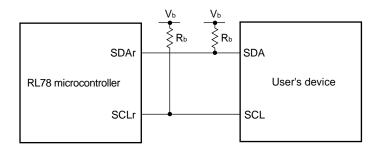
2. Use it with $V_{DD} \ge V_b$.

- 3. Set the fmck value to keep the hold time of SCLr = "L" and SCLr = "H".
- Caution Select the TTL input buffer and the N-ch open drain output (V_{DD} tolerance) mode for the SDAr pin and the N-ch open drain output (V_{DD} tolerance) mode for the SCLr pin by using port input mode register g (PIMg) and port output mode register g (POMg). For V_{IH} and V_{IL}, see the DC characteristics with TTL input buffer selected.

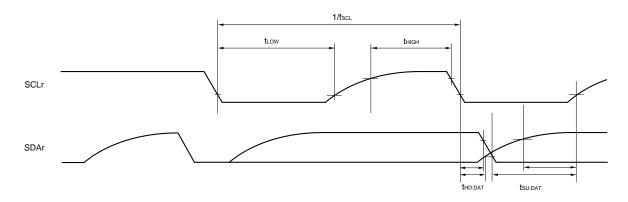
(**Remarks** are listed on the next page.)



Simplified I²C mode connection diagram (during communication at different potential)



Simplified I²C mode serial transfer timing (during communication at different potential)



- **Remarks 1.** R_b[Ω]:Communication line (SDAr, SCLr) pull-up resistance, C_b[F]: Communication line (SDAr, SCLr) load capacitance, V_b[V]: Communication line voltage
 - **2.** r: IIC number (r = 00), g: PIM, POM number (g = 0, 3, 5, 7)
 - 3. fMCK: Serial array unit operation clock frequency

(Operation clock to be set by the CKSmn bit of serial mode register mn (SMRmn). m: Unit number, n: Channel number (mn = 00)



2.5.2 Serial interface IICA

(1) I²C standard mode

 $(T_A = -40 \text{ to } +85^{\circ}\text{C}, 2.4 \text{ V} \le \text{V}_{\text{DD}} \le 5.5 \text{ V}, \text{V}_{\text{SS}} = 0 \text{ V})$

Parameter	Symbol	Conditio	ons	HS (high-spee	ed main) mode	Unit
				MIN.	MAX.	
SCLA0 clock frequency	fsc∟	Standard mode: fc⊥k≥ 1 MHz	$2.7~V \leq V_{\text{DD}} \leq 5.5~V$	0	100	kHz
			$2.4~V \leq V_{\text{DD}} \leq 5.5~V$	0	100	kHz
Setup time of restart condition	tsu:sta	$2.7~V \leq V_{\text{DD}} \leq 5.5~V$		4.7		μs
		$2.4~V \leq V_{\text{DD}} \leq 5.5~V$		4.7		μs
Hold time ^{Note 1}	thd:sta	$2.7~V \leq V_{\text{DD}} \leq 5.5~V$		4.0		μs
		$2.4~V \leq V_{\text{DD}} \leq 5.5~V$		4.0		μs
Hold time when SCLA0 = "L"	tLOW	$2.7 \text{ V} \leq V_{DD} \leq 5.5 \text{ V}$		4.7		μs
		$2.4~V \leq V_{\text{DD}} \leq 5.5~V$		4.7		μs
Hold time when SCLA0 = "H"	tніgн	$2.7 \text{ V} \leq V_{\text{DD}} \leq 5.5 \text{ V}$		4.0		μs
		$2.4 \text{ V} \leq \text{V}_{\text{DD}} \leq 5.5 \text{ V}$		4.0		μs
Data setup time (reception)	tsu:dat	$2.7 \text{ V} \leq \text{V}_{\text{DD}} \leq 5.5 \text{ V}$		250		μs
		$2.4~V \leq V_{\text{DD}} \leq 5.5~V$		250		μs
Data hold time	thd:dat	$2.7~V \leq V_{\text{DD}} \leq 5.5~V$		0	3.45	μs
(transmission) ^{Note 2}		$2.4~V \leq V_{\text{DD}} \leq 5.5~V$		0	3.45	μs
Setup time of stop condition	tsu:sto	$2.7~V \leq V_{\text{DD}} \leq 5.5~V$		4.0		μs
		$2.4~V \leq V_{\text{DD}} \leq 5.5~V$	4.0		μs	
Bus-free time	t BUF	$2.7~V \le V_{\text{DD}} \le 5.5~V$	4.7		μs	
		$2.4 \text{ V} \leq V_{\text{DD}} \leq 5.5 \text{ V}$		4.7		μs

Notes 1. The first clock pulse is generated after this period when the start/restart condition is detected.

2. The maximum value (MAX.) of the:DAT is during normal transfer and a wait state is inserted in the ACK (acknowledge) timing.

- Caution The values in the above table are applied even when bit 1 (PIOR1) in the peripheral I/O redirection register (PIOR) is 1. At this time, the pin characteristics (IOH1, IOL1, VOH1, VOL1) must satisfy the values in the redirect destination.
- **Remark** The maximum value of Cb (communication line capacitance) and the value of Rb (communication line pull-up resistor) at that time in each mode are as follows.

Standard mode: $C_b = 400 \text{ pF}, R_b = 2.7 \text{ k}\Omega$



(2) I²C fast mode

$(T_A = -40 \text{ to } +85^{\circ}\text{C}, 2.4 \text{ V} \le \text{V}_{DD} \le 5.5 \text{ V}, \text{ V}_{SS} = 0 \text{ V})$

Parameter	Symbol	Conditio	ons	HS (high-spee	ed main) Mode	Unit
				MIN.	MAX.	
SCLA0 clock frequency	fscl	Fast mode: fclk ≥ 3.5 MHz	$2.7~V \leq V_{\text{DD}} \leq 5.5~V$	0	400	kHz
			$2.4~V \leq V_{\text{DD}} \leq 5.5~V$	0	400	kHz
Setup time of restart condition	tsu:sta	$2.7~V \leq V_{\text{DD}} \leq 5.5~V$		0.6		μs
		$2.4~V \leq V_{\text{DD}} \leq 5.5~V$		0.6		μs
Hold time ^{Note 1}	thd:STA	$2.7~V \leq V_{\text{DD}} \leq 5.5~V$		0.6		μs
		$2.4~V \leq V_{\text{DD}} \leq 5.5~V$	0.6		μs	
Hold time when SCLA0 = "L"	tLOW	$2.7 \text{ V} \leq V_{\text{DD}} \leq 5.5 \text{ V}$		1.3		μs
		$2.4 \text{ V} \leq V_{\text{DD}} \leq 5.5 \text{ V}$		1.3		μs
Hold time when SCLA0 = "H"	tнigн	$2.7~V \leq V_{\text{DD}} \leq 5.5~V$	0.6		μs	
		$2.4~V \leq V_{\text{DD}} \leq 5.5~V$	0.6		μs	
Data setup time (reception)	tsu:dat	$2.7~V \leq V_{\text{DD}} \leq 5.5~V$	100		ns	
		$2.4~V \leq V_{\text{DD}} \leq 5.5~V$		100		ns
Data hold time	thd:dat	$2.7~V \leq V_{\text{DD}} \leq 5.5~V$		0	0.9	μs
(transmission) ^{Note 2}		$2.4~V \leq V_{\text{DD}} \leq 5.5~V$		0	0.9	μs
Setup time of stop condition	tsu:sto	$2.7~V \leq V_{\text{DD}} \leq 5.5~V$		0.6		μs
		$2.4~V \leq V_{\text{DD}} \leq 5.5~V$	0.6		μs	
Bus-free time	-free time t _{BUF} 2.7 V ≤ V _{DD} ≤ 5.5 V			1.3		μs
		$2.4~V \leq V_{\text{DD}} \leq 5.5~V$		1.3		μs

Notes 1. The first clock pulse is generated after this period when the start/restart condition is detected.

2. The maximum value (MAX.) of tHD:DAT is during normal transfer and a wait state is inserted in the ACK (acknowledge) timing.

- Caution The values in the above table are applied even when bit 1 (PIOR1) in the peripheral I/O redirection register (PIOR) is 1. At this time, the pin characteristics (IOH1, IOL1, VOH1, VOL1) must satisfy the values in the redirect destination.
- **Remark** The maximum value of Cb (communication line capacitance) and the value of Rb (communication line pull-up resistor) at that time in each mode are as follows.

Fast mode: $C_b = 320 \text{ pF}, R_b = 1.1 \text{ k}\Omega$



(3) I²C fast mode plus

($T_{A} = -40 \text{ to}$	+85°C. 2	.4 V <	VDD < 5.5	V, Vss = 0 V)	
	14 - 4010	+00 O, Z		100 - 0.0	$v_{1}, v_{23} = 0 v_{1}$	

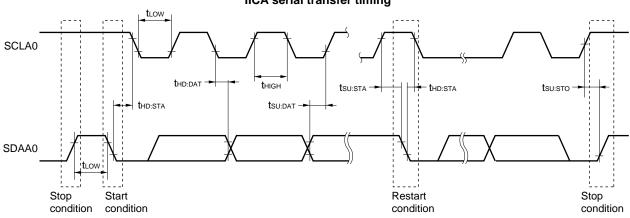
Parameter	Symbol	Conditi	ons	HS (high-spee	ed main) Mode	Unit
				MIN.	MAX.	
SCLA0 clock frequency	fscl	Fast mode plus:	$2.7~V \leq V_{\text{DD}} \leq 5.5~V$	0	1000	kHz
		fc∟k ≥ 10 MHz				
Setup time of restart condition	tsu:sta	$2.7 \text{ V} \leq \text{V}_{\text{DD}} \leq 5.5 \text{ V}$		0.26		μs
Hold time ^{Note 1}	thd:sta	$2.7~V \leq V_{\text{DD}} \leq 5.5~V$	$2.7 \text{ V} \le \text{V}_{\text{DD}} \le 5.5 \text{ V}$			μs
Hold time when SCLA0 = "L"	tLOW	$2.7~V \leq V_{\text{DD}} \leq 5.5~V$		0.5		μs
Hold time when SCLA0 = "H"	tніgн	$2.7~V \leq V_{\text{DD}} \leq 5.5~V$		0.26		μs
Data setup time (reception)	tsu:dat	$2.7~V \leq V_{\text{DD}} \leq 5.5~V$		50		ns
Data hold time (transmission) ^{Note 2}	thd:dat	$2.7~V \leq V_{DD} \leq 5.5~V$		0	0.45	μs
Setup time of stop condition	tsu:sto	$2.7~V \leq V_{\text{DD}} \leq 5.5~V$		0.26		μs
Bus-free time	t BUF	$2.7~V \leq V_{\text{DD}} \leq 5.5~V$		0.5		μs

Notes 1. The first clock pulse is generated after this period when the start/restart condition is detected.

2. The maximum value (MAX.) of the during normal transfer and a wait state is inserted in the ACK (acknowledge) timing.

- Caution The values in the above table are applied even when bit 1 (PIOR1) in the peripheral I/O redirection register (PIOR) is 1. At this time, the pin characteristics (IOH1, IOL1, VOH1, VOL1) must satisfy the values in the redirect destination.
- **Remark** The maximum value of Cb (communication line capacitance) and the value of Rb (communication line pull-up resistor) at that time in each mode are as follows.

Fast mode plus: $C_b = 120 \text{ pF}, R_b = 1.1 \text{ k}\Omega$



IICA serial transfer timing



2.5.3 USB

(1) Electrical specifications

(TA = -40 to +85°C, 3.0 V \leq UVDD \leq 3.6 V, 3.0 V \leq VDD \leq 5.5 V, Vss = 0 V)

	Parameter	Symbol	Conditions	MIN.	TYP.	MAX.	Unit
UVdd	UV _{DD} input voltage characteristic	UVdd	$ V_{\text{DD}} = 3.0 \text{ to } 5.5 \text{ V}, \text{PXXCON} = 1, \\ VDDUSEB = 0 (UV_{\text{DD}} \leq V_{\text{DD}}) $	3.0	3.3	3.6	V
	UV _{DD} output voltage characteristic	UVdd	$V_{DD} = 4.0$ to 5.5 V, PXXCON = VDDUSEB = 1	3.0	3.3	3.6	V
UVBUS	UV _{BUS} input voltage characteristic	UV _{BUS}	Function	4.35 (4.02 ^{Note})	5.00	5.25	V
			Host	4.75	5.00	5.25	V

Note Value of instantaneous voltage

$(T_A = -40 \text{ to } +85^{\circ}\text{C}, 3.0 \text{ V} \le U\text{V}_{DD} \le 3.6 \text{ V}, 3.0 \text{ V} \le \text{V}_{DD} \le 5.5 \text{ V}, \text{V}_{SS} = 0 \text{ V})$

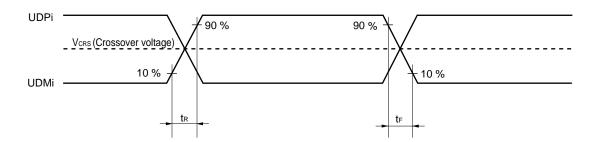
Par	rameter		Symbol	Conditions	MIN.	TYP.	MAX.	Unit
UDPi/UDMi	Input vol	tage	Vih		2.0			V
pins input characteristic			VIL				0.8	V
(FS/LS receiver)		Difference input sensitivity		UDP voltage – UDM voltage	0.2			V
	Difference common mode range		Vсм		0.8		2.5	V
UDPi/UDMi	Output v	oltage	Vон	Іон = -200 <i>µ</i> А	2.8		3.6	V
pins output characteristic			Vol	loL = 2.4 mA	0		0.3	V
(FS driver)	Transi-ti	Rising	t FR	Rising: From 10% to 90 % of amplitude, Falling: From 90% to 10 % of	4		20	ns
	on time	Falling	tff		4		20	ns
	Matching (TFR/TFF)		VFRFM	amplitude, CL = 50 pF	90		111.1	%
	Crossover voltage		VFCRS		1.3		2.0	V
	Output Impedance		Zdrv	UV _{DD} voltage = 3.3 V, Pin voltage = 1.65 V	28		44	Ω
UDPi/UDMi	Output v	oltage	Vон		2.8		3.6	V
pins output characteristic			Vol		0		0.3	V
(LS driver)	Transi-ti	Rising	tlr	Rising: From 10% to 90 % of amplitude, Falling: From 90% to 10 % of	75		300	ns
· · ·	on time	Falling	t∟F		75		300	ns
	Matching (TFR/TFF) Note		VLTFM	amplitude, CL = 200 to 600 pF	80		125	%
	Crossover voltage		VLCRS	When the host controller function is selected: The UDMi pin (i = 0, 1) is pulled up via 1.5 k Ω . When the function controller function is selected: The UDP0 and UDM0 pins are individually pulled down via 15 k Ω	1.3		2.0	V
UDPi/UDMi	Pull-dow	n resistor	Rpd		14.25		24.80	kΩ
pins pull-up, pull-down	Pull-up resistor	Idle	Rpui		0.9		1.575	kΩ
	(i = 0 only)	Recep-t ion	Rpua		1.425		3.09	kΩ
UVBUS	UV _{BUS} pu resistor	III-down	Rvbus	UV _{BUS} voltage = 5.5 V		1000		kΩ
	UV _{BUS} in	out	Vih		3.20			V
	voltage		VIL				0.8	V

Note Excludes the first signal transition from the idle state.

Remark i = 0, 1



Timing of UDPi and UDMi



(2) BC standard

$(T_A = -40 \text{ to } +85^{\circ}C, 3.0 \text{ V} \le UV_{DD} \le 3.6 \text{ V}, 3.0 \text{ V} \le V_{DD} \le 5.5 \text{ V}, \text{ Vss} = 0 \text{ V})$

	Parameter	Symbol	Conditions	MIN.	TYP.	MAX.	Unit
USB	UDPi sink current	DP_SINK		25		175	μA
standard BC1.2	UDMi sink current	Idm_sink		25		175	μA
501.2	DCD source current	IDP_SRC		7		13	μA
	Dedicated charging port resistor	Rdcp_dat	0 V < UDP/UDM voltage < 1.0 V			200	Ω
	Data detection voltage	VDAT_REF		0.25		0.4	V
	UDPi source voltage VDP_SRC		Output current 250 µA	0.5		0.7	V
	UDMi source voltage	Vdm_src	Output current 250 µA	0.5		0.7	V

Remark i = 0, 1



Par	ameter		Symbol	Conditions	MIN.	TYP.	MAX.	Unit
UDPi output	VDSELi	1000	VP20		38	40	42	% UV _{BUS}
voltage	[3:0]	1001	V _{P27}		51.6	53.6	55.6	% UV _{BUS}
(UV _{BUS} divider ratio)	(i = 0, 1)	1010	V _{P20}		38	40	42	% UV _{BUS}
• VDOUEi = 1		1100	V _{P33}		60	66	72	% UVвus
UDMi output	VDSELi	1000	V _{M20}		38	40	42	% UV _{BUS}
voltage	/ _{BUS} divider $(i = 0, 1)$	1001	V _{M20}		38	40	42	% UV _{BUS}
(UVBUS divider ratio)		1010	V _{M27}		51.6	53.6	55.6	% UV _{BUS}
• VDOUEi = 1		1100	Vмзз		60	66	72	% UV _{BUS}
UDPi	VDSELi	1000	VHDETP_UP0	The rise of pin voltage detection voltage	56.2			% UV _{BUS}
comparing Note 1 voltage	[3:0]		VHDETP_DWN0	The fall of pin voltage detection voltage			29.4	% UV _{BUS}
(UVBUS divider	/BUS divider	1001	VHDETP_UP1	The rise of pin voltage detection voltage	60.5			% UV _{BUS}
ratio)			VHDETP_DWN1	The fall of pin voltage detection voltage			45.0	% UV _{BUS}
• VDOUEi = 1		1010	VHDETP_UP2	The rise of pin voltage detection voltage	56.2			% UV _{BUS}
• CUSDETEi = 1	Ei = 1		VHDETP_DWN2	The fall of pin voltage detection voltage			29.4	% UV _{BUS}
UDMi	mparing tage Note 1 [3:0] (i = 0, 1)	ELi 1000	VHDETM_UP0	The rise of pin voltage detection voltage	56.2			% UV _{BUS}
comparing Note 1			VHDETM_DWN0	The fall of pin voltage detection voltage			29.4	% UV _{BUS}
Voltage (UV _{BUS} divider		1001	VHDETM_UP1	The rise of pin voltage detection voltage	56.2			% UV _{BUS}
ratio)			VHDETM_DWN1	The fall of pin voltage detection voltage			29.4	% UV _{BUS}
• VDOUEi = 1		1010	VHDETM_UP2	The rise of pin voltage detection voltage	60.5			% UV _{BUS}
• CUSDETEi = 1			VHDETM_DWN2	The fall of pin voltage detection voltage			45.0	% UV _{BUS}
UDPi pull-up de Note 2	etection	1000	RHDET_PULL	In full-speed mode, the power supply			1.575	kΩ
		1001		voltage range of pull-up resistors				
Connect detect	unction	1010		connected to the USB function module is between 3.0 V and 3.6 V.				
(pull-up resisto			_					
UDMi pull-up d Note 2	etection	1000	RHDET_PULL	In low-speed mode, the power supply voltage range of pull-up resistors			1.575	kΩ
Connect detect	tion with	1001		connected to the USB function				
the low-speed	(pull-up	1010		module is between 3.0 V and 3.6 V.				
resistor)								
UDMi sink curr detection Note 2	ent 2	1000	IHDET_SINK		25			μA
Connect detect		1001						
the BC1.2 porta		1010						
device (sink res	sistor)							

(3) BC option standard (Host)

Notes 1. If the voltage output from UDPi or UDMi (i = 0, 1) exceeds the range of the MAX and MIN values prescribed in this specification, DPCUSDETi (bit 8) and DMCUSDETi (bit 9) of the USBBCOPTi register are set to 1.

If the pull-up resistance or sink current prescribed in this specification is applied to UDPi or UDMi (i = 0, 1), DPCUSDETi (bit 8) and DMCUSDETi (bit 9) of the USBBCOPTi register are set to 1.

Remark i = 0, 1



Parameter Symbol Conditions MIN. TYP. MAX. Unit UDPi/UDMi VDSELi 0000 **V**DDET0 27 32 37 % UV_{BUS} [3:0] input 0001 % UV_{BUS} VDDET1 29 34 39 reference (i = 0)0010 37 % UV_{BUS} VDDET2 32 42 voltage (UVBUS divider 0011 Vddet3 35 40 45 % UV_{BUS} ratio) 0100 38 43 48 % UV_{BUS} VDDET4 • VDOUEi = 0 0101 46 % UV_{BUS} Vddet5 41 51 (i = 0)) 0110 VDDET6 44 49 54 % UV_{BUS} 0111 VDDET7 47 52 57 % UV_{BUS} Vddet8 1000 51 56 61 % UV_{BUS} 1001 Vddet9 55 60 65 % UV_{BUS} 1010 VDDET10 % UV_{BUS} 59 64 69 % UV_{BUS} 1011 VDDET11 63 68 73 1100 VDDET12 67 72 77 % UV_{BUS} 1101 VDDET13 71 76 81 % UV_{BUS} % UV_{BUS} 1110 VDDET14 75 80 85 % UV_{BUS} 1111 VDDET15 79 84 89

(4) BC option standard (Function)



2.6 Analog Characteristics

2.6.1 A/D converter characteristics

Classification of A/D converter characteristics

Input channel		Reference Voltage							
	Reference voltage (+) = AVREFP Reference voltage (-) = AVREFM	Reference voltage (+) = VDD Reference voltage (-) = Vss	Reference voltage (+) = VBGR Reference voltage (-) = AVREFM						
ANI0 to ANI7	Refer to 2.6.1 (1).	Refer to 2.6.1 (3).	Refer to 2.6.1 (4).						
ANI16, ANI17, ANI19	Refer to 2.6.1 (2).								
Internal reference voltage Temperature sensor output voltage	Refer to 2.6.1 (1) .		_						

(1) When AVREF (+) = AVREFP/ANIO (ADREFP1 = 0, ADREFP0 = 1), reference voltage (-) = AVREFM/ANI1 (ADREFM = 1), target pin: ANI2 to ANI7, internal reference voltage, and temperature sensor output voltage

 $(T_A = -40 \text{ to } +85^{\circ}\text{C}, 2.4 \text{ V} \le \text{AV}_{REFP} \le \text{V}_{DD} \le 5.5 \text{ V}, \text{V}_{SS} = 0 \text{ V}, \text{Reference voltage (+)} = \text{AV}_{REFP}, \text{Reference voltage (-)} = \text{AV}_{REFM} = 0 \text{ V})$

Parameter	Symbol	Cond	itions	MIN.	TYP.	MAX.	Unit
Resolution	Res			8		10	bit
Overall error ^{Note 1}	AINL	10-bit resolution AV _{REFP} = V _{DD} ^{Note 3}	$2.4 \text{ V} \leq \text{VDD} \leq 5.5 \text{ V}$		1.2	±3.5	LSB
Conversion time	t CONV	10-bit resolution	$3.6 \text{ V} \leq \text{V}\text{DD} \leq 5.5 \text{ V}$	2.125		39	μs
		Target pin: ANI2 to ANI7	$2.7~V \leq V_{DD} \leq 5.5~V$	3.1875		39	μs
			$2.4~V \leq V \text{DD} \leq 5.5~V$	17		39	μs
		10-bit resolution Target pin: Internal reference voltage, and temperature sensor output voltage (HS (high-speed main) mode)	$3.6~\text{V} \leq \text{Vdd} \leq 5.5~\text{V}$	2.375		39	μs
			$2.7~V \leq V_{DD} \leq 5.5~V$	3.5625		39	μs
			$2.4 \text{ V} \le \text{Vdd} \le 5.5 \text{ V}$	17		39	μs
Zero-scale error ^{Notes 1, 2}	EZS	10-bit resolution AV _{REFP} = V _{DD} ^{Note 3}	$2.4 \text{ V} \le \text{Vdd} \le 5.5 \text{ V}$			±0.25	%FSR
Full-scale error ^{Notes 1, 2}	EFS	10-bit resolution AV _{REFP} = V _{DD} ^{Note 3}	$2.4 \text{ V} \le \text{Vdd} \le 5.5 \text{ V}$			±0.25	%FSR
Integral linearity error ^{Note 1}	ILE	10-bit resolution AV _{REFP} = V _{DD} ^{Note 3}	$2.4~\text{V} \leq \text{Vdd} \leq 5.5~\text{V}$			±2.5	LSB
Differential linearity error Note 1	DLE	10-bit resolution AV _{REFP} = V _{DD} ^{Note 3}	$2.4~\text{V} \leq \text{Vdd} \leq 5.5~\text{V}$			±1.5	LSB
Analog input voltage	VAIN	ANI2 to ANI7	·	0		AVREFP	V
	$(2.4 V \le V)$ mode) Temperatu	Internal reference voltage (2.4 V \leq VDD \leq 5.5 V, HS (high-speed main) mode)			VBGR Note 4		V
		•	output voltage HS (high-speed main)	V _{TMPS25} Note 4		4	V

(Notes are listed on the next page.)



Notes 1. Excludes quantization error ($\pm 1/2$ LSB).

- **2.** This value is indicated as a ratio (%FSR) to the full-scale value.
- **3.** When AV_{REFP} < V_{DD}, the MAX. values are as follows. Overall error: Add ± 1.0 LSB to the MAX. value when AV_{REFP} = V_{DD}. Zero-scale error/Full-scale error: Add $\pm 0.05\%$ FSR to the MAX. value when AV_{REFP} = V_{DD}. Integral linearity error/ Differential linearity error: Add ± 0.5 LSB to the MAX. value when AV_{REFP} = V_{DD}.
- 4. Refer to 2.6.2 Temperature sensor/internal reference voltage characteristics.



(2) When reference voltage (+) = AVREFP/ANIO (ADREFP1 = 0, ADREFP0 = 1), reference voltage (-) = AVREFM/ANI1 (ADREFM = 1), target pin: ANI16, ANI17, ANI19

$(T_{A} = -40 \text{ to } +85^{\circ}\text{C}, 2.4 \text{ V} \le \text{AV}_{\text{REFP}} \le \text{V}_{\text{DD}} \le 5.5 \text{ V}, \text{V}_{\text{SS}} = 0 \text{ V}, \text{Reference voltage (+)} = \text{AV}_{\text{REFP}}, \text{REFP}, \text{AV}_{\text{REFP}}, $
$(-) = AV_{REFM} = 0 V$

Parameter	Symbol	Cond	itions	MIN.	TYP.	MAX.	Unit
Resolution	Res			8		10	bit
Overall error ^{Note 1}	AINL	10-bit resolution AV _{REFP} = $V_{DD}^{Note 3}$	$2.4 \text{ V} \leq \text{VDD} \leq 5.5 \text{ V}$		1.2	±5.0	LSB
Conversion time	t CONV	Target ANI pin:	$3.6~\text{V} \leq \text{VDD} \leq 5.5~\text{V}$	2.125		39	μs
			$2.7~V \leq V \text{DD} \leq 5.5~V$	3.1875		39	μs
	ANI16, ANI17,	ANI16, ANI17, ANI19	$2.4 \text{ V} \leq \text{Vdd} \leq 5.5 \text{ V}$	17		39	μs
Zero-scale error ^{Notes 1, 2}	EZS	10-bit resolution AV _{REFP} = V _{DD} ^{Note 3}	$2.4~V \leq V \text{DD} \leq 5.5~V$			±0.35	%FSR
Full-scale error ^{Notes 1, 2}	EFS	10-bit resolution AV _{REFP} = V _{DD} ^{Note 3}	$2.4 \text{ V} \leq \text{Vdd} \leq 5.5 \text{ V}$			±0.35	%FSR
Integral linearity error ^{Note 1}	ILE	10-bit resolution AV _{REFP} = V _{DD} ^{Note 3}	$2.4~V \leq V \text{DD} \leq 5.5~V$			±3.5	LSB
Differential linearity error Note 1	DLE	10-bit resolution AV _{REFP} = V _{DD} ^{Note 3}	$2.4~\text{V} \le \text{Vdd} \le 5.5~\text{V}$			±2.00	LSB
Analog input voltage	VAIN	ANI16, ANI17, ANI19		0		AVREFP and VDD	V

Notes 1. Excludes quantization error ($\pm 1/2$ LSB).

 $\ensuremath{\textbf{2.}}$ This value is indicated as a ratio (%FSR) to the full-scale value.

3. When $AV_{REFP} < V_{DD}$, the MAX. values are as follows.

Overall error: Add ± 4.0 LSB to the MAX. value when AV_{REFP} = V_{DD}.

Zero-scale error/Full-scale error: Add $\pm 0.20\%$ FSR to the MAX. value when AV_{REFP} = V_{DD}.

Integral linearity error/ Differential linearity error: Add ± 2.0 LSB to the MAX. value when AV_{REFP} = V_{DD}.



(3) Reference voltage (+) = V_{DD} (ADREFP1 = 0, ADREFP0 = 0), Reference voltage (-) = Vss (ADREFM = 0), target ANI pin: ANI0 to ANI7, ANI16, ANI17, ANI19, internal reference voltage, and temperature sensor output voltage

Parameter	Symbol	Conditio	ons	MIN.	TYP.	MAX.	Unit
Resolution	Res			8		10	bit
Overall error ^{Notes 1, 2}	AINL	10-bit resolution	$2.4~V \le V \text{DD} \le 5.5~V$		1.2	±7.0	LSB
Conversion time	t CONV	tconv 10-bit resolution 3	$3.6~V \le V_{DD} \le 5.5~V$	2.125		39	μs
		Target ANI pin:	$2.7~V \leq V_{DD} \leq 5.5~V$	3.1875		39	μs
		ANI0 to ANI7, ANI16, ANI17, ANI19	$2.4~\text{V} \leq \text{Vdd} \leq 5.5~\text{V}$	17		39	μs
		10-bit resolution	$3.6~\text{V} \leq \text{V}\text{DD} \leq 5.5~\text{V}$	2.375		39	μs
		Target ANI pin: Internal	$2.7~V \leq V_{DD} \leq 5.5~V$	3.5625		39	μs
	tempera output v	reference voltage, and temperature sensor output voltage (HS (high-speed main) mode)	$2.4 \text{ V} \leq \text{Vdd} \leq 5.5 \text{ V}$	17		39	μs
Zero-scale error ^{Notes 1, 2}	EZS	10-bit resolution	$2.4 \text{ V} \leq \text{VDD} \leq 5.5 \text{ V}$			±0.60	%FSR
Full-scale error ^{Notes 1, 2}	EFS	10-bit resolution	$2.4~\text{V} \leq \text{Vdd} \leq 5.5~\text{V}$			±0.60	%FSR
Integral linearity error ^{Note 1}	ILE	10-bit resolution	$2.4~\text{V} \leq \text{V}\text{DD} \leq 5.5~\text{V}$			±4.0	LSB
Differential linearity error Note 1	DLE	10-bit resolution	$2.4~V \le V \text{DD} \le 5.5~V$			±2.0	LSB
Analog input voltage	VAIN	ANI0 to ANI7, ANI16, ANI	17, ANI19	0		Vdd	V
		Internal reference voltage (2.4 V \leq VDD \leq 5.5 V, HS (high-speed main) mode)		V _{BGR} Note 3			V
		Temperature sensor output voltage (2.4 V \leq VDD \leq 5.5 V, HS (high-speed main) mode)		V _{TMPS25} Note 3			V

Notes 1. Excludes quantization error ($\pm 1/2$ LSB).

2. This value is indicated as a ratio (%FSR) to the full-scale value.

3. Refer to 2.6.2 Temperature sensor/internal reference voltage characteristics.



(4) When Reference voltage (+) = Internal reference voltage (ADREFP1 = 1, ADREFP0 = 0), Reference voltage (-) = AV_{REFM}/ANI1 (ADREFM = 1), target pin: ANI0 to ANI7, ANI16, ANI17, ANI19

(T_A = -40 to +85°C, 2.4 V \leq V_{DD} \leq 5.5 V, V_{SS} = 0 V, Reference voltage (+) = V_{BGR}^{Note 3}, Reference voltage (-) = AV_{REFM}^{Note 4} = 0 V, HS (high-speed main) mode)

Parameter	Symbol	Conditions		MIN.	TYP.	MAX.	Unit
Resolution	Res				8		Bit
Conversion time	t CONV	8-bit resolution	$2.4~V \le V_{DD} \le 5.5~V$	17		39	μs
Zero-scale error ^{Notes 1, 2}	EZS	8-bit resolution	$2.4~V \le V_{DD} \le 5.5~V$			±0.60	%FSR
Integral linearity error ^{Note 1}	ILE	8-bit resolution	$2.4~V \le V \text{DD} \le 5.5~V$			±2.0	LSB
Differential linearity error Note 1	DLE	8-bit resolution	$2.4~V \le V \text{DD} \le 5.5~V$			±1.0	LSB
Analog input voltage	VAIN			0		VBGR Note 3	V

Notes 1. Excludes quantization error ($\pm 1/2$ LSB).

2. This value is indicated as a ratio (%FSR) to the full-scale value.

3. Refer to 2.6.2 Temperature sensor/internal reference voltage characteristics.

4. When reference voltage (-) = Vss, the MAX. values are as follows.

Zero-scale error: Add $\pm 0.35\%$ FSR to the MAX. value when reference voltage (–) = AV_{REFM}.

Integral linearity error: Add ± 0.5 LSB to the MAX. value when reference voltage (–) = AV_{REFM}.

Differential linearity error: Add ± 0.2 LSB to the MAX. value when reference voltage (–) = AV_{REFM}.



2.6.2 Temperature sensor/internal reference voltage characteristics

Parameter	Symbol	Conditions	MIN.	TYP.	MAX.	Unit
Temperature sensor output voltage	VTMPS25	Setting ADS register = 80H, TA = +25°C		1.05		V
Internal reference voltage	Vbgr	Setting ADS register = 81H	1.38	1.45	1.5	V
Temperature coefficient	Fvtmps	Temperature sensor that depends on the temperature		-3.6		mV/°C
Operation stabilization wait time	tamp		5			μs

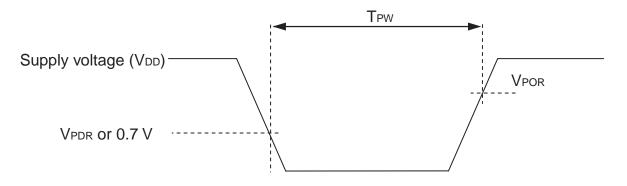
(TA = -40 to +85°C, 2.4 V \leq V_{DD} \leq 5.5 V, V_{SS} = 0 V, HS (high-speed main) mode)

2.6.3 POR circuit characteristics

$(T_A = -40 \text{ to } +85^{\circ}\text{C}, \text{ Vss} = 0 \text{ V})$

Parameter	Symbol	Conditions	MIN.	TYP.	MAX.	Unit
Detection voltage	VPOR	Power supply rise time	1.47	1.51	1.55	V
	VPDR	Power supply fall time	1.46	1.50	1.54	V
Minimum pulse width ^{Note}	Tpw		300			μs

Note Minimum time required for a POR reset when V_{DD} exceeds below V_{PDR}. This is also the minimum time required for a POR reset from when V_{DD} exceeds below 0.7 V to when V_{DD} exceeds V_{POR} while STOP mode is entered or the main system clock (fmain) is stopped through setting bit 0 (HIOSTOP) and bit 7 (MSTOP) in the clock operation status control register (CSC).





2.6.4 LVD circuit characteristics

LVD Detection Voltage of Reset Mode and Interrupt Mode

(TA = -40 to +85°C, VPDR \leq VDD \leq 5.5 V, Vss = 0 V)

	Parameter	Symbol	Conditions	MIN.	TYP.	MAX.	Unit
Detection	ction Supply voltage level		Power supply rise time	3.98	4.06	4.14	V
voltage			Power supply fall time	3.90	3.98	4.06	V
		VLVD1	Power supply rise time	3.68	3.75	3.82	V
			Power supply fall time	3.60	3.67	3.74	V
		VLVD2	Power supply rise time	3.07	3.13	3.19	V
			Power supply fall time	3.00	3.06	3.12	V
		VLVD3	Power supply rise time	2.96	3.02	3.08	V
			Power supply fall time	2.90	2.96	3.02	V
		VLVD4	Power supply rise time	2.86	2.92	2.97	V
			Power supply fall time	2.80	2.86	2.91	V
		VLVD5	Power supply rise time	2.76	2.81	2.87	V
			Power supply fall time	2.70	2.75	2.81	V
		VLVD6	Power supply rise time	2.66	2.71	2.76	V
			Power supply fall time	2.60	2.65	2.70	V
		VLVD7	Power supply rise time	2.56	2.61	2.66	V
			Power supply fall time	2.50	2.55	2.60	V
		VLVD8	Power supply rise time	2.45	2.50	2.55	V
			Power supply fall time	2.40	2.45	2.50	V
Minimum pu	Ilse width	t∟w		300			μs
Detection de	elay time	tld				300	μs



LVD Detection Voltage of Interrupt & Reset Mode

Parameter	Symbol	Con	ditions	MIN.	TYP.	MAX.	Unit
Interrupt and reset	VLVDC0	VPOC2, VPOC1, VPOC0 =	2.40	2.45	2.50	V	
mode	VLVDC1	LVIS1, LVIS0 = 1, 0	Rising release reset voltage	2.56	2.61	2.66	V
			Falling interrupt voltage	2.50	2.55	2.60	V
	VLVDC2	LVIS1, LVIS0 = 0, 1	Rising release reset voltage	2.66	2.71	2.76	V
			Falling interrupt voltage	2.60	2.65	2.70	V
Γ	VLVDC3	LVIS1, LVIS0 = 0, 0	Rising release reset voltage	3.68	3.75	3.82	V
			Falling interrupt voltage	3.60	3.67	3.74	V
	VLVDD0	VPOC2, VPOC1, VPOC0 = 0, 1, 1, falling reset voltage			2.75	2.81	V
	VLVDD1	LVIS1, LVIS0 = 1, 0	Rising release reset voltage	2.86	2.92	2.97	V
			Falling interrupt voltage	2.80	2.86	2.91	V
	VLVDD2	LVIS1, LVIS0 = 0, 1	Rising release reset voltage	2.96	3.02	3.08	V
			Falling interrupt voltage	2.90	2.96	3.02	V
	VLVDD3	LVIS1, LVIS0 = 0, 0	Rising release reset voltage	3.98	4.06	4.14	V
			Falling interrupt voltage	3.90	3.98	4.06	V

 $(T_A = -40 \text{ to } +85^{\circ}C, V_{PDR} \le V_{DD} \le 5.5 \text{ V}, V_{SS} = 0 \text{ V})$

2.6.5 Power supply voltage rising slope characteristics

 $(T_A = -40 \text{ to } +85^{\circ}\text{C}, \text{ Vss} = 0 \text{ V})$

Parameter	Symbol	Conditions	MIN.	TYP.	MAX.	Unit
Power supply voltage rising slope	SVDD				54	V/ms

Caution Make sure to keep the internal reset state by the LVD circuit or an external reset until V_{DD} reaches the operating voltage range shown in 2.4 AC Characteristics.

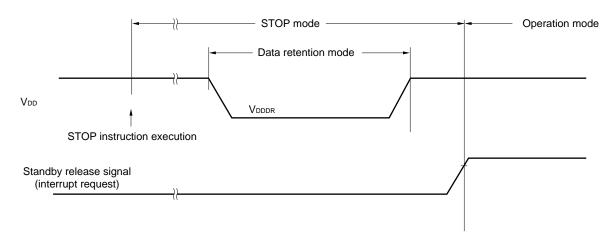


2.7 Data Memory STOP Mode Low Supply Voltage Data Retention Characteristics

 $(T_A = -40 \text{ to } +85^{\circ}C, \text{ Vss} = 0 \text{ V})$

Parameter	Symbol	Conditions	MIN.	TYP.	MAX.	Unit
Data retention supply voltage	VDDDR		1.46 ^{Note}		5.5	V

Note The value depends on the POR detection voltage. When the voltage drops, the data is retained before a POR reset is effected, but data is not retained when a POR reset is effected.



2.8 Flash Memory Programming Characteristics

TA = -40 (0 + 05 + 0.5									
Parameter	Symbol	Conditions	Conditions		TYP.	MAX.	Unit		
CPU/peripheral hardware clock frequency	fс∟к	$2.4~\text{V} \leq \text{Vdd} \leq 5.5~\text{V}$		1		24	MHz		
Number of code flash rewrites	Cerwr	Retaining years: 20 years	T _A = +85°C	1,000			Times		
Number of data flash rewrites Notes 1, 2, 3		Retaining years: 1 year	T _A = +25°C		1,000,000				
		Retaining years: 5 years	T _A = +85°C	100,000					
		Retaining years: 20 years	T _A = +85°C	10,000					

$(T_A = -40 \text{ to } +85^{\circ}\text{C}, 2.4 \text{ V} \le \text{V}_{DD} \le 5.5 \text{ V}, \text{V}_{SS} = 0 \text{ V})$

Notes 1. 1 erase + 1 write after the erase is regarded as 1 rewrite. The retaining years are until next rewrite after the rewrite.

2. When using flash memory programmer and Renesas Electronics self programming library.

3. These specifications show the characteristics of the flash memory and the results obtained from Renesas Electronics reliability testing.

2.9 Dedicated Flash Memory Programmer Communication (UART)

$(T_A = -40 \text{ to } +85^{\circ}C, 2.4 \text{ V} \le \text{V}_{DD} \le 5.5 \text{ V}, \text{V}_{SS} = 0 \text{ V})$

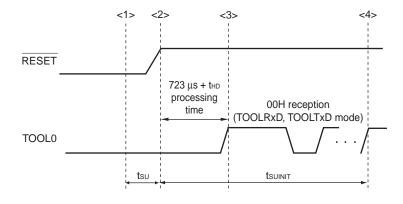
Parameter	Symbol	Conditions	MIN.	TYP.	MAX.	Unit
Transfer rate		During serial programming	115,200		1,000,000	bps



2.10 Timing Specs for Switching Flash Memory Programming Modes

Parameter	Symbol	Conditions	MIN.	TYP.	MAX.	Unit
How long from when an external reset ends until the initial communication settings are specified	tsuinit	POR and LVD reset must end before the external reset ends.			100	ms
How long from when the TOOL0 pin is placed at the low level until an external reset ends	tsu	POR and LVD reset must end before the external reset ends.	10			μs
How long the TOOL0 pin must be kept at the low level after an external reset ends (excluding the processing time of the firmware to control the flash memory)	tно	POR and LVD reset must end before the external reset ends.	1			ms

 $(T_A = -40 \text{ to } +85^{\circ}\text{C}, 2.4 \text{ V} \le \text{V}_{DD} \le 5.5 \text{ V}, \text{ V}_{SS} = 0 \text{ V})$



- <1> The low level is input to the TOOL0 pin.
- <2> The external reset ends (POR and LVD reset must end before the external reset ends.).
- <3> The TOOL0 pin is set to the high level.
- <4> Setting of the flash memory programming mode by UART reception and complete the baud rate setting.
- **Remark** tsuinit: The segment shows that it is necessary to finish specifying the initial communication settings within 100 ms from when the resets end.
 - $t_{su:}$ How long from when the TOOL0 pin is placed at the low level until an external reset ends
 - the: How long to keep the TOOL0 pin at the low level from when the external and internal resets end (excluding the processing time of the firmware to control the flash memory)



3. ELECTRICAL SPECIFICATIONS (G: T_A = -40 to +105°C)

This chapter describes the electrical specifications for the products "G: Industrial applications (T_A = -40 to +105°C)".

The target products G: Industrial applications ; T_A = -40 to +105°C

R5F10JBCGNA, R5F10JBCGFP, R5F10JGCGNA, R5F10JGCGFB, R5F10KBCGNA, R5F10KBCGFP, R5F10KGCGNA, R5F10KGCGFB

- Cautions 1. The RL78 microcontrollers has an on-chip debug function, which is provided for development and evaluation. Do not use the on-chip debug function in products designated for mass production, because the guaranteed number of rewritable times of the flash memory may be exceeded when this function is used, and product reliability therefore cannot be guaranteed. Renesas Electronics is not liable for problems occurring when the on-chip debug function is used.
 - 2. The pins mounted depend on the product. Refer to 2.1 Port Function to 2.2.1 With functions for each product in the RL78/G1C User's Manual: Hardware.
 - 3. Please contact Renesas Electronics sales office for derating of operation under T_A = +85°C to +105°C. Derating is the systematic reduction of load for the sake of improved reliability.

products "A: Consumer applications".			
Parameter	Application		

There are following differences between the products "G: Industrial applications ($T_A = -40$ to $+105^{\circ}C$)" and the

Parameter	Appl	ication
	A: Consumer applications	G: Industrial applications
Operating ambient temperature	$T_{A} = -40 \text{ to } +85^{\circ}\text{C}$	T _A = -40 to +105°C
High-speed on-chip oscillator clock	$2.4~V \leq V_{\text{DD}} \leq 5.5~V$	$2.4~V \leq V_{\text{DD}} \leq 5.5~V$
accuracy	±1.0%@ T _A = -20 to +85°C	±2.0%@ T _A = +85 to +105°C
	$\pm 1.5\%$ @ T _A = -40 to -20°C	±1.0%@ T _A = -20 to +85°C
		±1.5%@ T _A = -40 to -20°C
Serial array unit	UART	UART
	CSI: fcLk/2 (supporting 16 Mbps), fcLk/4	CSI: fc∟κ/4
	Simplified I ² C communication	Simplified I ² C communication
IICA	Normal mode	Normal mode
	Fast mode	Fast mode
	Fast mode plus	

Remark The electrical characteristics of the products G: Industrial applications ($T_A = -40$ to $+105^{\circ}C$) are different from those of the products "A: Consumer applications". For details, refer to **3.1** to **3.10**.

<R>



3.1 Absolute Maximum Ratings

Absolute Maximum Ratings (T_A = 25°C) (1/2)

Parameter	Symbols	Conditions	Ratings	Unit
Supply voltage	Vdd		-0.5 to +6.5	V
REGC pin input voltage	Viregc	REGC	-0.3 to +2.8 and -0.3 to V_{DD} +0.3 $^{\text{Note 1}}$	V
UVDD pin input voltage	VIUVDD	UVDD	-0.3 to VDD +0.3	V
Input voltage	VI1	P00, P01, P14 to P17, P20 to P27, P30, P31, P40, P41, P50, P51, P70 to P75, P120 to P124, P137, P140, EXCLK, EXCLKS, RESET	-0.3 to V _{DD} +0.3 ^{Note 2}	V
	VI2	P60 to P63 (N-ch open-drain)	-0.3 to +6.5	V
	Vı3	UDP0, UDM0, UDP1, UDM1	-0.3 to +6.5	V
	V _{I4}	UVBUS	-0.3 to +6.5	V
Output voltage	Vo1	P00, P01, P14 to P17, P20 to P27, P30, P31, P40, P41, P50, P51, P60 to P63, P70 to P75, P120, P130, P140	–0.3 to V _{DD} +0.3 ^{Note 2}	V
	V ₀₂	UDP0, UDM0, UDP1, UDM1	-0.3 to +6.5	V
Analog input voltage	Vaii	ANI16, ANI17, ANI19	-0.3 to V _{DD} +0.3 and -0.3 to AV _{REF} (+) +0.3 Notes 2, 3	V
	Vai2	ANI0 to ANI7	-0.3 to VDD +0.3 and -0.3 to AV_{REF} (+) +0.3 Notes 2, 3	V

Notes 1. Connect the REGC pin to Vss via a capacitor (0.47 to 1 μ F). This value regulates the absolute maximum rating of the REGC pin. Do not use this pin with voltage applied to it.

2. Must be 6.5 V or lower.

- 3. Do not exceed AVREF(+) + 0.3 V in case of A/D conversion target pin
- Caution Product quality may suffer if the absolute maximum rating is exceeded even momentarily for any parameter. That is, the absolute maximum ratings are rated values at which the product is on the verge of suffering physical damage, and therefore the product must be used under conditions that ensure that the absolute maximum ratings are not exceeded.
- **Remarks 1.** Unless specified otherwise, the characteristics of alternate-function pins are the same as those of the port pins.
 - AVREF (+): The + side reference voltage of the A/D converter. This can be selected from AVREFP, the internal reference voltage (1.45 V), and VDD.
 - 3. Vss: Reference voltage



Parameter	Symbols		Conditions	Ratings	Unit	
Output current, high	Іон1	Per pin	P00, P01, P14 to P17, P30, P31,	-40	mA	
			P40, P41, P50, P51, P70 to P75,			
			P120, P130, P140			
		Total of all pins	P00, P01, P40, P41, P120,	-70	mA	
		–170 mA	P130, P140			
			P14 to P17, P30, P31,	-100	mA	
			P50, P51, P70 to P75			
	Іон2	Per pin	P20 to P27	-0.5	mA	
		Total of all pins		-2	mA	
Output current, low	IOL1	Per pin	P00, P01, P14 to P17, P30, P31,	40	mA	
				P40, P41, P50, P51, P60 to P63,		
			P70 to P75, P120, P130, P140			
		Total of all pins	P00, P01, P40, P41, P120,	70	mA	
		170 mA	P130, P140			
			P14 to P17, P30, P31,	100	mA	
			P50, P51, P60 to P63, P70 to P75			
	IOL2	Per pin	P20 to P27	1	mA	
		Total of all pins		5	mA	
Operating ambient	TA	In normal operati	ion mode	-40 to +105	°C	
temperature		In flash memory	programming mode			
Storage temperature	Tstg			-65 to +150	°C	

Absolute Maximum Ratings (TA = 25°C) (2/2)

- Caution Product quality may suffer if the absolute maximum rating is exceeded even momentarily for any parameter. That is, the absolute maximum ratings are rated values at which the product is on the verge of suffering physical damage, and therefore the product must be used under conditions that ensure that the absolute maximum ratings are not exceeded.
- **Remark** Unless specified otherwise, the characteristics of alternate-function pins are the same as those of the port pins.



3.2 Oscillator Characteristics

3.2.1 X1, XT1 oscillator characteristics

$(T_A = -40 \text{ to } +105^{\circ}\text{C}, 2.4 \text{ V} \le \text{V}_{DD} \le 5.5 \text{ V}, \text{V}_{SS} = 0 \text{ V})$

Parameter	Resonator	Conditions	MIN.	TYP.	MAX.	Unit
X1 clock oscillation	Ceramic resonator/	$2.7~V \leq V_{\text{DD}} \leq 5.5~V$	1.0		20.0	MHz
frequency (fx) ^{Note}	crystal resonator	$2.4~V \leq V_{\text{DD}} < 2.7~V$	1.0		16.0	MHz
XT1 clock oscillation frequency (f _{XT}) ^{Note}	Crystal resonator		32	32.768	35	kHz

Note Indicates only permissible oscillator frequency ranges. Refer to AC Characteristics for instruction execution time. Request evaluation by the manufacturer of the oscillator circuit mounted on a board to check the oscillator characteristics.

- Caution Since the CPU is started by the high-speed on-chip oscillator clock after a reset release, check the X1 clock oscillation stabilization time using the oscillation stabilization time counter status register (OSTC) by the user. Determine the oscillation stabilization time of the OSTC register and the oscillation stabilization time select register (OSTS) after sufficiently evaluating the oscillation stabilization time with the resonator to be used.
- Remark When using the X1 oscillator and XT1 oscillator, refer to 5.4 System Clock Oscillator in the RL78/G1C User's Manual: Hardware.

3.2.2 On-chip oscillator characteristics

$(T_A = -40 \text{ to } +105^{\circ}\text{C}, 2.4 \text{ V} \le \text{V}_{DD} \le 5.5 \text{ V}, \text{V}_{SS} = 0 \text{ V})$

Oscillators	Parameters	Conditions	MIN.	TYP.	MAX.	Unit
High-speed on-chip oscillator clock frequency Notes 1, 2	fносо		1		48	MHz
High-speed on-chip oscillator		–20 to +85 °C	-1.0		+1.0	%
clock frequency accuracy		−40 to −20 °C	-1.5		+1.5	%
		+85 to +105 °C	-2.0		+2.0	%
Low-speed on-chip oscillator clock frequency	fı∟			15		kHz
Low-speed on-chip oscillator clock frequency accuracy			-15		+15	%

Notes 1. High-speed on-chip oscillator frequency is selected by bits 0 to 3 of option byte (000C2H/010C2H) and bits 0 to 2 of HOCODIV register.

2. This indicates the oscillator characteristics only. Refer to AC Characteristics for instruction execution time.



3.2.3 PLL oscillator characteristics

$(T_A = -40 \text{ to } +105^{\circ}\text{C}, 2.4 \text{ V} \le \text{V}_{DD} \le 5.5 \text{ V}, \text{V}_{SS} = 0 \text{ V})$

Oscillators	Parameters	Conditions	MIN.	TYP.	MAX.	Unit
PLL input frequency Note	fpllin	High-speed system clock	6.00		16.00	MHz
PLL output frequency Note	fpll			48.00		MHz
Lock up time		From PLL output enable to stabilization of the output frequency	40.00			μs
Interval time		From PLL stop to PLL re-operation setteing Wait time	4.00			μs
Setting wait time		From after PLL input clock stabilization and PLL setting is fixed to start setting Wait time required	1.00			μs

Note Indicates only oscillator characteristics. Refer to AC Characteristics for instruction execution time.



3.3 DC Characteristics

3.3.1 Pin characteristics

$(T_A = -40 \text{ to } +105^{\circ}\text{C}, 2.4 \text{ V} \le \text{V}_{DD} \le 5.5 \text{ V}, \text{V}_{SS} = 0 \text{ V})$

Items	Symbol	Conditions		MIN.	TYP.	MAX.	Unit
Output current, high ^{Note 1}	Іон1	Per pin for P00, P01, P14 to P17, P30, P31, P40, P41, P50, P51, P70 to P75, P120, P130, P140	$2.4 \text{ V} \leq V_{\text{DD}} \leq 5.5 \text{ V}$			-3.0 Note 2	mA
		Total of P00, P01, P40, P41, P120,	$4.0~V \leq V_{DD} \leq 5.5~V$			-30.0	mA
		P130, P140	$2.7 \text{ V} \leq \text{V}_{\text{DD}} < 4.0 \text{ V}$			-10.0	mA
		(When duty ≤ 70% ^{Note 3})	$2.4~\text{V} \leq \text{V}_\text{DD} < 2.7~\text{V}$			-5.0	mA
		Total of P14 to P17, P30, P31,	$4.0~V \leq V_{DD} \leq 5.5~V$			-30.0	mA
		P50, P51, P70 to P75	$2.7~\text{V} \leq \text{V}_{\text{DD}} < 4.0~\text{V}$			-19.0	mA
		(When duty ≤ 70% ^{Note 3})	$2.4~V \leq V_{DD}~<2.7~V$			-10.0	mA
		Total of all pins (When duty ≤ 70% ^{Note 3})	$2.4~V \leq V_{DD} \leq 5.5~V$			-60.0	mA
	Іон2	Per pin for P20 to P27	$2.4~V \le V_{\text{DD}} \le 5.5~V$			-0.1 ^{Note 2}	mA
		Total of all pins (When duty ≤ 70% ^{Note 3})	$2.4~V \le V_{\text{DD}} \le 5.5~V$			-1.5	mA

Notes 1. Value of current at which the device operation is guaranteed even if the current flows from the V_{DD} pin to an output pin.

- 2. However, do not exceed the total current value.
- 3. Specification under conditions where the duty factor ≤ 70%. The output current value that has changed to the duty factor > 70% the duty ratio can be calculated with the following expression (when changing the duty ratio to n%).
 - Total output current of pins = $(I_{OH} \times 0.7)/(n \times 0.01)$
 - <Example> Where n = 80% and $I_{OH} = -10.0 \text{ mA}$

Total output current of pins = $(-10.0 \times 0.7)/(80 \times 0.01) \cong -8.7$ mA

However, the current that is allowed to flow into one pin does not vary depending on the duty factor. A current higher than the absolute maximum rating must not flow into one pin.

Caution P00, P01, P30, and P74 do not output high level in N-ch open-drain mode.



Items	Symbol	Conditions		MIN.	TYP.	MAX.	Unit
Output current, Iow ^{Note 1}	Iol1	Per pin for P00, P01, P14 to P17, P30, P31, P40, P41, P50, P51, P70 to P75, P120, P130, P140	$2.4V \le V_{DD} \le 5.5 V$			8.5 ^{Note 2}	mA
		Per pin for P60 to P63	$2.4V \leq V_{\text{DD}} \leq 5.5 \; V$			15.0 Note 2	mA
		Total of P00, P01, P40, P41, P120,	$4.0~V \leq V_{DD} \leq 5.5~V$			40.0	mA
		P130, P140	$2.7~\text{V} \leq \text{V}_\text{DD} < 4.0~\text{V}$			15.0	mA
		(When duty ≤ 70% ^{Note 3})	$2.4~V \leq V_{DD} < 2.7~V$			9.0	mA
		Total of P14 to P17, P30, P31, P50,	$4.0~V \leq V_{DD} \leq 5.5~V$			40.0	mA
		P51, P60 to P63, P70 to P75	$2.7~\text{V} \leq \text{V}_\text{DD} < 4.0~\text{V}$			35.0	mA
		(When duty ≤ 70% ^{Note 3})	$2.4 \text{ V} \leq \text{V}_{\text{DD}} < 2.7 \text{ V}$			20.0	mA
		Total of all pins (When duty ≤ 70% ^{Note 3})	$2.4V \le V_{DD} \le 5.5 V$			80.0	mA
	IOL2	Per pin for P20 to P27	$2.4V \leq V_{DD} \leq 5.5~V$			0.4 Note 2	mA
		Total of all pins (When duty ≤ 70% ^{Note 3})	$2.4V \leq V_{\text{DD}} \leq 5.5 \text{ V}$			5.0	mA

$(T_A = -40 \text{ to } +105^{\circ}\text{C}, 2.4 \text{ V} \le \text{V}_{DD} \le 5.5 \text{ V}, \text{V}_{SS} = 0 \text{ V})$

Notes 1. Value of current at which the device operation is guaranteed even if the current flows from an output pin to the Vss pin.

2. However, do not exceed the total current value.

3. Specification under conditions where the duty factor \leq 70%.

The output current value that has changed to the duty factor > 70% the duty ratio can be calculated with the following expression (when changing the duty ratio to n%).

• Total output current of pins = $(I_{OL} \times 0.7)/(n \times 0.01)$

<Example> Where n = 80% and IoL = 10.0 mA

Total output current of pins = $(10.0 \times 0.7)/(80 \times 0.01) \approx 8.7$ mA

However, the current that is allowed to flow into one pin does not vary depending on the duty factor. A current higher than the absolute maximum rating must not flow into one pin.



Items	Symbol	Conditions		MIN.	TYP.	MAX.	Unit
Input voltage, high	Vih1	P00, P01, P14 to P17, P30, P31, P40, P41, P50, P51, P70 to P75, P120, P140	Normal input buffer	0.8Vdd		Vdd	V
	VIH2	P00, P01, P30, P50	TTL input buffer 4.0 V \leq V _{DD} \leq 5.5 V	2.2		Vdd	V
			TTL input buffer $3.3 \text{ V} \leq \text{V}_{\text{DD}} < 4.0 \text{ V}$	2.0		Vdd	V
			TTL input buffer $2.4 \text{ V} \leq \text{V}_{\text{DD}} < 3.3 \text{ V}$	1.5		Vdd	V
	Vінз	P20 to P27		0.7Vdd		Vdd	V
VIH4	VIH4	P60 to P63		0.7Vdd		6.0	V
	VIH5	P121 to P124, P137, EXCLK, EXCLK	0.8Vdd		Vdd	V	
Input voltage, low	VIL1	P00, P01, P14 to P17, P30, P31, P40, P41, P50, P51, P70 to P75, P120, P140	Normal input buffer	0		0.2Vdd	V
	VIL2	P00, P01, P30, P50	TTL input buffer 4.0 V \leq V _{DD} \leq 5.5 V	0		0.8	V
			TTL input buffer $3.3 \text{ V} \leq \text{V}_{\text{DD}} < 4.0 \text{ V}$	0		0.5	V
			TTL input buffer 2.4 V \leq V _{DD} $<$ 3.3 V	0		0.32	V
	VIL3	P20 to P27		0		0.3Vdd	V
	VIL4	P60 to P63		0		0.3VDD	V
	VIL5	P121 to P124, P137, EXCLK, EXCLK	S, RESET	0		0.2VDD	V

$(T_A = -40 \text{ to } +105^{\circ}\text{C}, 2.4 \text{ V} \le \text{V}_{DD} \le 5.5 \text{ V}, \text{V}_{SS} = 0 \text{ V})$

Caution The maximum value of V_{IH} of pins P00, P01, P30, and P74 is V_{DD}, even in the N-ch open-drain mode.



Items	Symbol	Conditions		MIN.	TYP.	MAX.	Unit
Output voltage, high	Vон1	P00, P01, P14 to P17, P30, P31, P40, P41, P50, P51, P70 to P75,	$\begin{array}{l} 4.0 \ V \leq V_{\text{DD}} \leq 5.5 \ V, \\ I_{\text{OH1}} = -3.0 \ \text{mA} \end{array}$	Vdd - 0.7			V
		P120, P130, P140	$2.7 \text{ V} \le \text{V}_{\text{DD}} \le 5.5 \text{ V},$ Ioh1 = -2.0 mA	Vdd - 0.6			V
			$2.4 \text{ V} \le \text{V}_{\text{DD}} \le 5.5 \text{ V},$ Іон1 = -1.5 mA	Vdd - 0.5			V
	Voh2	P20 to P27	$2.4 \text{ V} \le \text{V}_{\text{DD}} \le 5.5 \text{ V},$ IOH2 = -100 μ A	Vdd - 0.5			V
Output voltage, low	Vol1	P00, P01, P14 to P17, P30, P31, P40, P41, P50, P51, P70 to P75,	$\begin{array}{l} 4.0 \ V \leq V_{\text{DD}} \leq 5.5 \ V, \\ I_{\text{OL1}} = 8.5 \ mA \end{array} \end{array} \label{eq:VDD}$			0.7	V
		P120, P130, P140	$\begin{array}{l} 2.7 \ V \leq V_{\text{DD}} \leq 5.5 \ V, \\ I_{\text{OL1}} = 3.0 \ mA \end{array} \end{array} \label{eq:DD}$			0.6	V
			$\begin{array}{l} 2.7 \ V \leq V_{\text{DD}} \leq 5.5 \ V, \\ I_{\text{OL1}} = 1.5 \ mA \end{array} \end{array} \label{eq:eq:electropy}$			0.4	V
			$\begin{array}{l} 2.4 \ V \leq V_{\text{DD}} \leq 5.5 \ V, \\ I_{\text{OL1}} = 0.6 \ mA \end{array} \end{array} \label{eq:VDD}$			0.4	V
	Vol2	P20 to P27	$2.4 \text{ V} \le \text{V}_{\text{DD}} \le 5.5 \text{ V},$ $\text{Iol2} = 400 \ \mu \text{ A}$			0.4	V
	Vol3	P60 to P63	$4.0 \text{ V} \le \text{V}_{\text{DD}} \le 5.5 \text{ V},$ $I_{\text{OL1}} = 15.0 \text{ mA}$			2.0	V
		$\begin{array}{l} 4.0 \ V \leq V_{\text{DD}} \leq 5.5 \ V, \\ I_{\text{OL1}} = 5.0 \ mA \end{array} \end{array} \label{eq:VDD}$			0.4	V	
		$\begin{array}{l} 2.7 \ V \leq V_{\text{DD}} \leq 5.5 \ V, \\ I_{\text{OL1}} = 3.0 \ mA \end{array} \end{array} eq:delta_de$			0.4	V	
			$\begin{array}{l} 2.4 \ V \leq V_{DD} \leq 5.5 \ V, \\ I_{OL1} = 2.0 \ mA \end{array} \end{array} \label{eq:VDD}$			0.4	V

 $(T_A = -40 \text{ to } +105^{\circ}\text{C}, 2.4 \text{ V} \le \text{V}_{DD} \le 5.5 \text{ V}, \text{V}_{SS} = 0 \text{ V})$

Caution P00, P01, P30, and P74 do not output high level in N-ch open-drain mode.



Items	Symbol	Conditio	ns		MIN.	TYP.	MAX.	Unit
Input leakage current, high	Ішні	P00, P01, P14 to P17, P20 to P27, P30, P31, P40, P41, P50, P51, P60 to P63, P70 to P75, P120, P137, P140, RESET	VI = VDD				1	μA
	Ilih2	P121 to P124 (X1, X2, XT1, XT2, EXCLK, EXCLKS)	Vi = Vdd	In input port or external clock input			1	μA
				In resonator connection			10	μA
Input leakage current, low	Ilul1	P00, P01, P14 to P17, P20 to P27, P30, P31, P40, P41, P50, P51, P60 to P63, P70 to P75, P120, P137, P140, RESET	VI = Vss				-1	μA
	ILIL2	P121 to P124 (X1, X2, XT1, XT2, EXCLK, EXCLKS)	VI = Vss	In input port or external clock input			-1	μA
				In resonator connection			-10	μA
On-chip pll-up resistance	Ru	P00, P01, P14 to P17, P30, P31, P40, P41, P50, P51, P70 to P75, P120, P140	Vı = Vss, Ir	n input port	10	20	100	kΩ

(TA = -40 to +105°C, 2.4 V \leq VDD \leq 5.5 V, Vss = 0 V)



3.3.2 Supply current characteristics

$(T_A = -40 \text{ to } +105^{\circ}\text{C}, 2.4 \text{ V} \le \text{V}_{DD} \le 5.5 \text{ V}, \text{V}_{SS} = 0 \text{ V})$

(1/2)

Parameter	Symbol			Conditions	Conditions			TYP.	MAX.	Unit	
Supply	IDD1	Operating	HS	fносо = 48 MHz	Basic	Vdd = 5.0 V		1.7		mA	
Current Note 1		mode	(High-speed	fin = 24 MHz ^{Note 3}	operation	V _{DD} = 3.0 V		1.7		mA	
			main) modffe ^{Note 6}		Normal	V _{DD} = 5.0 V		3.7	5.8	mA	
					operation	VDD = 3.0 V		3.7	5.8	mA	
				fносо = 24 MHz ^{Note 5}	Normal	VDD = 5.0 V		2.3	3.4	mA	
				$f_{IH} = 12 \text{ MHz}^{Note 3}$	operation	VDD = 3.0 V		2.3	3.4	mA	
				fносо = 12 MHz ^{Note 5}	Normal	Vdd = 5.0 V		1.6	2.2	mA	
				fiH = 6 MHz Note 3	operation	VDD = 3.0 V		1.6	2.2	mA	
				fHOCO = 6 MHz Note	Normal	Vdd = 5.0 V		1.2	1.6	mA	
				o Note 3	operation	$V_{DD} = 3.0 V$		1.2	1.6	mA	
				$f_{IH} = 3 \text{ MHz}^{\text{Note 3}}$		-					
			HS (High-speed	$f_{MX} = 20 \text{ MHz}^{\text{Note 2}},$	Normal operation	Square wave input		3.0	4.9	mA	
			main) mode	$V_{DD} = 5.0 V$	· .	Resonator connection		3.2	5.0	mA	
			Note 6	$f_{MX} = 20 \text{ MHz}^{\text{Note 2}},$	Normal operation	Square wave input		3.0	4.9	m/	
				VDD = 3.0 V		Resonator connection		3.2	5.0	m/	
			· · ·	Normal	Square wave input		1.9	2.9	m/		
						operation	Resonator connection		1.9	2.9	m/
			$f_{MX} = 10 \text{ MHz}^{Note 2},$	Normal	Square wave input		1.9	2.9	m/		
		VDD = 3.0 V	operation	Resonator connection		1.9	2.9	m/			
	HS (High-speed	$f_{PLL} = 48 \text{ MHz},$	Normal	Vdd = 5.0 V		4.0	6.3	m			
			main) mode (PLL fr operation) for Note 6	main) mode	fclk = 24 MHz ^{Note 2}	operation	Vdd = 3.0 V		4.0	6.3	m
				fpll = 48 MHz,	Normal	Vdd = 5.0 V		2.6	3.9	m/	
				fclk = 12 MHz ^{Note 2}	operation	Vdd = 3.0 V		2.6	3.9	m/	
				fpll = 48 MHz,	Normal	$V_{DD} = 5.0 V$		1.9	2.7	m/	
				fclк = 6 MHz ^{Note 2}	operation	Vdd = 3.0 V		1.9	2.7	m/	
			Subsystem	fsuв = 32.768 kHz Note 4	Normal	Resonator connection		4.1	4.9	μF	
			clock operation	Note 4 $T_A = -40^{\circ}C$	operation	Square wave input		4.2	5.0	μP	
				fsuв = 32.768 kHz	Normal	Square wave input		4.1	4.9	μĤ	
				Note 4	operation	Resonator connection		4.1	4.9 5.0	μF	
				T _A = +25°C				4.2	5.0	μ	
				fsuв = 32.768 kHz	Normal	Square wave input		4.2	5.5	μF	
				Note 4	operation	Resonator connection		4.3	5.6	μŀ	
				T _A = +50°C							
				fsuв = 32.768 kHz	Normal	Square wave input		4.2	6.3	μŀ	
				Note 4	operation	Resonator connection		4.3	6.4	μA	
				$T_A = +70^{\circ}C$							
				fsuв = 32.768 kHz	Normal	Square wave input		4.8	7.7	μA	
				Note 4	operation	Resonator connection		4.9	7.8	μA	
				$T_A = +85^{\circ}C$							
				fsuв = 32.768 kHz	Normal	Square wave input		6.9	19.7	μA	
				Note 4	operation	Resonator connection		7.0	19.8	μA	
				T _A = +105°C						ł	

(Notes and Remarks are listed on the next page.)



- **Notes 1.** Total current flowing into V_{DD}, including the input leakage current flowing when the level of the input pin is fixed to V_{DD}, or V_{SS}. The values below the MAX. column include the peripheral operation current. However, not including the current flowing into the A/D converter, LVD circuit, I/O port, and on-chip pull-up/pull-down resistors and the current flowing during data flash rewrite.
 - 2. When high-speed on-chip oscillator and subsystem clock are stopped.
 - 3. When high-speed system clock and subsystem clock are stopped.
 - **4.** When high-speed on-chip oscillator and high-speed system clock are stopped. When AMPHS1 = 1 (Ultra-low power consumption oscillation). However, not including the current flowing into the RTC, 12-bit interval timer, and watchdog timer.
 - **5.** When Operating frequency setting of option byte = 48 MHz. When fHOCO is divided by HOCODIV. When RDIV[1:0] = 00 (divided by 2: default).
 - **6.** Relationship between operation voltage width, operation frequency of CPU and operation mode is as below.

HS (high-speed main) mode: 2.7 V \leq V_{DD} \leq 5.5 V@1 MHz to 24 MHz 2.4 V \leq V_{DD} \leq 5.5 V@1 MHz to 16 MHz

- Remarks 1. fHOCO: High-speed on-chip oscillator clock frequency (Max. 48 MHz)
 - 2. fill: Main system clock source frequency obtained by dividing the high-speed on-chip oscillator clock by 2, 4, or 8 (Max. 24 MHz)
 - **3.** fmx: High-speed system clock frequency (X1 clock oscillation frequency or external main system clock frequency)
 - 4. fPLL: PLL oscillation frequency
 - 5. fsub: Subsystem clock frequency (XT1 clock oscillation frequency)
 - 6. fcLK: CPU/peripheral hardware clock frequency
 - 7. Except subsystem clock operation, temperature condition of the TYP. value is $T_A = 25^{\circ}C$.



(TA = -40 to +105°C, 2.4 V \leq VDD \leq 5.5 V, Vss = 0 V)

(2/2)

14 - 40		•, =- · · ·		\mathbf{v}, \mathbf{v} ss = 0 \mathbf{v})					(2/2
Parameter	Symbol			Conditions		MIN.	TYP.	MAX.	Unit
Supply	DD2	HALT	HS	fносо = 48 MHz	Vdd = 5.0 V		0.67	2.25	mA
Current Note 1	Note 2	mode	(High-speed	fiн = 24 MHz ^{Note 4}	Vdd = 3.0 V		0.67	2.25	mA
			main) mode Note 9	fHOCO = 24 MHz ^{Note 7}	Vdd = 5.0 V		0.50	1.55	mA
				fıн = 12 MHz ^{Note 4}	VDD = 3.0 V		0.50	1.55	mA
				fHOCO = 12 MHz ^{Note 7}	Vdd = 5.0 V		0.41	1.21	mA
				fін = 6 MHz ^{Note 4}	VDD = 3.0 V		0.41	1.21	mA
				fHOCO = 6 MHz ^{Note 7}	VDD = 5.0 V		0.37	1.05	mA
				fін = 3 MHz ^{Note 4}	V _{DD} = 3.0 V		0.37	1.05	mA
			HS	$f_{MX} = 20 \text{ MHz}^{\text{Note 3}},$	Square wave input		0.28	1.90	mA
			(High-speed	$V_{DD} = 5.0 V$	Resonator connection		0.45	2.00	mA
			main) mode Note 9	f _{MX} = 20 MHz ^{Note 3} ,	Square wave input		0.28	1.90	mA
				$V_{DD} = 3.0 V$	Resonator connection		0.45	2.00	mA
				f _{MX} = 10 MHz ^{Note 3} ,	Square wave input		0.19	1.02	mA
				Vdd = 5.0 V	Resonator connection		0.26	1.10	mA
				fмx = 10 MHz ^{Note 3} ,	Square wave input		0.19	1.02	mA
				Vdd = 3.0 V	Resonator connection		0.26	1.10	mA
			HS	fpll = 48 MHz,	Vdd = 5.0 V		0.91	2.74	mA
		(High-speed	fclk = 24 MHz Note 3	VDD = 3.0 V		0.91	2.74	mA	
		main) mode (PLL	fpll = 48 MHz,	Vdd = 5.0 V		0.85	2.31	mA	
			operation)	fclk = 12 MHz Note 3	VDD = 3.0 V		0.85	2.31	mA
		Note 9	fpll = 48 MHz,	Vdd = 5.0 V		0.82	2.07	mA	
				fclk = 6 MHz ^{Note 3}	VDD = 3.0 V		0.82	2.07	mA
				fsuв = 32.768 kHz ^{Note 5}	Square wave input		0.25	0.57	μA
			clock	$T_A = -40^{\circ}C$	Resonator connection		0.44	0.76	<i>,</i> μΑ
			operation	fsuв = 32.768 kHz ^{Note 5}	Square wave input		0.30	0.57	, μA
				T₄ = +25°C	Resonator connection		0.49	0.76	, μΑ
				fs∪в = 32.768 kHz ^{Note 5}	Square wave input		0.33	1.17	, μΑ
				T _A = +50°C	Resonator connection		0.63	1.36	, μΑ
				fsuв = 32.768 kHz ^{Note 5}	Square wave input		0.46	1.97	, μA
				T _A = +70°C	Resonator connection		0.76	2.16	, μA
				fsuв = 32.768 kHz ^{Note 5}	Square wave input		0.97	3.37	, μA
				T₄ = +85°C	Resonator connection		1.16	3.56	, μA
				fsuв = 32.768 kHz ^{Note 5}	Square wave input		3.01	15.37	, μΑ
				T _A = +105°C	Resonator connection		3.20	15.56	μA
	DD3Note 6	STOP	T _A = −40°C	L	1		0.18	0.50	μA
		mode Note 8	T _A = +25°C				0.23	0.50	μA
		T _A = +50°C				0.26	1.10	μA	
			T _A = +70°C				0.29	1.90	μA
			T _A = +85°C				0.90	3.30	μA
			T _A = +105°C				2.94	15.30	μA

(Notes and Remarks are listed on the next page.)



- **Notes 1.** Total current flowing into VDD, including the input leakage current flowing when the level of the input pin is fixed to VDD or Vss. The values below the MAX. column include the peripheral operation current. However, not including the current flowing into the A/D converter, LVD circuit, USB2.0 host/function module, I/O port, and on-chip pull-up/pull-down resistors and the current flowing during data flash rewrite.
 - 2. During HALT instruction execution by flash memory.
 - 3. When high-speed on-chip oscillator and subsystem clock are stopped.
 - 4. When high-speed system clock and subsystem clock are stopped.
 - 5. When high-speed on-chip oscillator and high-speed system clock are stopped. When RTCLPC = 1 and setting ultra-low current consumption (AMPHS1 = 1). The current flowing into the RTC is included. However, not including the current flowing into the 12-bit interval timer and watchdog timer.
 - 6. Not including the current flowing into the RTC, 12-bit interval timer, and watchdog timer.
 - **7.** When Operating frequency setting of option byte = 48 MHz. When fHOCO is divided by HOCODIV. When RDIV[1:0] = 00 (divided by 2: default).
 - 8. Regarding the value for current to operate the subsystem clock in STOP mode, refer to that in HALT mode.
 - **9.** Relationship between operation voltage width, operation frequency of CPU and operation mode is as below.

HS (high-speed main) mode: 2.7 V \leq V_{DD} \leq 5.5 V@1 MHz to 24 MHz 2.4 V \leq V_{DD} \leq 5.5 V@1 MHz to 16 MHz

- Remarks 1. fHOCO: High-speed on-chip oscillator clock frequency (Max. 48 MHz)
 - 2. fill: Main system clock source frequency obtained by dividing the high-speed on-chip oscillator clock by 2, 4, or 8 (Max. 24 MHz)
 - **3.** fmx: High-speed system clock frequency (X1 clock oscillation frequency or external main system clock frequency)
 - 4. fPLL: PLL oscillation frequency
 - 5. fsub: Subsystem clock frequency (XT1 clock oscillation frequency)
 - 6. fcLK: CPU/peripheral hardware clock frequency
 - 7. Except subsystem clock operation, temperature condition of the TYP. value is $T_A = 25^{\circ}C$.



Parameter	Symbol		Conditions	MIN.	TYP.	MAX.	Unit
Low-speed on-chip oscillator operating current	FIL Note 1				0.20		μA
RTC operating current	IRTC Notes 1, 2, 3				0.02		μA
12-bit interval timer operating current	_{I⊤} Notes 1, 2, 4				0.02		μA
Watchdog timer operating current	IWDT Notes 1, 2, 5	fı∟ = 15 kHz			0.22		μA
A/D converter	ADC Notes 1,	When conversion	Normal mode, AV _{REFP} = V _{DD} = 5.0 V		1.3	1.8	mA
operating current	6	at maximum speed	Low voltage mode, $AV_{REFP} = V_{DD} = 3.0 V$		0.5	0.8	mA
A/D converter reference voltage current	IADREF Note				75.0		μA
Temperature sensor operating current	ITMPS Note 1				75.0		μA
LVD operating current	I _{LVD} Notes 1, 7				0.08		μA
Self-programming operating current	I _{FSP} ^{Notes 1,} 9				2.00	12.30	mA
BGO operating current	I _{BGO} Notes 1, 8				2.00	12.30	mA
SNOOZE operating	ISNOZ Note 1	ADC operation	The mode is performed Note 10		0.80	1.97	mA
current			The A/D conversion operations are performed, Low voltage mode, $AV_{REFP} = V_{DD} = 3.0 V$		1.20	3.00	mA
		CSI operation			0.70	1.56	mA

(TA = -40 to +105°C, 2.4 V \leq VDD \leq 5.5 V, Vss = 0 V) (1/2)

(Notes and Remarks are listed on the next page.)



$(T_A = -40 \text{ to } +105^{\circ}\text{C}, 2.4 \text{ V} \le \text{V}_{DD} \le 5.5 \text{ V}, \text{V}_{SS} = 0 \text{ V})$ (2/2)

Parameter	Symbol	Conditions	MIN.	TYP.	MAX.	Unit
USB operating current	IUSBH Note 11	 During USB communication operation under the following settings and conditions (V_{DD} = 5.0 V, T_A = +25°C): The internal power supply for the USB is used. X1 oscillation frequency (fx) = 12 MHz, PLL oscillation frequency (f_{PLL}) = 48 MHz The host controller (via two ports) is set to operate in full-speed mode with four pipes (end points) used simultaneously. (PIPE4: Bulk OUT transfer (64 bytes), PIPE5: Bulk IN transfer (64 bytes), PIPE6: Interrupt OUT transfer, PIPE7: Interrupt IN transfer). The USB ports (two ports) are individually connected to a peripheral function via a 0.5 m USB cable. 		9.0		mA
	IUSBF Note 11	 During USB communication operation under the following settings and conditions (V_{DD} = 5.0 V, T_A = +25°C): The internal power supply for the USB is used. X1 oscillation frequency (fx) = 12 MHz, PLL oscillation frequency (f_{PLL}) = 48 MHz The function controller is set to operate in full-speed mode with four pipes (end points) used simultaneously. (PIPE4: Bulk OUT transfer (64 bytes), PIPE5: Bulk IN transfer (64 bytes), PIPE6: Interrupt OUT transfer, PIPE7: Interrupt IN transfer). The USB port (one port) is connected to the host device via a 0.5 m USB cable. 		2.5		mA
	ISUSP Note 12	 During suspended state under the following settings and conditions (V_{DD} = 5.0 V, T_A = +25°C): The function controller is set to full-speed mode (the UDP0 pin is pulled up). The internal power supply for the USB is used. The system is set to STOP mode (When the high-speed on-chip oscillator, high-speed system clock, and subsystem clock are stopped. When the watchdog timer is stopped.). The USB port (one port) is connected to the host device via a 0.5 m USB cable. 		240		μA

(Notes and Remarks are listed on the next page.)



Notes 1. Current flowing to VDD.

- 2. When high speed on-chip oscillator and high-speed system clock are stopped.
- 3. Current flowing only to the real-time clock (RTC) (excluding the operating current of the low-speed on-chip ocsillator and the XT1 oscillator). The supply current of the RL78 microcontrollers is the sum of the values of either IDD1 or IDD2, and IRTC, when the real-time clock operates in operation mode or HALT mode. When the low-speed on-chip oscillator is selected, IFIL should be added. IDD2 subsystem clock operation includes the operational current of the real-time clock.
- 4. Current flowing only to the 12-bit interval timer (excluding the operating current of the low-speed on-chip ocsillator and the XT1 oscillator). The supply current of the RL78 microcontrollers is the sum of the values of either IDD1 or IDD2, and IIT, when the 12-bit interval timer operates in operation mode or HALT mode. When the low-speed on-chip oscillator is selected, IFIL should be added.
- 5. Current flowing only to the watchdog timer (including the operating current of the low-speed on-chip oscillator). The supply current of the RL78 microcontrollers is the sum of IDD1, IDD2 or IDD3 and IWDT when the watchdog timer is in operation.
- 6. Current flowing only to the A/D converter. The supply current of the RL78 microcontrollers is the sum of IDD1 or IDD2 and IADC when the A/D converter operates in an operation mode or the HALT mode.
- **7.** Current flowing only to the LVD circuit. The current value of the RL78/G1C is the sum of IDD1, IDD2 or IDD3 and ILVI when the LVD circuit operates in the Operating, HALT or STOP mode.
- 8. Current flowing only during data flash rewrite.
- 9. Current flowing only during self programming.
- 10. For shift time to the SNOOZE mode, see 19.3.3 SNOOZE mode the RL78/G1C User's Manual: Hardware.
- **11.** Current consumed only by the USB module and the internal power supply for the USB.
- **12.** Includes the current supplied from the pull-up resistor of the UDP0 pin to the pull-down resistor of the host device, in addition to the current consumed by this MCU during the suspended state.

Remarks 1. fil: Low-speed on-chip oscillator clock frequency

- 2. fsub: Subsystem clock frequency (XT1 clock oscillation frequency)
- 3. fcLK: CPU/peripheral hardware clock frequency
- 4. Temperature condition of the TYP. value is $T_A = 25^{\circ}C$



3.4 AC Characteristics

3.4.1 Basic operation

(TA = -40 to +105°C, 2.4 V \leq VDD \leq 5.5 V, Vss = 0 V)

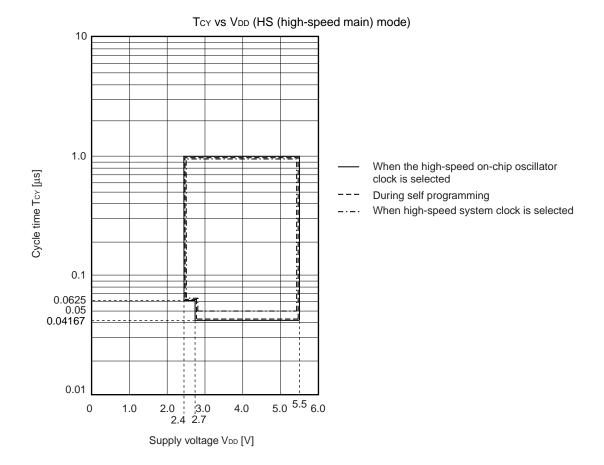
Items	Symbol	Conditions			MIN.	TYP.	MAX.	Unit
Instruction cycle (minimum	Тсү	Main	HS	$2.7V\!\leq\!V_{DD}\!\leq\!5.5V$	0.04167		1	μs
instruction execution time)		system clock (f _{MAIN}) operation	(High-speed main) mode	$2.4 \text{ V} \le \text{V}_{DD} < 2.7 \text{ V}$	0.0625		1	μs
		Subsystem c	lock (fsus)	$2.4V\!\leq\!V_{DD}\!\leq\!5.5V$	28.5	30.5	31.3	μs
		operation						
		In the self	HS	$2.7V\!\leq\!V_{DD}\!\leq\!5.5V$	0.04167		1	μs
		programming mode	(High-speed main) mode	$2.4 \text{ V} \le \text{V}_{DD} < 2.7 \text{ V}$	0.0625		1	μs
External system clock frequency	fex	$2.7 \text{ V} \leq \text{V}_{\text{DD}} \leq$	5.5 V		1.0		20.0	MHz
		$2.4 \text{ V} \leq \text{V}_{\text{DD}}$ <	: 2.7 V		1.0		16.0	MHz
	fexs				32		35	kHz
External system clock input	texh, texl	$2.7 \text{ V} \leq V_{\text{DD}} \leq$	5.5 V		24			ns
high-level width, low-level width		$2.4 \text{ V} \leq \text{V}_{\text{DD}}$ <	: 2.7 V		30			ns
	texhs, texls				13.7			μs
TI00 to TI03 input high-level width, low-level width	tтıн, tтı∟				1/fмск+10			ns
TO00 to TO03 output frequency	fто	High-speed r	main 4.0 V	$\leq V_{DD} \leq 5.5 \text{ V}$			12	MHz
		mode	2.7 V	\leq Vdd < 4.0 V			8	MHz
			2.4 V	\leq Vdd < 2.7 V			4	MHz
PCLBUZ0, PCLBUZ1 output	f PCL	High-speed r	nain 4.0 V	$\leq V_{DD} \leq 5.5 \text{ V}$			16	MHz
frequency		mode	2.7 V :	\leq Vdd < 4.0 V			8	MHz
			2.4 V :	\leq Vdd < 2.7 V			4	MHz
Interrupt input high-level width, low-level width	tinth, tintl	INTP0 to INT INTP8, INTP	-)	$\leq V_{DD} \leq 5.5 \text{ V}$	1			μs
Key interrupt input low-level width	t kr	KR0 to KR5	2.4 V	$\leq V_{DD} \leq 5.5 \text{ V}$	250			ns
RESET low-level width	trsl		•		10			μs

Remark fmck: Timer array unit operation clock frequency

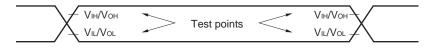
(Operation clock to be set by the CKS0n bit of timer mode register 0n (TMR0n). n: Channel number (n = 0 to 3))



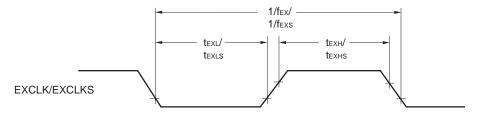
Minimum Instruction Execution Time during Main System Clock Operation



AC Timing Test Points

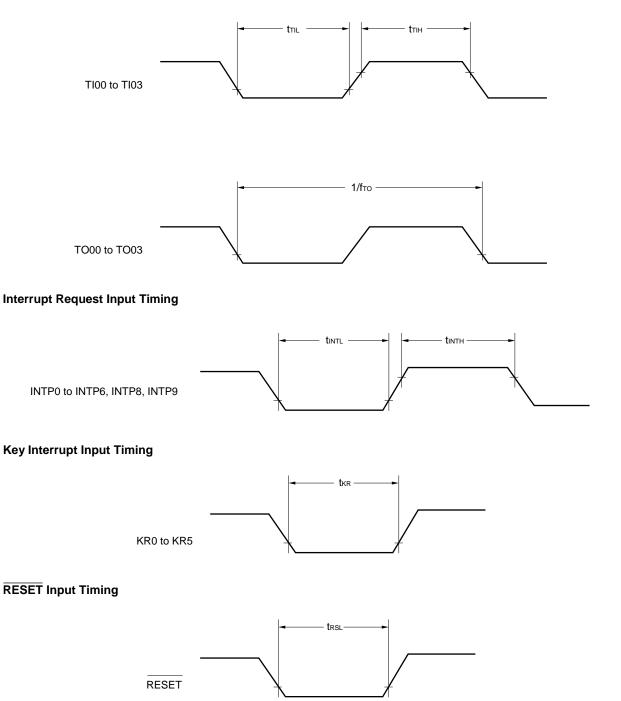


External System Clock Timing





TI/TO Timing





3.5 Peripheral Functions Characteristics

3.5.1 Serial array unit

(1) During communication at same potential (UART mode) (dedicated baud rate generator output) ($T_A = -40$ to +105°C, 2.4 V \leq V_{DD} \leq 5.5 V, V_{SS} = 0 V)

Parameter	Symbol	Conditions	MIN.	TYP.	MAX.	Unit
Transfer rate					fмск/12	bps
		Theoretical value of the maximum transfer rate $f_{MCK} = f_{CLK}$ ^{Note}			2.0	Mbps

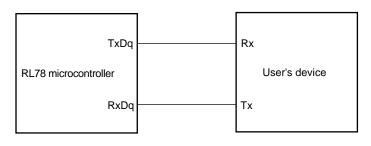
Note The maximum operating frequencies of the CPU/peripheral hardware clock (fcLK) are:

HS (high-speed main) mode: 24 MHz (2.7 V \leq VDD \leq 5.5 V)

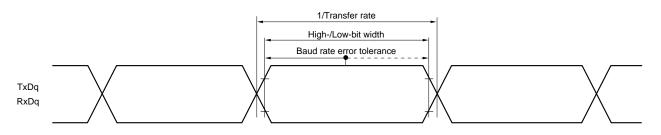
16 MHz (2.4 V \leq VDD \leq 5.5 V)

Caution Select the normal input buffer for the RxDq pin and the normal output mode for the TxDq pin by using port input mode register g (PIMg) and port output mode register g (POMg).

UART mode connection diagram (during communication at same potential)



UART mode bit width (during communication at same potential) (reference)



- **Remarks 1.** q: UART number (q = 0), g: PIM and POM number (g = 5)
 - 2. fmck: Serial array unit operation clock frequency

(Operation clock to be set by the CKSmn bit of serial mode register mn (SMRmn). m: Unit number,

n: Channel number (mn = 00))



(2)	During communication at same potential (CSI mode) (master mode, SCKp internal clock output)	
	$(T_A = -40 \text{ to } +105^{\circ}\text{C}, 2.4 \text{ V} \le V_{DD} \le 5.5 \text{ V}, \text{ Vss} = 0 \text{ V})$	

Parameter	Symbol	C	Conditions	MIN.	TYP.	MAX.	Unit
SCKp cycle time	tkCY1	tксү1 ≥ 4/fclк	$2.7~V \leq V_{\text{DD}} \leq 5.5~V$	250			ns
			$2.4~V \leq V_{\text{DD}} \leq 5.5~V$	500			ns
SCKp high-/low-level width	t кн1,	$4.0~V \leq V_{\text{DD}} \leq$	5.5 V	tkcy1/2-24			ns
	t KL1	$2.7~V \leq V_{\text{DD}} \leq$	5.5 V	tkcy1/2 - 36			ns
		$2.4~V \leq V_{\text{DD}} \leq$	$2.4~V \leq V_{DD} \leq 5.5~V$				ns
SIp setup time (to SCKp↑) ^{Note 1}	tsik1	$4.0~V \leq V_{\text{DD}} \leq$	5.5 V	66			ns
		$2.7~V \leq V_{\text{DD}} \leq$	5.5 V	66			ns
		$2.4~V \leq V_{\text{DD}} \leq$	5.5 V	113			ns
SIp hold time (from SCKp1) $^{\rm Note\ 2}$	tksi1			38			ns
Delay time from SCKp↓ to SOp output ^{Note 3}	tkso1	C = 30 pF ^{Note}	4			50	ns

Notes 1. When DAPmn = 0 and CKPmn = 0, or DAPmn = 1 and CKPmn = 1. The SIp setup time becomes "to SCKp↓" when DAPmn = 0 and CKPmn = 1, or DAPmn = 1 and CKPmn = 0.

- 2. When DAPmn = 0 and CKPmn = 0, or DAPmn = 1 and CKPmn = 1. The SIp hold time becomes "from SCKp↓" when DAPmn = 0 and CKPmn = 1, or DAPmn = 1 and CKPmn = 0.
- **3.** When DAPmn = 0 and CKPmn = 0, or DAPmn = 1 and CKPmn = 1. The delay time to SOp output becomes "from SCKp[↑]" when DAPmn = 0 and CKPmn = 1, or DAPmn = 1 and CKPmn = 0.
- 4. C is the load capacitance of the SCKp and SOp output lines.

Caution Select the normal input buffer for the SIp pin and the normal output mode for the SOp pin and SCKp pin by using port input mode register g (PIMg) and port output mode register g (POMg).

Remarks 1. p: CSI number (p = 00, 01), m: Unit number (m = 0), n: Channel number (n = 0, 1),

g: PIM and POM numbers (g = 0, 3, 5, 7)

2. fmck: Serial array unit operation clock frequency

(Operation clock to be set by the CKSmn bit of serial mode register mn (SMRmn). m: Unit number,

n: Channel number (mn = 00, 01))



(3)	During communication at same potential (CSI mode) (slave mode, SCKp external clock input)

Parameter	Symbol	Conc	ditions	MIN.	TYP.	MAX.	Unit
SCKp cycle time Note 5	t ксү2	$4.0~V \leq V_{\text{DD}} \leq 5.5~V$	20 MHz < fмск	16/fмск			ns
			fмск ≤ 20 MHz	12/fмск			ns
		$2.7~V \leq V_{\text{DD}} \leq 5.5~V$	16 MHz < fмск	16/fмск			ns
			fмск ≤ 16 MHz	12/fмск			ns
		$2.4~V \leq V_{\text{DD}} \leq 5.5~V$		12/fмск and 1000			ns
SCKp high-/low-level width	evel width t_{KH2} , $4.0 V \le t_{KL2}$		$4.0 \text{ V} \leq \text{EV}_{\text{DD0}} \leq 5.5 \text{ V}$				ns
		$2.7 \text{ V} \leq \text{EV}_{\text{DD0}} \leq 5.5 \text{ V}$	$7 \text{ V} \leq \text{EV}_{\text{DD0}} \leq 5.5 \text{ V}$				ns
		$2.4~V \leq V_{\text{DD}} \leq 5.5~V$		tксү2/2 – 36			ns
SIp setup time	tsik2	$2.7~V \leq V_{\text{DD}} \leq 5.5~V$		1/fмск+40			ns
(to SCKp↑) Note 1		$2.4~V \le V_{\text{DD}} \le 5.5~V$		1/fмск+60			ns
SIp hold time	tKSI2	$2.7~V \leq V_{\text{DD}} \leq 5.5~V$		1/fмск+62			ns
(from SCKp↑) Note 2	om SCKp↑) ^{Note 2}		$2.4 \text{ V} \leq \text{V}_{\text{DD}} \leq 5.5 \text{ V}$				ns
Delay time from SCKp \downarrow to	tkso2	C = 30 pF ^{Note 4}	$2.7~V \leq V_{\text{DD}} \leq 5.5~V$			2/fмск+66	ns
SOp output Note 3			$2.4~V \leq V_{\text{DD}} \leq 5.5~V$			2/fмск+113	ns

Notes 1. When DAPmn = 0 and CKPmn = 0, or DAPmn = 1 and CKPmn = 1. The SIp setup time becomes "to SCKp↓" when DAPmn = 0 and CKPmn = 1, or DAPmn = 1 and CKPmn = 0.

2. When DAPmn = 0 and CKPmn = 0, or DAPmn = 1 and CKPmn = 1. The SIp hold time becomes "from SCKp↓" when DAPmn = 0 and CKPmn = 1, or DAPmn = 1 and CKPmn = 0.

- **3.** When DAPmn = 0 and CKPmn = 0, or DAPmn = 1 and CKPmn = 1. The delay time to SOp output becomes "from SCKp[↑]" when DAPmn = 0 and CKPmn = 1, or DAPmn = 1 and CKPmn = 0.
- 4. C is the load capacitance of the SOp output lines.
- 5. Transfer rate in the SNOOZE mode: MAX. 1 Mbps

Caution Select the normal input buffer for the SIp pin and SCKp pin and the normal output mode for the SOp pin by using port input mode register g (PIMg) and port output mode register g (POMg).

Remarks 1. p: CSI number (p = 00, 01), m: Unit number (m = 0),

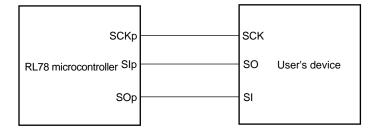
n: Channel number (n = 0, 1), g: PIM number (g = 0, 3, 5, 7)

2. fMCK: Serial array unit operation clock frequency

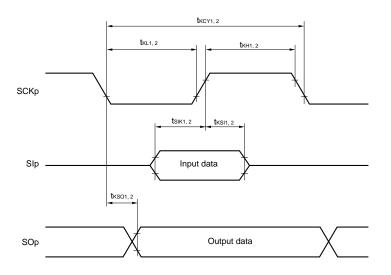
(Operation clock to be set by the CKSmn bit of serial mode register mn (SMRmn). m: Unit number, n: Channel number (mn = 00, 01))

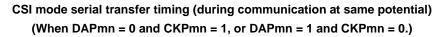


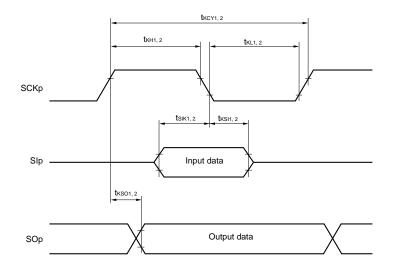
CSI mode connection diagram (during communication at same potential)



CSI mode serial transfer timing (during communication at same potential) (When DAPmn = 0 and CKPmn = 0, or DAPmn = 1 and CKPmn = 1.)







Remarks 1. p: CSI number (p = 00, 01)

2. m: Unit number, n: Channel number (mn = 00, 01)



$(IA = -40 \text{ to } +105^{\circ}\text{C}, 2.4 \text{ V} \le \text{VDD} \le$	5.5 V, Vss = 0 V				
Parameter	Symbol	Conditions	MIN.	MAX.	Unit
SCLr clock frequency	fsc∟	$2.7 \text{ V} \leq \text{V}_{\text{DD}} \leq 5.5 \text{ V},$		400 Note 1	kHz
		$C_b = 50 \text{ pF}, R_b = 2.7 \text{ k}\Omega$			
		$2.4 \text{ V} \leq \text{V}_{\text{DD}} \leq 5.5 \text{ V},$		100 ^{Note 1}	kHz
		$C_b = 100 \text{ pF}, R_b = 3 \text{ k}\Omega$			
Hold time when SCLr = "L"	tLow	$2.7~V \leq V_{\text{DD}} \leq 5.5~V,$	1200		ns
		$C_b = 50 \text{ pF}, R_b = 2.7 \text{ k}\Omega$			
		$2.4~V \leq V_{\text{DD}} \leq 5.5~V,$	4600		ns
		$C_b = 100 \text{ pF}, R_b = 3 \text{ k}\Omega$			
Hold time when SCLr = "H"	tнigн	$2.7~V \leq V_{\text{DD}} \leq 5.5~V,$	1200		ns
		$C_b = 50 \text{ pF}, R_b = 2.7 \text{ k}\Omega$			
		$2.4~V \leq V_{\text{DD}} \leq 5.5~V,$	4600		ns
		$C_b = 100 \text{ pF}, R_b = 3 \text{ k}\Omega$			
Data setup time (reception)	tsu:dat	$2.7~V \leq V_{\text{DD}} \leq 5.5~V,$	1/fмск + 220		ns
		$C_b = 50 \text{ pF}, R_b = 2.7 \text{ k}\Omega$	Note 2		
		$2.4~V \leq V_{DD} \leq 5.5~V,$	1/fмск + 580		ns
		$C_b = 100 \text{ pF}, R_b = 3 \text{ k}\Omega$	Note 2		
Data hold time (transmission)	thd:dat	$2.7 \text{ V} \leq \text{V}_{\text{DD}} \leq 5.5 \text{ V},$	0	770	ns
		$C_b = 50 \text{ pF}, R_b = 2.7 \text{ k}\Omega$			
		$2.4~V \leq V_{\text{DD}} \leq 5.5~V,$	0	1420	ns
		$C_b = 100 \text{ pF}, R_b = 3 \text{ k}\Omega$			

(4) During communication at same potential (simplified l^2C mode) (T_A = -40 to +105°C. 2.4 V \leq V_{DD} \leq 5.5 V, V_{SS} = 0 V)

Notes 1. The value must also be equal to or less than $f_{MCK}/4$.

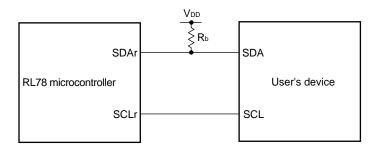
2. Set the fMCK value to keep the hold time of SCLr = "L" and SCLr = "H".

Caution Select the normal input buffer and the N-ch open drain output (VDD tolerance) mode for the SDAr pin and the normal output mode for the SCLr pin by using port input mode register g (PIMg) and port output mode register h (POMh).

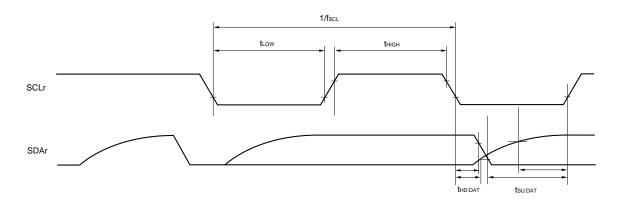
(Caution and Remarks are listed on the next page.)



Simplified I²C mode mode connection diagram (during communication at same potential)



Simplified I²C mode serial transfer timing (during communication at same potential)



Remarks 1. R_b[Ω]:Communication line (SDAr) pull-up resistance, C_b[F]: Communication line (SDAr, SCLr) load capacitance

2. r: IIC number (r = 00, 01), g: PIM number (g = 5), h: POM number (h = 3, 5)

3. fMCK: Serial array unit operation clock frequency

(Operation clock to be set by the CKSmn bit of serial mode register mn (SMRmn). m: Unit number (m

= 0), n: Channel number (n = 0, 1), mn = 00, 01)



(5) Communication at different potential (2.5 V, 3 V) (UART mode) (1/2) $(T_A = -40 \text{ to } +105^{\circ}\text{C}, 2.4 \text{ V} \le \text{V}_{DD} \le 5.5 \text{ V}, \text{V}_{SS} = 0 \text{ V})$

Parameter	Symbol		$50 \leq 3.3 \text{ V}, \text{ V} \text{ss} = 0 \text{ V}$ Conditio		MIN.	TYP.	MAX.	Unit
Transfer rate		reception	$4.0 V \le V_{DD} \le 5.5 V$, $2.7 V \le V_b \le 4.0 V$				fмск/12 Note 1	bps
				Theoretical value of the maximum transfer rate $f_{CLK} = 24$ MHz, $f_{MCK} = f_{CLK}$ Note 2			2.0	Mbps
			$2.7 \text{ V} \leq \text{V}_{\text{DD}} < 4.0 \text{ V},$ $2.3 \text{ V} \leq \text{V}_{b} \leq 2.7 \text{ V}$				fмск/12 Note 1	bps
				Theoretical value of the maximum transfer rate $f_{CLK} = 24$ MHz, $f_{MCK} = f_{CLK}$ Note 2			2.0	Mbps
			$2.4 \text{ V} \leq \text{V}_{\text{DD}} < 3.3 \text{ V},$ $1.6 \text{ V} \leq \text{V}_{b} \leq 2.0 \text{ V}$				fмск/12 Note 1	bps
				Theoretical value of the maximum transfer rate $f_{CLK} = 24$ MHz, $f_{MCK} = f_{CLK}$ Note 2			2.0	Mbps

Notes 1. Use it with $V_{DD} \ge V_b$.

- 2. The maximum operating frequencies of the CPU/peripheral hardware clock (fcLK) are: HS (high-speed main) mode: 24 MHz ($2.7 \text{ V} \le \text{V}_{\text{DD}} \le 5.5 \text{ V}$) 16 MHz ($2.4 \text{ V} \le \text{V}_{\text{DD}} \le 5.5 \text{ V}$)
- Caution Select the TTL input buffer for the RxDq pin and the N-ch open drain output (V_{DD} tolerance) mode for the TxDq pin by using port input mode register g (PIMg) and port output mode register g (POMg). For V_H and V_L, see the DC characteristics with TTL input buffer selected
- Remarks 1. Vb[V]: Communication line voltage
 - **2.** q: UART number (q = 0), g: PIM and POM number (g = 5)
 - 3. fmck: Serial array unit operation clock frequency

(Operation clock to be set by the CKSmn bit of serial mode register mn (SMRmn). m: Unit number,

n: Channel number (mn = 00)



(5)	Comn	nunicati	on at diff	erent pote	ntial (2.5 V, 3	V) (UART mode) (2/2)

Parameter	Symbol		Conditions			TYP.	MAX.	Unit
Transfer rate		transmission	$4.0~V \leq V_{DD} \leq 5.5~V,$				Note 1	bps
			$2.7~V \leq V_b \leq 4.0~V$	Theoretical value of the maximum transfer rate $C_b = 50 \text{ pF}, R_b = 1.4 \text{ k}\Omega, V_b = 2.7 \text{ V}$			2.6 ^{Note 2}	Mbps
			$2.7 \text{ V} \le \text{V}_{\text{DD}} < 4.0 \text{ V},$				Note 3	bps
			$2.3~V \leq V_b \leq 2.7~V$	Theoretical value of the maximum transfer rate $C_b = 50 \text{ pF}, R_b = 2.7 \text{ k}\Omega, V_b = 2.3 \text{ V}$			1.2 ^{Note 4}	Mbps
			$2.4 \text{ V} \le \text{V}_{\text{DD}} < 3.3 \text{ V},$ $1.6 \text{ V} \le \text{V}_{\text{b}} \le 2.0 \text{ V}$				Notes 5, 6	bps
				Theoretical value of the maximum transfer rate			0.43 Note 7	Mbps
				$C_b = 50 \text{ pF}, R_b = 5.5 \text{ k}\Omega, V_b = 1.6 \text{ V}$				

Notes 1. The smaller maximum transfer rate derived by using fMCK/12 or the following expression is the valid maximum transfer rate.

Expression for calculating the transfer rate when 4.0 V \leq V_{DD} \leq 5.5 V and 2.7 V \leq V_b \leq 4.0 V

Maximum transfer rate =

$$\frac{1}{\{-Cb \times Rb \times \ln (1 - \frac{2.2}{Vb})\} \times 3}$$
 [bps]

Baud rate error (theoretical value) =

 $\frac{1}{\text{Transfer rate} \times 2} - \{-\text{Cb} \times \text{Rb} \times \ln(1 - \frac{2.2}{\text{Vb}})\}$ $\frac{1}{(\frac{1}{\text{Transfer rate}}) \times \text{Number of transferred bits}}$

- × 100 [%]

* This value is the theoretical value of the relative difference between the transmission and reception sides.

- 2. This value as an example is calculated when the conditions described in the "Conditions" column are met. Refer to Note 1 above to calculate the maximum transfer rate under conditions of the customer.
- 3. The smaller maximum transfer rate derived by using fMck/12 or the following expression is the valid maximum transfer rate.

Expression for calculating the transfer rate when 2.7 V \leq VDD < 4.0 V and 2.3 V \leq Vb \leq 2.7 V

Maximum transfer rate =
$$\frac{1}{\{-Cb \times Rb \times ln (1 - \frac{2.0}{Vb})\} \times 3}$$
 [bps]

rate error (theoretical value) =
$$\frac{\frac{1}{\text{Transfer rate} \times 2} - \{-\text{Cb} \times \text{Rb} \times \ln(1 - \frac{2.0}{\text{Vb}})\}}{(\frac{1}{\text{Transfer rate}}) \times \text{Number of transferred bits}} \times 100 [\%]$$

* This value is the theoretical value of the relative difference between the transmission and reception sides.

- **4.** This value as an example is calculated when the conditions described in the "Conditions" column are met. Refer to Note 3 above to calculate the maximum transfer rate under conditions of the customer.
- **5.** Use it with $V_{DD} \ge V_b$.

Baud



Notes 6. The smaller maximum transfer rate derived by using fMCK/12 or the following expression is the valid maximum transfer rate.

Expression for calculating the transfer rate when 2.4 V \leq V_DD < 3.3 V and 1.6 V \leq V_b \leq 2.0 V

Maximum transfer rate =
$$\frac{1}{\{-Cb \times Rb \times ln (1 - \frac{1.5}{Vb})\} \times 3}$$
 [bps]

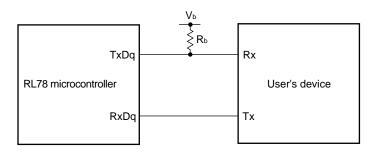
Baud rate error (theoretical value) =

$$\frac{\frac{1}{\text{Transfer rate} \times 2} - \{-\text{Cb} \times \text{Rb} \times \ln(1 - \frac{1.5}{\text{Vb}})\}}{(\frac{1}{\text{Transfer rate}}) \times \text{Number of transferred bits}} \times 100 [\%]$$

* This value is the theoretical value of the relative difference between the transmission and reception sides.7. This value as an example is calculated when the conditions described in the "Conditions" column are

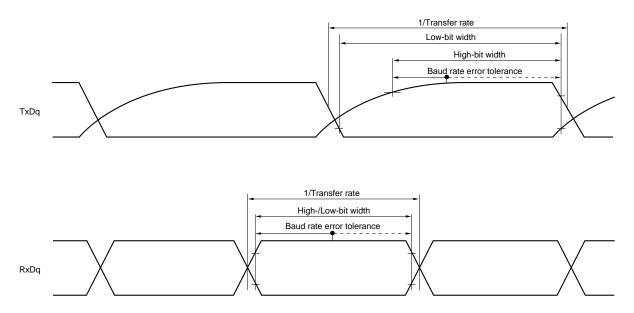
- 7. This value as an example is calculated when the conditions described in the "Conditions" column are met. Refer to Note 6 above to calculate the maximum transfer rate under conditions of the customer.
- Caution Select the TTL input buffer for the RxDq pin and the N-ch open drain output (V_{DD} tolerance) mode for the TxDq pin by using port input mode register g (PIMg) and port output mode register g (POMg). For V_H and V_L, see the DC characteristics with TTL input buffer selected

UART mode connection diagram (during communication at different potential)









- Remarks 1.
 R_b[Ω]:Communication line (TxDq) pull-up resistance, C_b[F]: Communication line (TxDq) load

 capacitance, V_b[V]: Communication line voltage
 - **2.** q: UART number (q = 0), g: PIM and POM number (g = 5)
 - 3. fmck: Serial array unit operation clock frequency

(Operation clock to be set by the CKSmn bit of serial mode register mn (SMRmn).

m: Unit number, n: Channel number (mn = 00))



(6) Communication at different potential (1.8 V, 2.5 V, 3 V) (CSI mode) (master mode, SCKp... internal clock output) (1/2)

Parameter	Symbol		Conditions	MIN.	TYP.	MAX.	Unit
SCKp cycle time	tkcy1	tkcy1 ≥ 4/fclk	$\begin{array}{l} 4.0 \ V \leq V_{DD} \leq 5.5 \ V, \\ 2.7 \ V \leq V_b \leq 4.0 \ V, \\ C_b = 30 \ pF, \ R_b = 1.4 \ k\Omega \end{array}$	600			ns
			$\begin{array}{l} 2.7 \ V \leq V_{DD} < 4.0 \ V, \\ 2.3 \ V \leq V_b \leq 2.7 \ V, \\ C_b = 30 \ pF, \ R_b = 2.7 \ k\Omega \end{array}$	1000			ns
			$\begin{array}{l} 2.4 \; V \leq V_{DD} < 3.3 \; V, \\ 2.4 \; V \leq V_b \leq 2.0 \; V, \\ C_b = 30 \; pF, \; R_b = 5.5 \; k\Omega \end{array}$	2300			ns
SCKp high-level width	tкнı	$\begin{array}{l} 4.0 \; V \leq V_{DD} \leq 5.5 \; V, \; 2.7 \; V \leq V_b \leq 4.0 \; V, \\ C_b = 30 \; pF, \; R_b = 1.4 \; k\Omega \end{array}$		tксү1/2 – 150			ns
		$2.7 \text{ V} \le \text{V}_{\text{DD}} <$ $C_{\text{b}} = 30 \text{ pF, F}$	$x 4.0 V, 2.3 V \le V_b \le 2.7 V,$ R _b = 2.7 kΩ	tксү1/2 – 340			ns
		$2.4 \text{ V} \le \text{V}_{\text{DD}} <$ $C_{\text{b}} = 30 \text{ pF}, \text{ F}$	$x 3.3$ V, 1.6 V \le V _b \le 2.0 V, R _b = 5.5 kΩ	tксү1/2 – 916			ns
SCKp low-level width	tĸ∟1	$4.0 \text{ V} \leq \text{V}_{\text{DD}} \leq C_{\text{b}} = 30 \text{ pF, F}$	≤ 5.5 V, 2.7 V \leq Vb ≤ 4.0 V, R_b = 1.4 k\Omega	tkcy1/2-24			ns
		$2.7 \text{ V} \le \text{V}_{\text{DD}} <$ $C_{\text{b}} = 30 \text{ pF}, \text{ F}$		tксү1/2-36			ns
		$2.4 \text{ V} \leq \text{V}_{\text{DD}} <$ $C_{\text{b}} = 30 \text{ pF}, \text{ F}$: 3.3 V, 1.6 V \leq Vb \leq 2.0 V, Rb = 5.5 k\Omega	tксү1/2 – 100			ns

 $(T_A = -40 \text{ to } +105^{\circ}\text{C}, 2.4 \text{ V} \le \text{V}_{DD} \le 5.5 \text{ V}, \text{V}_{SS} = 0 \text{ V})$

Cautions 1. Select the TTL input buffer for the SIp pin and the N-ch open drain output (V_{DD} tolerance) mode for the SOp pin and SCKp pin by using port input mode register g (PIMg) and port output mode register g (POMg). For V_{IH} and V_{IL}, see the DC characteristics with TTL input buffer selected.

2. Use it with $V_{DD} \ge V_b$.

(Remarks are listed two pages after the next page.)



(6) Communication at different potential (1.8 V, 2.5 V, 3 V) (CSI mode) (master mode, SCKp... internal clock output) (2/2)

Parameter	Symbol	Conditions	MIN.	TYP.	MAX.	Unit
SIp setup time	tsik1	$4.0~V \leq V_{\text{DD}} \leq 5.5~V,~2.7~V \leq V_{\text{b}} \leq 4.0~V,$	162			ns
(to SCKp↑) Note 1		$C_{\rm b}=30~pF,~R_{\rm b}=1.4~k\Omega$				
		$2.7 \ V \leq V_{DD} < 4.0 \ V, \ 2.3 \ V \leq V_b \leq 2.7 \ V,$	354			ns
		$C_{\rm b}=30~pF,~R_{\rm b}=2.7~k\Omega$				
		$2.4 \ V \leq V_{\text{DD}} < 3.3 \ V, \ 1.6 \ V \leq V_{\text{b}} \leq 2.0 \ V^{\text{Note 3}},$	958			ns
		$C_{\rm b}=30~pF,~R_{\rm b}=5.5~k\Omega$				
SIp hold time	tksi1	$4.0 \ V \leq V_{\text{DD}} \leq 5.5 \ V, \ 2.7 \ V \leq V_{\text{b}} \leq 4.0 \ V,$	38			ns
(from SCKp↑) Note 1		$C_{\rm b}=30~pF,~R_{\rm b}=1.4~k\Omega$				
		$2.7 \ V \leq V_{DD} < 4.0 \ V, \ 2.3 \ V \leq V_b \leq 2.7 \ V,$	38			ns
		$C_{\rm b}=30~pF,~R_{\rm b}=2.7~k\Omega$				
		$2.4 \text{ V} \leq \text{V}_{\text{DD}} < 3.3 \text{ V}, \ 1.6 \text{ V} \leq \text{V}_{\text{b}} \leq 2.0 \text{ V}^{\text{Note }3},$	38			ns
		$C_{\rm b}=30~pF,~R_{\rm b}=5.5~k\Omega$				
Delay time from SCKp↓ to	tkso1	$4.0~V \leq V_{\text{DD}} \leq 5.5~V,~2.7~V \leq V_{\text{b}} \leq 4.0~V,$			200	ns
SOp output Note 1		$C_{\rm b}=30~pF,~R_{\rm b}=1.4~k\Omega$				
		$2.7 \ V \leq V_{DD} < 4.0 \ V, \ 2.3 \ V \leq V_b \leq 2.7 \ V,$			390	ns
		$C_{\rm b}=30~pF,~R_{\rm b}=2.7~k\Omega$				
		$2.4 \text{ V} \leq \text{V}_{\text{DD}} < 3.3 \text{ V}, \ 1.6 \text{ V} \leq \text{V}_{\text{b}} \leq 2.0 \text{ V}^{\text{Note }3},$			966	ns
		$C_{\rm b}=30~pF,~R_{\rm b}=5.5~k\Omega$				
SIp setup time	tsik1	$4.0 \ V \leq V_{DD} \leq 5.5 \ V, \ 2.7 \ V \leq V_b \leq 4.0 \ V,$	88			ns
(to SCKp↓) Note 2		$C_{\rm b}=30~pF,~R_{\rm b}=1.4~k\Omega$				
		$2.7 \ V \leq V_{DD} < 4.0 \ V, \ 2.3 \ V \leq V_b \leq 2.7 \ V,$	88			ns
		$C_{\rm b}=30~pF,~R_{\rm b}=2.7~k\Omega$				
		$2.4 \ V \leq V_{\text{DD}} < 3.3 \ V, \ 1.6 \ V \leq V_{\text{b}} \leq 2.0 \ V^{\text{Note 3}},$	220			ns
		$C_{\rm b}=30~pF,~R_{\rm b}=5.5~k\Omega$				
SIp hold time	tksi1	$4.0~V \leq V_{\text{DD}} \leq 5.5~V,~2.7~V \leq V_{b} \leq 4.0~V,$	38			ns
(from SCKp↓) Note 2		$C_{\rm b}=30~pF,~R_{\rm b}=1.4~k\Omega$				
		$2.7 \ V \leq V_{DD} < 4.0 \ V, \ 2.3 \ V \leq V_b \leq 2.7 \ V,$	38			ns
		$C_{\rm b}=30~pF,~R_{\rm b}=2.7~k\Omega$				
		$2.4 \ V \leq V_{\text{DD}} < 3.3 \ V, \ 1.6 \ V \leq V_{\text{b}} \leq 2.0 \ V^{\text{Note 3}},$	38			ns
		C_{b} = 30 pF, R_{b} = 5.5 k Ω				
Delay time from SCKp↑ to	tkso1	$4.0 \ \text{V} \leq \text{V}_{\text{DD}} \leq 5.5 \ \text{V}, \ 2.7 \ \text{V} \leq \text{V}_{\text{b}} \leq 4.0 \ \text{V}, \label{eq:VDD}$			50	ns
SOp output Note 2		$C_{\rm b}=30~pF,~R_{\rm b}=1.4~k\Omega$				
		$2.7 \ V \leq V_{DD} < 4.0 \ V, \ 2.3 \ V \leq V_b \leq 2.7 \ V,$			50	ns
		$C_{\rm b}=30~pF,~R_{\rm b}=2.7~k\Omega$				
		$2.4 \text{ V} \leq \text{V}_{\text{DD}} < 3.3 \text{ V}, \ 1.6 \text{ V} \leq \text{V}_{\text{b}} \leq 2.0 \text{ V}^{\text{Note 3}},$			50	ns
		$C_b = 30 \text{ pF}, R_b = 5.5 \text{ k}\Omega$				

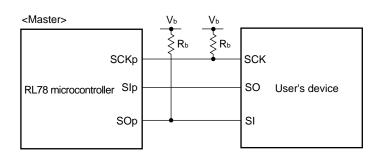
 $(T_A = -40 \text{ to } +105^{\circ}\text{C}, 2.4 \text{ V} \le \text{V}_{DD} \le 5.5 \text{ V}, \text{V}_{SS} = 0 \text{ V})$

(Notes, Cautions and Remarks are listed on the next page.)



- **Notes 1.** When DAPmn = 0 and CKPmn = 0, or DAPmn = 1 and CKPmn = 1.
 - **2.** When DAPmn = 0 and CKPmn = 1, or DAPmn = 1 and CKPmn = 0.
 - **3.** Use it with $V_{DD} \ge V_b$.
- Caution Select the TTL input buffer for the SIp pin and the N-ch open drain output (V_{DD} tolerance) mode for the SOp pin and SCKp pin by using port input mode register g (PIMg) and port output mode register g (POMg). For V_{IH} and V_{IL}, see the DC characteristics with TTL input buffer selected.

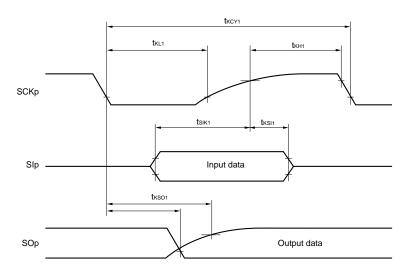
CSI mode connection diagram (during communication at different potential)



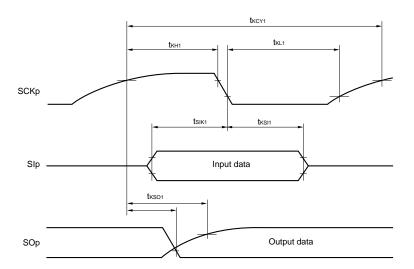
- **Remarks 1.** R_b[Ω]:Communication line (SCKp, SOp) pull-up resistance, C_b[F]: Communication line (SCKp, SOp) load capacitance, V_b[V]: Communication line voltage
 - p: CSI number (p = 00), m: Unit number , n: Channel number (mn = 00), g: PIM and POM number (g = 0, 3, 5, 7)
 - **3.** fMCK: Serial array unit operation clock frequency (Operation clock to be set by the CKSmn bit of serial mode register mn (SMRmn). m: Unit number, n: Channel number (mn = 00))
 - **4.** CSI01 cannot communicate at different potential. Use other CSI for communication at different potential.



CSI mode serial transfer timing (master mode) (during communication at different potential) (When DAPmn = 0 and CKPmn = 0, or DAPmn = 1 and CKPmn = 1.)



CSI mode serial transfer timing (master mode) (during communication at different potential) (When DAPmn = 0 and CKPmn = 1, or DAPmn = 1 and CKPmn = 0.)



- **Remarks 1.** p: CSI number (p = 00), m: Unit number, n: Channel number (mn = 00), g: PIM and POM number (g = 0, 3, 5, 7)
 - 2. CSI01 cannot communicate at different potential. Use other CSI for communication at different potential.



(7) Communication at different potential (1.8 V, 2.5 V, 3 V) (CSI mode) (slave mode, SCKp... external clock input)

Parameter	Symbol	C	Conditions	MIN.	TYP.	MAX.	Unit
SCKp cycle time Note 1	tkCY2	$4.0 V \le V_{DD} \le 5.5 V$,	20 MHz < fмск ≤24 MHz	24/fмск			ns
		$2.7V{\leq}V_b{\leq}4.0V$	8 MHz < fмск ≤20 MHz	20/f мск			ns
			4 MHz < fмск ≤ 8 MHz	16/fмск			ns
			fмск ≤4 MHz	12/fмск			ns
		$2.7 \text{ V} \le \text{V}_{\text{DD}} < 4.0 \text{ V},$	20 MHz < fмск ≤24 MHz	32/f мск			ns
		$2.3 V \le V_b \le 2.7 V$	16 MHz < fмск ≤ 20 MHz	28/fмск			ns
			8 MHz < fмск ≤ 16 MHz	24/fмск			ns
			4 MHz < fмск ≤ 8 MHz	16/fмск			ns
			fмск ≤4 MHz	12/fмск			ns
		$2.4 \text{ V} \le \text{V}_{\text{DD}} < 3.3 \text{ V},$	20 MHz < fмск ≤24 MHz	72/f мск			ns
		$1.6 \: V {\le} V_b {\le} 2.0 \: V^{\: \text{Note}}$	16 MHz < fмск ≤ 20 MHz	64/f мск			ns
		2	8 MHz < fмск ≤ 16 MHz	52/f мск			ns
			4 MHz < fмск ≤ 8 MHz	32/f мск			ns
			fмск ≤4 MHz	20/f мск			ns
SCKp high-/low-level width	tкн2, tк∟2	$4.0 \text{ V} \leq \text{V}_{\text{DD}} \leq 5.5 \text{ V}$	$^{\prime},2.7~V\leq V_b\leq 4.0~V$	tксү2/2 – 24			ns
		$2.7 \text{ V} \le \text{V}_{\text{DD}} < 4.0 \text{ V}$	$V_{\rm b}$ 2.3 V \leq V _b \leq 2.7 V	tксү2/2 – 36			ns
		$2.4 \text{ V} \leq \text{V}_{\text{DD}} < 3.3 \text{ V}$	/, 1.6 V \leq V $_{b}$ \leq 2.0 V $^{Note 2}$	tксү2/2 – 100			ns
SIp setup time (to SCKp↑) ^{Note 3}	tsik2	$4.0 \text{ V} \le \text{V}_{\text{DD}} \le 5.5 \text{ V}$	$V, 2.7 \text{ V} \le V_b \le 4.0 \text{ V}$	1/fмск + 40			ns
		$2.7 \text{ V} \leq \text{V}_{\text{DD}} < 4.0 \text{ V}$	$V, 2.3 V \le V_b \le 2.7 V$	1/fмск + 40			ns
		$2.4 \text{ V} \leq \text{V}_{\text{DD}} < 3.3 \text{ V}$	/, 1.6 V \leq V $_{b}$ \leq 2.0 V $^{Note 2}$	1/fмск + 60			ns
SIp hold time (from SCKp↑) ^{Note 4}	tksi2			1/fмск + 62			ns
Delay time from SCKp↓ to SOp output ^{Note 5}	tĸso2	$4.0 \text{ V} \le \text{V}_{\text{DD}} \le 5.5 \text{ V}$	$V_{\rm v}, 2.7~V \le V_{\rm b} \le 4.0~V_{\rm v},$			2/fмск +	ns
		$C_b = 30 \text{ pF}, R_b = 1.$	4 kΩ			240	
		$2.7 \text{ V} \leq \text{V}_{\text{DD}} < 4.0 \text{ V}$	$V_{\rm r}, 2.3 \ V \le V_{\rm b} \le 2.7 \ V_{\rm r},$			2/fмск +	ns
		$C_b = 30 \text{ pF}, R_b = 2.$	7 kΩ			428	
		$2.4 \text{ V} \leq \text{V}_{\text{DD}} < 3.3 \text{ V}$	$V_{\rm h}, \ 1.6 \ V \leq V_{\rm b} \leq 2.0 \ V^{\text{Note 2}},$			2/fмск +	ns
		$C_b = 30 \text{ pF}, R_b = 5.$	5 kΩ			1146	

 $(T_A = -40 \text{ to } +105^{\circ}\text{C}, 2.4 \text{ V} \le \text{V}_{DD} \le 5.5 \text{ V}, \text{V}_{SS} = 0 \text{ V})$

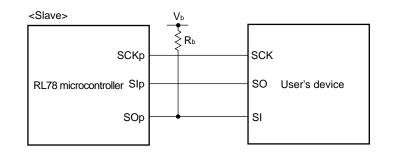
Notes 1. Transfer rate in the SNOOZE mode: MAX. 1 Mbps

- **2.** Use it with $V_{DD} \ge V_b$.
- 3. When DAPmn = 0 and CKPmn = 0, or DAPmn = 1 and CKPmn = 1. The SIp setup time becomes "to SCKp↓" when DAPmn = 0 and CKPmn = 1, or DAPmn = 1 and CKPmn = 0.
- 4. When DAPmn = 0 and CKPmn = 0, or DAPmn = 1 and CKPmn = 1. The SIp hold time becomes "from SCKp↓" when DAPmn = 0 and CKPmn = 1, or DAPmn = 1 and CKPmn = 0.
- 5. When DAPmn = 0 and CKPmn = 0, or DAPmn = 1 and CKPmn = 1. The delay time to SOp output becomes "from SCKp[↑]" when DAPmn = 0 and CKPmn = 1, or DAPmn = 1 and CKPmn = 0.

(Caution and Remarks are listed on the next page.)

Caution Select the TTL input buffer for the SIp pin and SCKp pin and the N-ch open drain output (V_{DD} tolerance) mode for the SOp pin by using port input mode register g (PIMg) and port output mode register g (POMg). For V_H and V_L, see the DC characteristics with TTL input buffer selected.

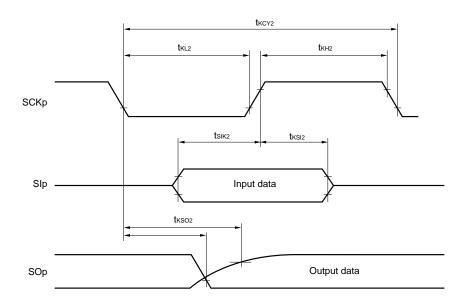
CSI mode connection diagram (during communication at different potential)

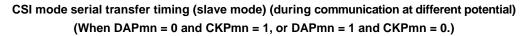


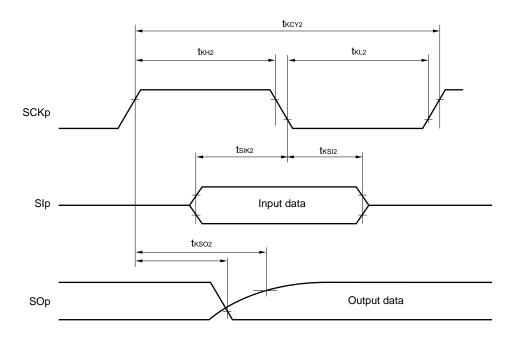
- **Remarks 1.** R_b[Ω]:Communication line (SOp) pull-up resistance, C_b[F]: Communication line (SOp) load capacitance, V_b[V]: Communication line voltage
 - 2. p: CSI number (p = 00), m: Unit number, n: Channel number (mn = 00), g: PIM and POM number (g = 0, 3, 5, 7)
 - fMCK: Serial array unit operation clock frequency
 (Operation clock to be set by the CKSmn bit of serial mode register mn (SMRmn).
 m: Unit number, n: Channel number (mn = 00))
 - **4.** CSI01 cannot communicate at different potential. Use other CSI for communication at different potential.



CSI mode serial transfer timing (slave mode) (during communication at different potential) (When DAPmn = 0 and CKPmn = 0, or DAPmn = 1 and CKPmn = 1.)







- **Remarks 1.** p: CSI number (p = 00), m: Unit number, n: Channel number (mn = 00), g: PIM and POM number (g = 0, 3, 5, 7)
 - **2.** CSI01 cannot communicate at different potential. Use other CSI for communication at different potential.



(8) Communication at different potential (1.8 V, 2.5 V, 3 V) (simplified I^2C mode) (1/2) (T_A = -40 to +105°C, 2.4 V < V_{DD} < 5.5 V, V_{SS} = 0 V)

(T _A = −40 to +105°C, 2.4 V ≤ V _{DD} ≤ 5.5 V Parameter	Symbol	Conditions	MIN.	MAX.	Unit
SCLr clock frequency	fsc∟			400 ^{Note 1}	kHz
		$\begin{array}{l} 2.7 \; V \leq V_{DD} < 4.0 \; V, \\ 2.3 \; V \leq V_b < 2.7 \; V, \\ C_b = 50 \; pF, \; R_b = 2.7 \; k\Omega \end{array}$		400 ^{Note 1}	kHz
				100 ^{Note 1}	kHz
		$\begin{array}{l} 2.7 \ V \leq V_{DD} < 4.0 \ V, \\ 2.3 \ V \leq V_b < 2.7 \ V, \\ C_b = 100 \ pF, \ R_b = 2.7 \ k\Omega \end{array}$		100 ^{Note 1}	kHz
		$ \begin{split} & 2.4 \ V \leq V_{DD} < 3.3 \ V, \\ & 1.6 \ V \leq V_b \leq 2.0 \ V^{\text{Note 2}}, \\ & C_b = 100 \ pF, \ R_b = 5.5 \ k\Omega \end{split} $		100 ^{Note 1}	kHz
Hold time when SCLr = "L"	tLow		1200		ns
		$\label{eq:VDD} \begin{array}{l} 2.7 \ V \leq V_{DD} < 4.0 \ V, \\ 2.3 \ V \leq V_b < 2.7 \ V, \\ C_b = 50 \ pF, \ R_b = 2.7 \ k\Omega \end{array}$	1200		ns
			4600		ns
		$\begin{array}{l} 2.7 \; V \leq V_{DD} < 4.0 \; V, \\ 2.3 \; V \leq V_b < 2.7 \; V, \\ C_b = 100 \; p\text{F}, \; R_b = 2.7 \; k\Omega \end{array}$	4600		ns
		$\label{eq:VDD} \begin{split} & 2.4 \; V \leq V_{DD} < 3.3 \; V, \\ & 1.6 \; V \leq V_{b} \leq 2.0 \; V^{\; \text{Note 2}}, \\ & C_{b} = 100 \; pF, \; R_{b} = 5.5 \; k\Omega \end{split}$	4650		ns
Hold time when SCLr = "H"	tнıgн		620		ns
		$\begin{array}{l} 2.7 \; V \leq V_{DD} < 4.0 \; V, \\ 2.3 \; V \leq V_b < 2.7 \; V, \\ C_b = 50 \; pF, \; R_b = 2.7 \; k\Omega \end{array}$	500		ns
			2700		ns
		$\begin{array}{l} 2.7 \; V \leq V_{DD} < 4.0 \; V, \\ 2.3 \; V \leq V_b < 2.7 \; V, \\ C_b = 100 \; p\text{F}, \; R_b = 2.7 \; k\Omega \end{array}$	2400		ns
		$ \begin{array}{l} 2.4 \; V \leq V_{DD} < 3.3 \; V, \\ 1.6 \; V \leq V_b \leq 2.0 \; V^{\text{Note 2}}, \\ C_b = 100 \; pF, \; R_b = 5.5 \; k\Omega \end{array} $	1830		ns

(Notes, Caution and Remarks are listed on the next page.)



Parameter	Symbol	Conditions	MIN.	MAX.	Unit
Data setup time (reception)	tsu:dat		1/f _{MCK} + 340 Note 3		ns
		$\begin{array}{l} 2.7 \; V \leq V_{DD} < 4.0 \; V, \\ 2.3 \; V \leq V_b < 2.7 \; V, \\ C_b = 50 \; pF, \; R_b = 2.7 \; k\Omega \end{array}$	1/fмск + 340 ^{Note 3}		ns
			1/fмск + 760 Note 3		ns
		$\label{eq:VDD} \begin{array}{l} 2.7 \; V \leq V_{DD} < 4.0 \; V, \\ 2.3 \; V \leq V_b < 2.7 \; V, \\ C_b = 100 \; pF, \; R_b = 2.7 \; k\Omega \end{array}$	1/fмск + 760 Note 3		ns
			1/fмск + 570 Note 3		ns
Data hold time (transmission)	thd:dat		0	770	ns
		$\begin{array}{l} 2.7 \; V \leq V_{DD} < 4.0 \; V, \\ 2.3 \; V \leq V_b < 2.7 \; V, \\ C_b = 50 \; pF, \; R_b = 2.7 \; k\Omega \end{array}$	0	770	ns
			0	1420	ns
		$\begin{array}{l} 2.7 \; V \leq V_{DD} < 4.0 \; V, \\ 2.3 \; V \leq V_b < 2.7 \; V, \\ C_b = 100 \; pF, \; R_b = 2.7 \; k\Omega \end{array}$	0	1420	ns
		$\begin{array}{l} 2.4 \ V \leq V_{DD} < 3.3 \ V, \\ 1.6 \ V \leq V_b \leq 2.0 \ V^{\text{Note 2}}, \\ C_b = 100 \ pF, \ R_b = 5.5 \ k\Omega \end{array}$	0	1215	ns

(8) Communication at different potential (1.8 V, 2.5 V, 3 V) (simplified I^2C mode) (2/2) (T₁ = 40 to $\pm 105^{\circ}C$, 2.4 V $\leq V_{22} \leq 5.5$ V, $V_{22} = 0.0$ V)

Notes 1. The value must also be equal to or less than $f_{MCK}/4$.

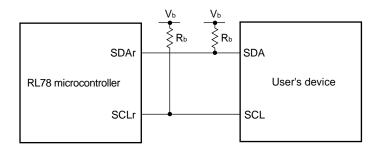
2. Use it with $V_{DD} \ge V_b$.

- 3. Set the fMCK value to keep the hold time of SCLr = "L" and SCLr = "H".
- Caution Select the TTL input buffer and the N-ch open drain output (V_{DD} tolerance) mode for the SDAr pin and the N-ch open drain output (V_{DD} tolerance) mode for the SCLr pin by using port input mode register g (PIMg) and port output mode register g (POMg). For V_{IH} and V_{IL}, see the DC characteristics with TTL input buffer selected.

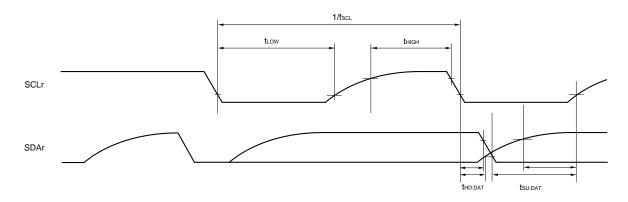
(**Remarks** are listed on the next page.)



Simplified I²C mode connection diagram (during communication at different potential)



Simplified I²C mode serial transfer timing (during communication at different potential)



- **Remarks 1.** R_b[Ω]:Communication line (SDAr, SCLr) pull-up resistance, C_b[F]: Communication line (SDAr, SCLr) load capacitance, V_b[V]: Communication line voltage
 - **2.** r: IIC number (r = 00), g: PIM, POM number (g = 0, 3, 5, 7)
 - 3. fMCK: Serial array unit operation clock frequency

(Operation clock to be set by the CKSmn bit of serial mode register mn (SMRmn). m: Unit number, n: Channel number (mn = 00)



3.5.2 Serial interface IICA

Parameter	Symbol	Conditions	HS (h	Unit			
				ndard ode	Fast	Mode	
			MIN.	MAX.	MIN.	MAX.	
SCLA0 clock frequency	fsc∟	Fast mode: fcLK ≥ 3.5 MHz	-	_	0	400	kHz
		Standard mode: $f_{CLK} \ge 1 \text{ MHz}$	0	100	-	-	kHz
Setup time of restart condition	tsu:sta		4.7		0.6		μs
Hold time ^{Note 1}	thd:sta		4.0		0.6		μs
Hold time when SCLA0 = "L"	tLOW		4.7		1.3		μs
Hold time when SCLA0 = "H"	tніgн		4.0		0.6		μs
Data setup time (reception)	tsu:dat		250		100		ns
Data hold time (transmission)Note 2	thd:dat		0	3.45	0	0.9	μs
Setup time of stop condition	tsu:sto		4.0		0.6		μs
Bus-free time	t BUF		4.7		1.3		μs

$(T_A = -40 \text{ to } +105^{\circ}\text{C}, 2.4 \text{ V} \le \text{V}_{DD} \le 5.5 \text{ V}, \text{V}_{SS} = 0 \text{ V})$

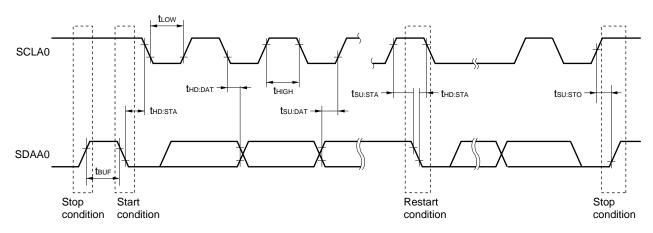
Notes 1. The first clock pulse is generated after this period when the start/restart condition is detected.

2. The maximum value (MAX.) of the during normal transfer and a wait state is inserted in the ACK (acknowledge) timing.

- Caution The values in the above table are applied even when bit 1 (PIOR1) in the peripheral I/O redirection register (PIOR) is 1. At this time, the pin characteristics (IOH1, IOL1, VOH1, VOL1) must satisfy the values in the redirect destination.
- **Remark** The maximum value of Cb (communication line capacitance) and the value of Rb (communication line pull-up resistor) at that time in each mode are as follows.

 $\begin{array}{ll} \mbox{Standard mode:} & C_b = 400 \mbox{ pF}, \mbox{ } R_b = 2.7 \mbox{ } k\Omega \\ \mbox{Fast mode:} & C_b = 320 \mbox{ pF}, \mbox{ } R_b = 1.1 \mbox{ } k\Omega \\ \end{array}$

IICA serial transfer timing





3.5.3 USB

(1) Electrical specifications

(TA = -40 to +105°C, 3.0 V \leq UV_{DD} \leq 3.6 V, 3.0 V \leq V_{DD} \leq 5.5 V, V_{SS} = 0 V)

	Parameter	Symbol	Conditions	MIN.	TYP.	MAX.	Unit
UVdd	UV _{DD} input voltage characteristic	UVdd	$ V_{\text{DD}} = 3.0 \text{ to } 5.5 \text{ V}, \text{PXXCON} = 1, \\ VDDUSEB = 0 (UV_{\text{DD}} \leq V_{\text{DD}}) $	3.0	3.3	3.6	V
	UV _{DD} output voltage characteristic	UVdd	V _{DD} = 4.0 to 5.5 V, PXXCON = VDDUSEB = 1	3.0	3.3	3.6	V
UVBUS	UV _{BUS} input voltage characteristic	UVBUS	Function	4.35 (4.02 ^{Note})	5.00	5.25	V
			Host	4.75	5.00	5.25	V

Note Value of instantaneous voltage

$(T_A = -40 \text{ to } +105^{\circ}C, 3.0 \text{ V} \le UV_{DD} \le 3.6 \text{ V}, 3.0 \text{ V} \le V_{DD} \le 5.5 \text{ V}, \text{ Vss} = 0 \text{ V})$

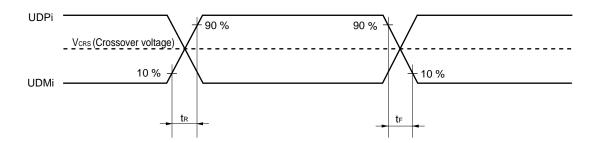
Par	Parameter		Symbol	Conditions	MIN.	TYP.	MAX.	Unit
UDPi/UDMi	Input voltage		Viн		2.0			V
pins input characteristic (FS/LS receiver)			VIL				0.8	V
	Differenc sensitivit		Vdi	UDP voltage – UDM voltage	0.2			V
	Differenc common range	-	Vсм		0.8		2.5	V
UDPi/UDMi	Output v	oltage	Vон	Іон = -200 μА	2.8		3.6	V
pins output characteristic			Vol	IoL = 2.4 mA	0		0.3	V
(FS driver)	Transi-ti	Rising	trr	Rising: From 10% to 90 % of	4		20	ns
. ,	on time	Falling	tff	amplitude, Falling: From 90% to 10 % of	4		20	ns
	Matching (TFR/TF		Vfrfm	amplitude, CL = 50 pF	90		111.1	%
	Crossover voltage		VFCRS		1.3		2.0	V
	Output Impedance		Zdrv	UV _{DD} voltage = 3.3 V, Pin voltage = 1.65 V	28		44	Ω
UDPi/UDMi	Output voltage		Vон		2.8		3.6	V
pins output characteristic			Vol		0		0.3	V
(LS driver)	Transi-ti on time	Rising	tlr	Rising: From 10% to 90 % of amplitude, Falling: From 90% to 10 % of	75		300	ns
. ,		Falling	tlf		75		300	ns
	Matching (TFR/TFF) Note Crossover voltage		VLTFM	amplitude, CL = 200 to 600 pF	80		125	%
			VLCRS	When the host controller function is selected: The UDMi pin (i = 0, 1) is pulled up via 1.5 k Ω . When the function controller function is selected: The UDP0 and UDM0 pins are individually pulled down via 15 k Ω	1.3		2.0	V
UDPi/UDMi	Pull-dow	n resistor	Rpd		14.25		24.80	kΩ
pins pull-up, pull-down	Pull-up resistor	Idle	Rpui		0.9		1.575	kΩ
	(i = 0 only)	Recep-t ion	Rpua		1.425		3.09	kΩ
UVBUS	UV _{BUS} puresistor	ill-down	Rvbus	UV _{BUS} voltage = 5.5 V		1000		kΩ
	UV _{BUS} in	put	Viн		3.20			V
	voltage		VIL				0.8	V

Note Excludes the first signal transition from the idle state.

Remark i = 0, 1



Timing of UDPi and UDMi



(2) BC standard

$(T_{\text{A}} = -40 \text{ to } +105^{\circ}\text{C}, 3.0 \text{ V} \le \text{UV}_{\text{DD}} \le 3.6 \text{ V}, 3.0 \text{ V} \le \text{V}_{\text{DD}} \le 5.5 \text{ V}, \text{V}_{\text{SS}} = 0 \text{ V})$

	Parameter	Symbol	Conditions	MIN.	TYP.	MAX.	Unit
USB	UDPi sink current	DP_SINK		25		175	μA
standard BC1.2	UDMi sink current	Idm_sink		25		175	μA
501.2	DCD source current	IDP_SRC		7		13	μA
	Dedicated charging port resistor	Rdcp_dat	0 V < UDP/UDM voltage < 1.0 V			200	Ω
	Data detection voltage	VDAT_REF		0.25		0.4	V
	UDPi source voltage	Vdp_src	Output current 250 µA	0.5		0.7	V
	UDMi source voltage	Vdm_src	Output current 250 µA	0.5		0.7	V

Remark i = 0, 1



Pai	rameter		Symbol	Conditions	MIN.	TYP.	MAX.	Unit
UDPi output	VDSELi	1000	V _{P20}		38	40	42	% UV _{BUS}
voltage	[3:0]	1001	Vp27		51.6	53.6	55.6	% UV _{BUS}
(UV _{BUS} divider ratio)	(i = 0, 1)	1010	V _{P20}		38	40	42	% UV _{BUS}
• VDOUEi = 1		1100	V _{P33}		60	66	72	% UVвus
UDMi output	VDSELi	1000	VM20		38	40	42	% UV _{BUS}
voltage	[3:0]	1001	VM20		38	40	42	% UV _{BUS}
(UV _{BUS} divider ratio)	(i = 0, 1)	1010	Vm27		51.6	53.6	55.6	% UV _{BUS}
• VDOUEi = 1		1100	Vмзз		60	66	72	% UV _{BUS}
UDPi	VDSELi	1000	VHDETP_UP0	The rise of pin voltage detection voltage	56.2			% UVвus
comparing Note 1 voltage	[3:0]		VHDETP_DWN0	The fall of pin voltage detection voltage			29.4	% UV _{BUS}
UVBUS divider	(i = 0, 1)	1001	VHDETP_UP1	The rise of pin voltage detection voltage	60.5			% UV _{BUS}
ratio)			VHDETP_DWN1	The fall of pin voltage detection voltage			45.0	% UV _{BUS}
• VDOUEi = 1		1010	VHDETP_UP2	The rise of pin voltage detection voltage	56.2			% UV _{BUS}
• CUSDETEi = 1			VHDETP_DWN2	The fall of pin voltage detection voltage			29.4	% UV _{BUS}
UDMi	VDSELi	1000	VHDETM_UP0	The rise of pin voltage detection voltage	56.2			% UV _{BUS}
comparing voltage Note 1	[3:0]		VHDETM_DWN0	The fall of pin voltage detection voltage			29.4	% UV _{BUS}
UVBUS divider	(i = 0, 1)	1001	VHDETM_UP1	The rise of pin voltage detection voltage	56.2			% UV _{BUS}
ratio)			VHDETM_DWN1	The fall of pin voltage detection voltage			29.4	% UV _{BUS}
• VDOUEi = 1		1010	VHDETM_UP2	The rise of pin voltage detection voltage	60.5			% UV _{BUS}
• CUSDETEi = 1			VHDETM_DWN2	The fall of pin voltage detection voltage			45.0	% UV _{BUS}
UDPi pull-up d	etection	1000	RHDET_PULL	In full-speed mode, the power supply			1.575	kΩ
		1001		voltage range of pull-up resistors				
Connect detec the full speed f (pull-up resisto	unction	1010		connected to the USB function module is between 3.0 V and 3.6 V.				
		1000	RHDET_PULL	In low-speed mode, the power supply			1.575	kΩ
Note 2	UDMi pull-up detection Note 2		INHDET_PULL	voltage range of pull-up resistors			1.575	K32
Connect detection with		1001 1010	ł	connected to the USB function				
the low-speed resistor)	(pull-up	1010		module is between 3.0 V and 3.6 V.				
/	ent	1000	HDET SINK		25			μA
detection Note 2	2	1000			_0			ي مير
Connect detec	tion with	1010	ł					
the BC1.2 port device (sink re								
device (SITIK Te	313101)							

(3) BC option standard (Host)

Notes 1. If the voltage output from UDPi or UDMi (i = 0, 1) exceeds the range of the MAX and MIN values prescribed in this specification, DPCUSDETi (bit 8) and DMCUSDETi (bit 9) of the USBBCOPTi register are set to 1.

If the pull-up resistance or sink current prescribed in this specification is applied to UDPi or UDMi (i = 0, 1), DPCUSDETi (bit 8) and DMCUSDETi (bit 9) of the USBBCOPTi register are set to 1.

Remark i = 0, 1



(4) BC option standard (Function)

Par	Parameter		Symbol	Conditions	MIN.	TYP.	MAX.	Unit
UDPi/UDMi	VDSELi	0000	VDDET0		27	32	37	% UV _{BUS}
input	[3:0]	0001	VDDET1		29	34	39	% UV _{BUS}
reference voltage	(i = 0)	0010	VDDET2		32	37	42	% UV _{BUS}
(UVBUS divider		0011	Vddet3		35	40	45	% UV _{BUS}
ratio)		0100	VDDET4		38	43	48	% UV _{BUS}
• VDOUEi = 0		0101	Vddet5		41	46	51	% UV _{BUS}
(i = 0))		0110	Vddet6		44	49	54	% UV _{BUS}
		0111	VDDET7		47	52	57	% UV _{BUS}
		1000	Vddet8		51	56	61	% UV _{BUS}
		1001	Vddet9		55	60	65	% UV _{BUS}
		1010	VDDET10		59	64	69	% UV _{BUS}
		1011	VDDET11		63	68	73	% UV _{BUS}
		1100	VDDET12		67	72	77	% UV _{BUS}
		1101	VDDET13		71	76	81	% UV _{BUS}
		1110	VDDET14		75	80	85	% UV _{BUS}
		1111	Vddet15		79	84	89	% UV _{BUS}



3.6 Analog Characteristics

3.6.1 A/D converter characteristics

Classification of A/D converter characteristics

Input channel		Reference Voltage					
	Reference voltage (+) = AVREFP Reference voltage (-) = AVREFM	Reference voltage (+) = Vbb Reference voltage (-) = Vss	Reference voltage (+) = VBGR Reference voltage (-) = AVREFM				
ANI0 to ANI7	Refer to 3.6.1 (1).	Refer to 3.6.1 (3).	Refer to 3.6.1 (4).				
ANI16, ANI17, ANI19	Refer to 3.6.1 (2).						
Internal reference voltage Temperature sensor output voltage	Refer to 3.6.1 (1) .		_				

(1) When AVREF (+) = AVREFP/ANIO (ADREFP1 = 0, ADREFP0 = 1), reference voltage (-) = AVREFM/ANI1 (ADREFM = 1), target pin: ANI2 to ANI7, internal reference voltage, and temperature sensor output voltage

(T_A = -40 to +105°C, 2.4 V \leq AV_{REFP} \leq V_{DD} \leq 5.5 V, V_{SS} = 0 V, Reference voltage (+) = AV_{REFP}, Reference voltage (-) = AV_{REFM} = 0 V)

Parameter	Symbol	Con	ditions	MIN.	TYP.	MAX.	Unit
Resolution	Res			8		10	bit
Overall error ^{Note 1}	AINL	10-bit resolution AV _{REFP} = V _{DD} ^{Note 3}	$2.4~V \le AV_{\text{REFP}} \le 5.5~V$		1.2	±3.5	LSB
Conversion time	t CONV	10-bit resolution	$3.6~\text{V} \leq \text{V}\text{DD} \leq 5.5~\text{V}$	2.125		39	μs
		Target pin: ANI2 to ANI7	$2.7~V \leq V \text{DD} \leq 5.5~V$	3.1875		39	μs
		ANIZ	$2.4~V \leq V \text{DD} \leq 5.5~V$	17		39	μs
		10-bit resolution	$3.6~V \leq V\text{DD} \leq 5.5~V$	2.375		39	μs
		Target pin: Internal	$2.7~V \leq V \text{DD} \leq 5.5~V$	3.5625		39	μs
		reference voltage, and temperature sensor output voltage (HS (high-speed main) mode)	$2.4~V \le V_{DD} \le 5.5~V$	17		39	μs
Zero-scale error ^{Notes 1, 2}	EZS	10-bit resolution AV _{REFP} = V _{DD} ^{Note 3}	$2.4 \text{ V} \leq \text{AV}_{\text{REFP}} \leq 5.5 \text{ V}$			±0.25	%FSR
Full-scale error ^{Notes 1, 2}	EFS	10-bit resolution AV _{REFP} = V _{DD} ^{Note 3}	$2.4 \text{ V} \leq \text{AV}_{\text{REFP}} \leq 5.5 \text{ V}$			±0.25	%FSR
Integral linearity error ^{Note 1}	ILE	10-bit resolution AV _{REFP} = V _{DD} ^{Note 3}	$2.4 \text{ V} \le \text{AV}_{\text{REFP}} \le 5.5 \text{ V}$			±2.5	LSB
Differential linearity error Note 1	DLE	10-bit resolution AV _{REFP} = V _{DD} ^{Note 3}	$2.4 \text{ V} \le \text{AV}_{\text{REFP}} \le 5.5 \text{ V}$			±1.5	LSB
Analog input voltage	VAIN	ANI2 to ANI7	·	0		AVREFP	V
		Internal reference voltage (2.4 V \leq VDD \leq 5.5 V, HS (high-speed main) mode) Temperature sensor output voltage (2.4 V \leq VDD \leq 5.5 V, HS (high-speed main) mode)		V _{BGR} Note 4			V
				V	/ _{TMPS25} Note	2 4	V

(Notes are listed on the next page.)



- **Notes 1.** Excludes quantization error ($\pm 1/2$ LSB).
 - **2.** This value is indicated as a ratio (%FSR) to the full-scale value.
 - **3.** When AV_{REFP} < V_{DD}, the MAX. values are as follows. Overall error: Add ± 1.0 LSB to the MAX. value when AV_{REFP} = V_{DD}. Zero-scale error/Full-scale error: Add $\pm 0.05\%$ FSR to the MAX. value when AV_{REFP} = V_{DD}. Integral linearity error/ Differential linearity error: Add ± 0.5 LSB to the MAX. value when AV_{REFP} = V_{DD}.
 - 4. Refer to 3.6.2 Temperature sensor/internal reference voltage characteristics.



(2) When reference voltage (+) = AVREFP/ANIO (ADREFP1 = 0, ADREFP0 = 1), reference voltage (-) = AVREFM/ANI1 (ADREFM = 1), target pin: ANI16, ANI17, ANI19

(TA = -40 to +105°C, 2.4 V \leq AV _{REFP} \leq V _{DD} \leq 5.5 V, V _{SS} = 0 V, Reference voltage (+) = AV _{REFP} , AV _{REFP} , AV _{REFP} , AV _{REFP} , AV
voltage (–) = AV _{REFM} = 0 V)

Parameter	Symbol	Con	ditions	MIN.	TYP.	MAX.	Unit
Resolution	Res			8		10	bit
Overall error ^{Note 1}	AINL	10-bit resolution AV _{REFP} = V_{DD} ^{Note 3}	$2.4~V \le AV_{REFP} \le 5.5~V$		1.2	±5.0	LSB
Conversion time	t CONV	10-bit resolution	$3.6 \text{ V} \leq \text{Vdd} \leq 5.5 \text{ V}$	2.125		39	μs
			$2.7~\text{V} \leq \text{Vdd} \leq 5.5~\text{V}$	3.1875		39	μs
		ANI16, ANI17, ANI19	$2.4~\text{V} \leq \text{V}\text{DD} \leq 5.5~\text{V}$	17		39	μs
Zero-scale error ^{Notes 1, 2}	EZS	10-bit resolution AV _{REFP} = V _{DD} ^{Note 3}	$2.4~V \leq AV_{\text{REFP}} \leq 5.5~V$			±0.35	%FSR
Full-scale error ^{Notes 1, 2}	EFS	10-bit resolution AV _{REFP} = V _{DD} ^{Note 3}	$2.4~V \leq AV_{\text{REFP}} \leq 5.5~V$			±0.35	%FSR
Integral linearity error ^{Note 1}	ILE	10-bit resolution AV _{REFP} = V _{DD} ^{Note 3}	$2.4~V \le AV_{REFP} \le 5.5~V$			±3.5	LSB
Differential linearity error Note 1	DLE	10-bit resolution AV _{REFP} = V _{DD} ^{Note 3}	$2.4~V \le AV_{REFP} \le 5.5~V$			±2.0	LSB
Analog input voltage	Vain	ANI16, ANI17, ANI19		0		AVREFP and VDD	V

Notes 1. Excludes quantization error ($\pm 1/2$ LSB).

- 2. This value is indicated as a ratio (%FSR) to the full-scale value.
- 3. When $AV_{REFP} < V_{DD}$, the MAX. values are as follows.

Overall error: Add ± 4.0 LSB to the MAX. value when AV_{REFP} = V_{DD}.

Zero-scale error/Full-scale error: Add $\pm 0.20\%$ FSR to the MAX. value when AV_{REFP} = V_{DD}.

Integral linearity error/ Differential linearity error: Add ± 2.0 LSB to the MAX. value when AV_{REFP} = V_{DD}.



(3) Reference voltage (+) = V_{DD} (ADREFP1 = 0, ADREFP0 = 0), Reference voltage (-) = Vss (ADREFM = 0), target ANI pin: ANI0 to ANI7, ANI16, ANI17, ANI19, internal reference voltage, and temperature sensor output voltage

Parameter	Symbol	Conditio	ons	MIN.	TYP.	MAX.	Unit
Resolution	Res			8		10	bit
Overall error ^{Notes 1, 2}	AINL	10-bit resolution	$2.4~V \le V \text{DD} \le 5.5~V$		1.2	±7.0	LSB
Conversion time	t CONV	10-bit resolution	$3.6~V \leq V \text{dd} \leq 5.5~V$	2.125		39	μs
		Target ANI pin:	$2.7~V \leq V \text{DD} \leq 5.5~V$	3.1875		39	μs
		ANI0 to ANI7, ANI16, ANI17, ANI19	$2.4~\text{V} \leq \text{Vdd} \leq 5.5~\text{V}$	17		39	μs
		10-bit resolution	$3.6~\text{V} \leq \text{Vdd} \leq 5.5~\text{V}$	2.375		39	μs
		Target ANI pin: Internal	$2.7~V \leq V \text{DD} \leq 5.5~V$	3.5625		39	μs
		reference voltage, and temperature sensor output voltage (HS (high-speed main) mode)	$2.4 \text{ V} \leq \text{Vdd} \leq 5.5 \text{ V}$	17		39	μs
Zero-scale error ^{Notes 1, 2}	EZS	10-bit resolution	$2.4~\text{V} \leq \text{Vdd} \leq 5.5~\text{V}$			±0.60	%FSR
Full-scale error ^{Notes 1, 2}	EFS	10-bit resolution	$2.4~\text{V} \leq \text{Vdd} \leq 5.5~\text{V}$			±0.60	%FSR
Integral linearity error ^{Note 1}	ILE	10-bit resolution	$2.4~\text{V} \leq \text{Vdd} \leq 5.5~\text{V}$			±4.0	LSB
Differential linearity error Note 1	DLE	10-bit resolution	$2.4~V \le V \text{DD} \le 5.5~V$			±2.0	LSB
Analog input voltage	VAIN	ANI0 to ANI7, ANI16, ANI	17, ANI19	0		Vdd	V
		Internal reference voltage V_{B4} (2.4 V \leq VDD \leq 5.5 V, HS (high-speed main)mode)		VBGR Note 3		V	
		Temperature sensor output (2.4 V \leq V _{DD} \leq 5.5 V, HS (I mode)	0	VTMPS25 Note 3		3	V

Notes 1. Excludes quantization error ($\pm 1/2$ LSB).

2. This value is indicated as a ratio (%FSR) to the full-scale value.

3. Refer to 3.6.2 Temperature sensor/internal reference voltage characteristics.



(4) When Reference voltage (+) = Internal reference voltage (ADREFP1 = 1, ADREFP0 = 0), Reference voltage (-) = AV_{REFM}/ANI1 (ADREFM = 1), target pin: ANI0 to ANI7, ANI16, ANI17, ANI19

 $(T_A = -40 \text{ to } +105^{\circ}\text{C}, 2.4 \text{ V} \le \text{V}_{DD} \le 5.5 \text{ V}, \text{V}_{SS} = 0 \text{ V}, \text{Reference voltage (+)} = \text{V}_{BGR}^{Note 3}, \text{Reference voltage (-)} = \text{AV}_{REFM}^{Note 4} = 0 \text{ V}, \text{HS (high-speed main) mode)}$

Parameter	Symbol	Conditions		MIN.	TYP.	MAX.	Unit
Resolution	Res				8		Bit
Conversion time	t CONV	8-bit resolution	$2.4~V \le V_{DD} \le 5.5~V$	17		39	μs
Zero-scale error ^{Notes 1, 2}	EZS	8-bit resolution	$2.4~V \le V \text{DD} \le 5.5~V$			±0.60	%FSR
Integral linearity error ^{Note 1}	ILE	8-bit resolution	$2.4~V \le V \text{DD} \le 5.5~V$			±2.0	LSB
Differential linearity error Note 1	DLE	8-bit resolution	$2.4~V \le V \text{DD} \le 5.5~V$			±1.0	LSB
Analog input voltage	VAIN			0		VBGR Note 3	V

Notes 1. Excludes quantization error (±1/2 LSB).

2. This value is indicated as a ratio (%FSR) to the full-scale value.

3. Refer to 3.6.2 Temperature sensor/internal reference voltage characteristics.

4. When reference voltage (-) = Vss, the MAX. values are as follows.

Zero-scale error: Add $\pm 0.35\%$ FSR to the MAX. value when reference voltage (–) = AV_{REFM}.

Integral linearity error: Add ± 0.5 LSB to the MAX. value when reference voltage (–) = AV_{REFM}.

Differential linearity error: Add ± 0.2 LSB to the MAX. value when reference voltage (–) = AV_{REFM}.



3.6.2 Temperature sensor/internal reference voltage characteristics

Parameter	Symbol	Conditions	MIN.	TYP.	MAX.	Unit
Temperature sensor output voltage	VTMPS25	Setting ADS register = 80H, TA = +25 $^{\circ}$ C		1.05		V
Internal reference voltage	Vbgr	Setting ADS register = 81H	1.38	1.45	1.5	V
Temperature coefficient	Fvtmps	Temperature sensor that depends on the temperature		-3.6		mV/°C
Operation stabilization wait time	tamp		5			μs

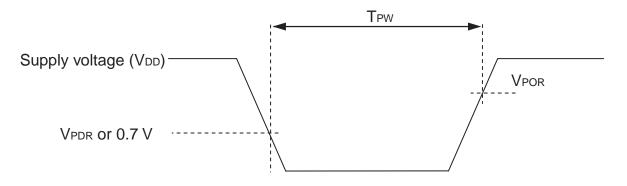
(TA = -40 to +105°C, 2.4 V \leq VDD \leq 5.5 V, Vss = 0 V, HS (high-speed main) mode)

3.6.3 POR circuit characteristics

$(T_A = -40 \text{ to } +105^{\circ}\text{C}, \text{ Vss} = 0 \text{ V})$

Parameter	Symbol	Conditions	MIN.	TYP.	MAX.	Unit
Detection voltage	VPOR	Power supply rise time	1.45	1.51	1.57	V
	VPDR	Power supply fall time	1.44	1.50	1.56	V
Minimum pulse width ^{Note}	TPW		300			μs

Note Minimum time required for a POR reset when V_{DD} exceeds below V_{PDR}. This is also the minimum time required for a POR reset from when V_{DD} exceeds below 0.7 V to when V_{DD} exceeds V_{POR} while STOP mode is entered or the main system clock (f_{MAIN}) is stopped through setting bit 0 (HIOSTOP) and bit 7 (MSTOP) in the clock operation status control register (CSC).





3.6.4 LVD circuit characteristics

LVD Detection Voltage of Reset Mode and Interrupt Mode

(TA = -40 to +105°C, VPDR \leq VDD \leq 5.5 V, Vss = 0 V)

	Parameter	Symbol	Conditions	MIN.	TYP.	MAX.	Unit
Detection	Supply voltage level	VLVD0	Power supply rise time	3.90	4.06	4.22	V
voltage			Power supply fall time	3.83	3.98	4.13	V
		VLVD1	Power supply rise time	3.60	3.75	3.90	V
			Power supply fall time	3.53	3.67	3.81	V
		VLVD2	Power supply rise time	3.01	3.13	3.25	V
			Power supply fall time	2.94	3.06	3.18	V
		VLVD3	Power supply rise time	2.90	3.02	3.14	V
			Power supply fall time	2.85	2.96	3.07	V
		VLVD4	Power supply rise time	2.81	2.92	3.03	V
			Power supply fall time	2.75	2.86	2.97	V
		VLVD5	Power supply rise time	2.70	2.81	2.92	V
			Power supply fall time	2.64	2.75	2.86	V
		VLVD6	Power supply rise time	2.61	2.71	2.81	V
			Power supply fall time	2.55	2.65	2.75	V
		VLVD7	Power supply rise time	2.51	2.61	2.71	V
			Power supply fall time	2.45	2.55	2.65	V
Minimum pu	ulse width	tLW		300			μs
Detection d	elay time	tld				300	μs



LVD Detection Voltage of Interrupt & Reset Mode $(T_A = -40 \text{ to } +105^{\circ}\text{C}, V_{PDR} \le V_{DD} \le 5.5 \text{ V}, V_{SS} = 0 \text{ V})$

Parameter	Symbol		Cond	litions	MIN.	TYP.	MAX.	Unit
Interrupt and reset	VLVDD0	VPOC	2, VPOC1, VPOC0 =	0, 1, 1, falling reset voltage	2.64	2.75	2.86	V
mode	VLVDD1		LVIS1, LVIS0 = 1, 0	Rising release reset voltage	2.81	2.92	3.03	V
				Falling interrupt voltage	2.75	2.86	2.97	V
	VLVDD2		LVIS1, LVIS0 = 0, 1	Rising release reset voltage	2.90	3.02	3.14	V
				Falling interrupt voltage	2.85	2.96	3.07	V
	VLVDD3		LVIS1, LVIS0 = 0, 0	Rising release reset voltage	3.90	4.06	4.22	V
				Falling interrupt voltage	3.83	3.98	4.13	V

3.6.5 Power supply voltage rising slope characteristics

$(T_A = -40 \text{ to } +105^{\circ}\text{C}, \text{ Vss} = 0 \text{ V})$

Parameter	Symbol	Conditions	MIN.	TYP.	MAX.	Unit
Power supply voltage rising slope	SVDD				54	V/ms

Caution Make sure to keep the internal reset state by the LVD circuit or an external reset until V_{DD} reaches the operating voltage range shown in 3.4 AC Characteristics.

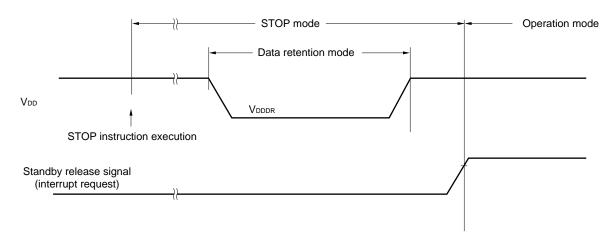


3.7 Data Memory STOP Mode Low Supply Voltage Data Retention Characteristics

(T_A = -40 to +105°C, Vss = 0 V)

Parameter	Symbol	Conditions	MIN.	TYP.	MAX.	Unit
Data retention supply voltage	VDDDR		1.44 ^{Note}		5.5	V

Note The value depends on the POR detection voltage. When the voltage drops, the data is retained before a POR reset is effected, but data is not retained when a POR reset is effected.



3.8 Flash Memory Programming Characteristics

|--|

Parameter	Symbol	Conditions		MIN.	TYP.	MAX.	Unit
CPU/peripheral hardware clock frequency	fclк	$2.4 \text{ V} \leq \text{Vdd} \leq 5.5 \text{ V}$		1		24	MHz
Number of code flash rewrites	Cerwr	Retaining years: 20 years	T _A = +85°C	1,000			Times
Number of data flash rewrites Notes 1, 2, 3		Retaining years: 1 year	T _A = +25°C		1,000,000		
		Retaining years: 5 years	T _A = +85°C	100,000			
		Retaining years: 20 years	T _A = +85°C	10,000			

Notes 1. 1 erase + 1 write after the erase is regarded as 1 rewrite. The retaining years are until next rewrite after the rewrite.

- 2. When using flash memory programmer and Renesas Electronics self programming library.
- **3.** These specifications show the characteristics of the flash memory and the results obtained from Renesas Electronics reliability testing.

3.9 Dedicated Flash Memory Programmer Communication (UART)

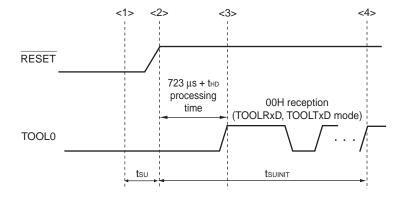
$(T_A = -40 \text{ to } +105^{\circ}\text{C}, 2.4 \text{ V} \le \text{V}_{\text{DD}} \le 5.5 \text{ V}, \text{V}_{\text{SS}} = 0 \text{ V})$

Parameter	Symbol	Conditions	MIN.	TYP.	MAX.	Unit
Transfer rate		During serial programming	115,200		1,000,000	bps



3.10 Timing Specs for Switching Flash Memory Programming Modes

Parameter	Symbol	Conditions	MIN.	TYP.	MAX.	Unit
How long from when an external reset ends until the initial communication settings are specified	tsuinit	POR and LVD reset must end before the external reset ends.			100	ms
How long from when the TOOL0 pin is placed at the low level until an external reset ends	tsu	POR and LVD reset must end before the external reset ends.	10			μs
How long the TOOL0 pin must be kept at the low level after an external reset ends (excluding the processing time of the firmware to control the flash memory)	tно	POR and LVD reset must end before the external reset ends.	1			ms



- <1> The low level is input to the TOOL0 pin.
- <2> The external reset ends (POR and LVD reset must end before the external reset ends.).
- <3> The TOOL0 pin is set to the high level.
- <4> Setting of the flash memory programming mode by UART reception and complete the baud rate setting.
- **Remark** tsuinit: The segment shows that it is necessary to finish specifying the initial communication settings within 100 ms from when the resets end.
 - $t_{su:}$ How long from when the TOOL0 pin is placed at the low level until an external reset ends
 - thd: How long to keep the TOOL0 pin at the low level from when the external and internal resets end (excluding the processing time of the firmware to control the flash memory)

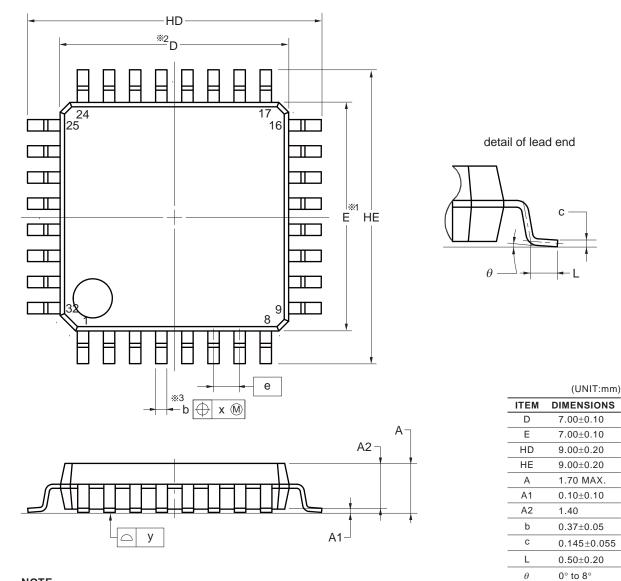


4. PACKAGE DRAWINGS

4.1 32-pin Products

R5F10JBCAFP, R5F10KBCAFP R5F10JBCGFP, R5F10KBCGFP

JEITA Package Code	RENESAS Code	Previous Code	MASS (TYP.) [g]
P-LQFP32-7x7-0.80	PLQP0032GB-A	P32GA-80-GBT-1	0.2



NOTE

1.Dimensions "%1" and "%2" do not include mold flash.

2.Dimension "%3" does not include trim offset.

R01DS0348EJ0110 Rev.1.10 Nov 15, 2013



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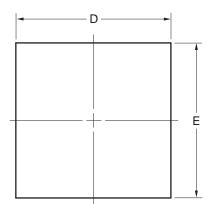
x y 0.80

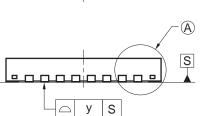
0.20

0.10

R5F10JBCANA, R5F10KBCANA R5F10JBCGNA, R5F10KBCGNA

JEITA Package Code	RENESAS Code	Previous Code	MASS (TYP.) [g]
P-HWQFN32-5x5-0.50	PWQN0032KB-A	P32K8-50-3B4-3	0.06





D2 –

32

25

- Lp

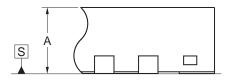
7

24

В

A





	(UNIT:mm)
ITEM	DIMENSIONS
D	5.00 ± 0.05
Е	5.00 ± 0.05
А	0.75 ± 0.05
b	$0.25^{+0.05}_{-0.07}$
е	0.50
Lp	0.40 ± 0.10
х	0.05
У	0.05

ITEM		D2			E2		
		MIN	NOM	MAX	MIN	NOM	MAX
EXPOSED DIE PAD VARIATIONS	А	3.45	3.50	3.55	3.45	3.50	3.55

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C

C

е

- b 🕀 x 🕅 S A B

E2

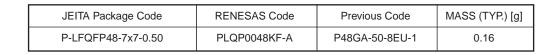
16

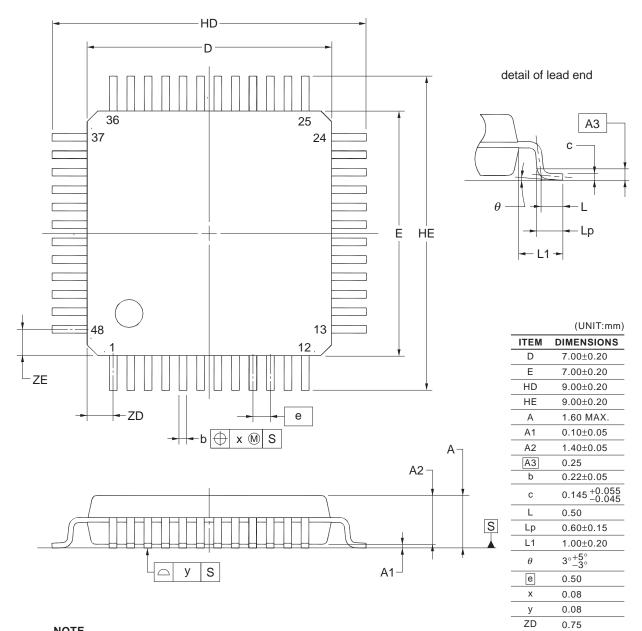
EXPOSED DIE PAD



4.2 48-pin products

R5F10JGCAFB, R5F10KGCAFB R5F10JGCGFB, R5F10KGCGFB





NOTE

Each lead centerline is located within 0.08 mm of its true position at maximum material condition.

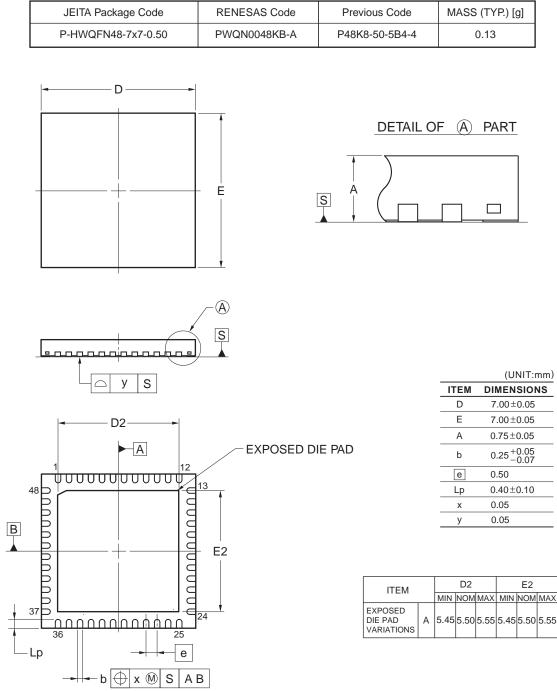
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ZE

0.75



R5F10JGCANA, R5F10KGCANA R5F10JGCGNA, R5F10KGCGNA



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E2

Revision History

RL78/G1C Data Sheet

		Description				
Rev.	Date	Page	Summary			
0.01	Sep 20, 2012	-	First Edition issued			
1.00	Aug 08, 2013	Throughout	Deletion of the bar over SCK and SCKxx			
			Renaming of fext to fexs			
			Renaming of interval timer (unit) to 12-bit interval timer			
			Addition of products for G: Industrial applications (T_A = -40 to +105 $^\circ\text{C}$)			
		1	Change of 1.1 Features			
		2	Change of 1.2 List of Part Numbers			
		3	Modification of Figure 1-1. Part Number, Memory Size, and Package of RL78/G1C			
		4, 5	Addition of remark to 1.3 Pin Configuration (Top View)			
		15, 16	Change of 1.6 Outline of Functions			
		17 to 76	Addition of a whole chapter			
		77 to 131	Addition of a whole chapter			
		132	Addition of products for G: Industrial applications (T_A = -40 to +105 $^\circ C$)			
1.10	Nov 15, 2013	77	Caution 3 added.			
		79	Note for operating ambient temperature in 3.1 Absolute Maximum Ratings deleted.			

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NOTES FOR CMOS DEVICES

- (1) VOLTAGE APPLICATION WAVEFORM AT INPUT PIN: Waveform distortion due to input noise or a reflected wave may cause malfunction. If the input of the CMOS device stays in the area between VIL (MAX) and VIH (MIN) due to noise, etc., the device may malfunction. Take care to prevent chattering noise from entering the device when the input level is fixed, and also in the transition period when the input level passes through the area between VIL (MAX) and VIH (MIN).
- (2) HANDLING OF UNUSED INPUT PINS: Unconnected CMOS device inputs can be cause of malfunction. If an input pin is unconnected, it is possible that an internal input level may be generated due to noise, etc., causing malfunction. CMOS devices behave differently than Bipolar or NMOS devices. Input levels of CMOS devices must be fixed high or low by using pull-up or pull-down circuitry. Each unused pin should be connected to VDD or GND via a resistor if there is a possibility that it will be an output pin. All handling related to unused pins must be judged separately for each device and according to related specifications governing the device.
- (3) PRECAUTION AGAINST ESD: A strong electric field, when exposed to a MOS device, can cause destruction of the gate oxide and ultimately degrade the device operation. Steps must be taken to stop generation of static electricity as much as possible, and quickly dissipate it when it has occurred. Environmental control must be adequate. When it is dry, a humidifier should be used. It is recommended to avoid using insulators that easily build up static electricity. Semiconductor devices must be stored and transported in an anti-static container, static shielding bag or conductive material. All test and measurement tools including work benches and floors should be grounded. The operator should be grounded using a wrist strap. Semiconductor devices must not be touched with bare hands. Similar precautions need to be taken for PW boards with mounted semiconductor devices.
- (4) STATUS BEFORE INITIALIZATION: Power-on does not necessarily define the initial status of a MOS device. Immediately after the power source is turned ON, devices with reset functions have not yet been initialized. Hence, power-on does not guarantee output pin levels, I/O settings or contents of registers. A device is not initialized until the reset signal is received. A reset operation must be executed immediately after power-on for devices with reset functions.
- (5) POWER ON/OFF SEQUENCE: In the case of a device that uses different power supplies for the internal operation and external interface, as a rule, switch on the external power supply after switching on the internal power supply. When switching the power supply off, as a rule, switch off the external power supply and then the internal power supply. Use of the reverse power on/off sequences may result in the application of an overvoltage to the internal elements of the device, causing malfunction and degradation of internal elements due to the passage of an abnormal current. The correct power on/off sequence must be judged separately for each device and according to related specifications governing the device.
- (6) INPUT OF SIGNAL DURING POWER OFF STATE : Do not input signals or an I/O pull-up power supply while the device is not powered. The current injection that results from input of such a signal or I/O pull-up power supply may cause malfunction and the abnormal current that passes in the device at this time may cause degradation of internal elements. Input of signals during the power off state must be judged separately for each device and according to related specifications governing the device.

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Renesas Electronics America Inc. 2880 Scott Boulevard Santa Clara, CA 95050-2554, U.S.A. Tel: +1-408-588-6000, Fax: +1-408-588-6130 Renesas Electronics Canada Limited 101 Nicholson Road, Newmarket, Ontario L3Y 9C3, Canada Tel: +1-905-598-5441, Fax: +1-905-698-5220 Renesas Electronics Europe Limited Dukes Meadow, Milload Road, Bourne End, Buckinghamshire, SL8 5FH, U.K Tel: +44-1628-651-700, Fax: +44-1628-651-804 Renesas Electronics Europe GmbH Arcadiastrasse 10, 40472 Düsseldorf, Germany Tel: +49-211-65030, Fax: +449-211-6503-1327 Renesas Electronics Changloon, Fax: +449-211-6503-1327 Renesas Electronics (Shangha) Co., Ltd. 7th Floor, Quantum Plaza, No.27 ZhiChunLu Haidian District, Beijing 100083, P.R.China Tel: +86-21-557-1318, Fax: +86-21-6887-7858 Renesas Electronics (Shanghai) Co., Ltd. Unit 204, 205, AZIA Center, No.1233 Lujiazul Ring Rd., Pudong District, Shanghai 200120, China Tel: +86-27-577-1818, Fax: +86-22-6887-7858 Renesas Electronics Hong Kong Limited Unit 204, 205, AZIA Center, No.1233 Lujiazul Ring Rd., Pudong District, Shanghai 200120, China Tel: +86-27-577-1818, Fax: +86-22-6887-7858 Renesas Electronics Shanghai) Co., Ltd. Unit 1501-1613, 16/F., Tower 2, Grand Century Place, 193 Prince Edward Road West, Mongkok, Kowloon, Hong Kong Tel: +85-2886-9318, Fax: +852-2886-9022/9044 Renesas Electronics Singapore PL. Ltd. 80 Bendemeer Road, Unit #06-02 Hyllux Innovation Centre Singapore 339949 Tel: +65-213-0200, Fax: +65-2613-03000 Renesas Electronics Singapore PL. Ltd. 80 Bendemeer Road, Unit #06-02 Hyllux Innovation Centre Singapore 339949 Tel: +65-213-0200, Fax: +65-2613-03000 Renesas Electronics Korea Co., Ltd. 91 FJ, Samik Lavied or Bldg., 720-22 Yeoksam-Dong, Kangnam-Ku, Seoul 135-080, Korea Tel: +60-375-59390, Fax: +63-26-765141